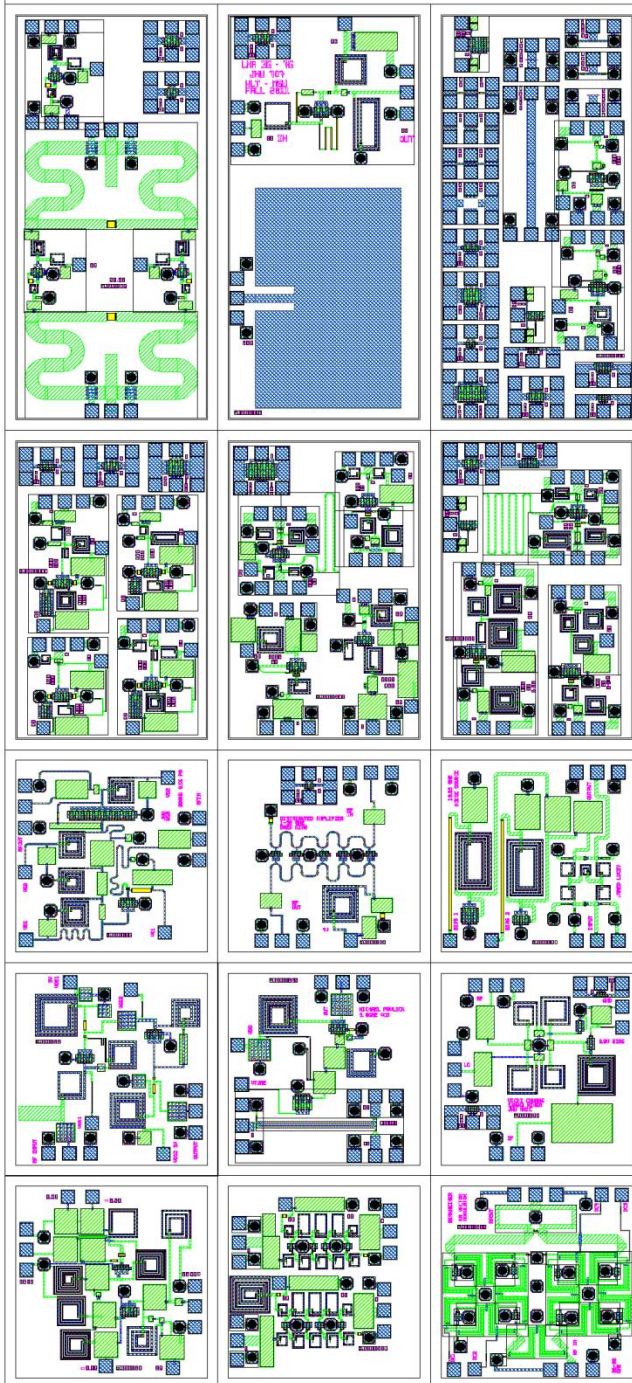


Johns Hopkins University
MMIC Class Fall 2011
Measured Results (Summer 2012)
John E. Penn & Dr. Willie Thompson



5x10mm Tile

9-60x60mil

3-60x90mil

3-60x120mil

PROJECTS F11

X-band Noise Diode –Jared Lucey

jhu11jl

Distributed Amplifier –Drew King

jhu11dk

Broad-band Low Noise Amp (LNA) –Avi Sharma

jhu11as

C-band Power Amplifier (PA)–Muhammed Usman

jhu11mu

Ka-band Vector Modulator – Mark Berkheimer

jhu11mb

C-band Mixer–Vicki Chuang

jhu11vc

X-band Power Amplifier (PA)–Wayne Miller

jhu11wm

Voltage Controlled Oscillator (VCO)–Mike Pavlick

jhu11mp

MMIC Class Fall 2011

Measured Results (Summer 2012)

A quick summary of the projects:

Noise Diode--Applying a large reverse bias voltage to the diode resulted in a significant noise increase. Very interesting because the models did not simulate in this region of bias!

Distributed Amp--This student project worked very well! Lots of bandwidth.

Broad Band Low Noise Amp--This design worked but had lower gain than expected. Possibly the interstage return loss was poor as part of the design tradeoff and was thus more sensitive to process/modeling variation. Still, it worked reasonably well.

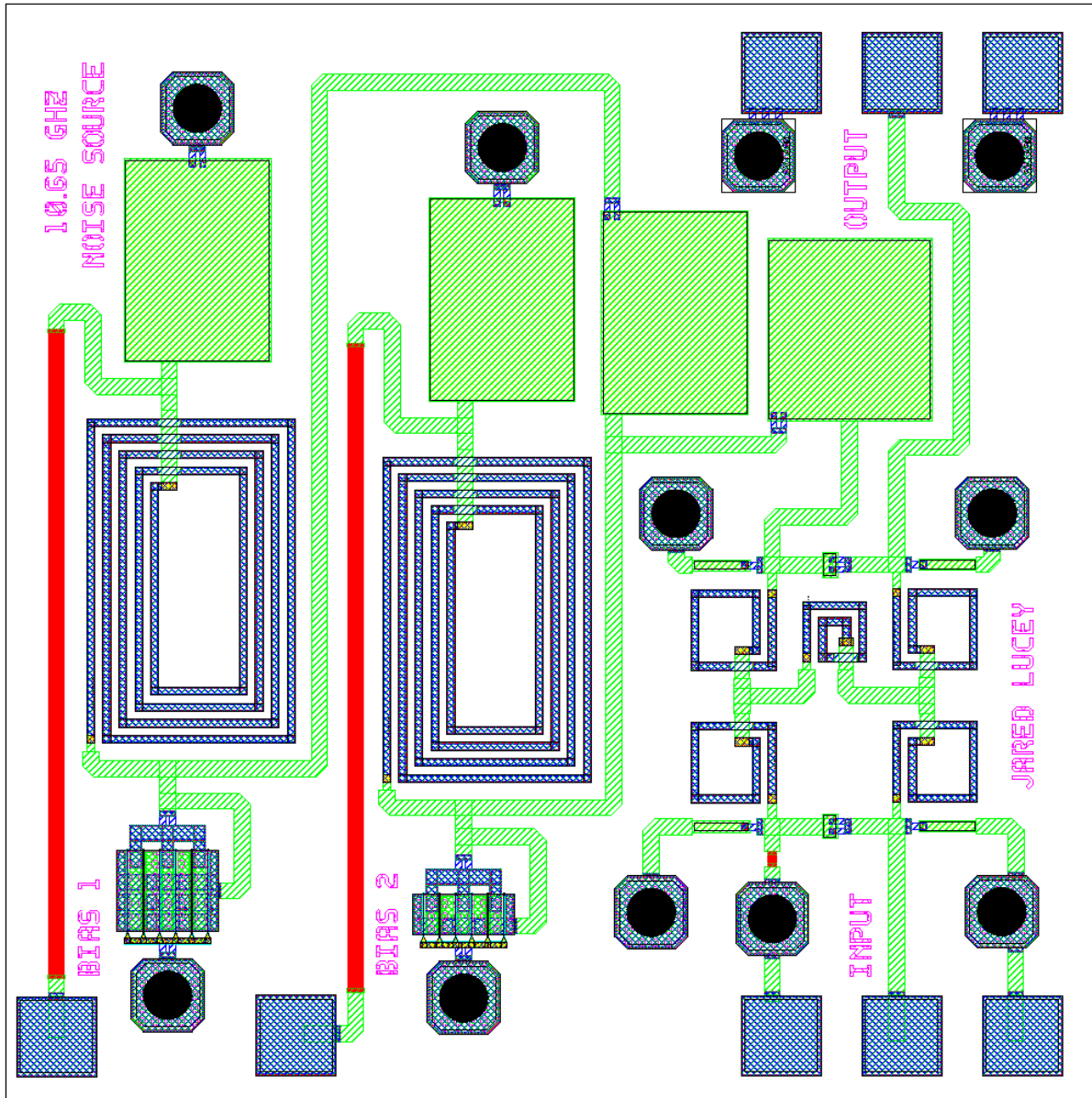
C-Band Power Amp--It was difficult to test the two stage amp which was supposed to be biased below Class C for one stage. But, we got high gain and some measurements in spite of the low freq. problems. More than 100 mW of RF power and very good efficiency in the 2nd stage amp.

Ka-Band Vector Mod--This worked as a vector mod, though ideally it would be good to take lots of measurements over a range of DC biases for the 4 DC inputs and then create a lookup table to optimize the amplitude/phase control. Very, very compact design for Ka-Band operation! 34-40 GHz or so.

C-Band Mixer--Diode mixer worked very well at C-band. Interesting that the 0.13 um PHEMTs as diodes work best with some forward bias (~0.8V) but not so well with no bias (0V) as compared to previous year's diode mixers using the different 0.5 um TQPED PHEMT process.

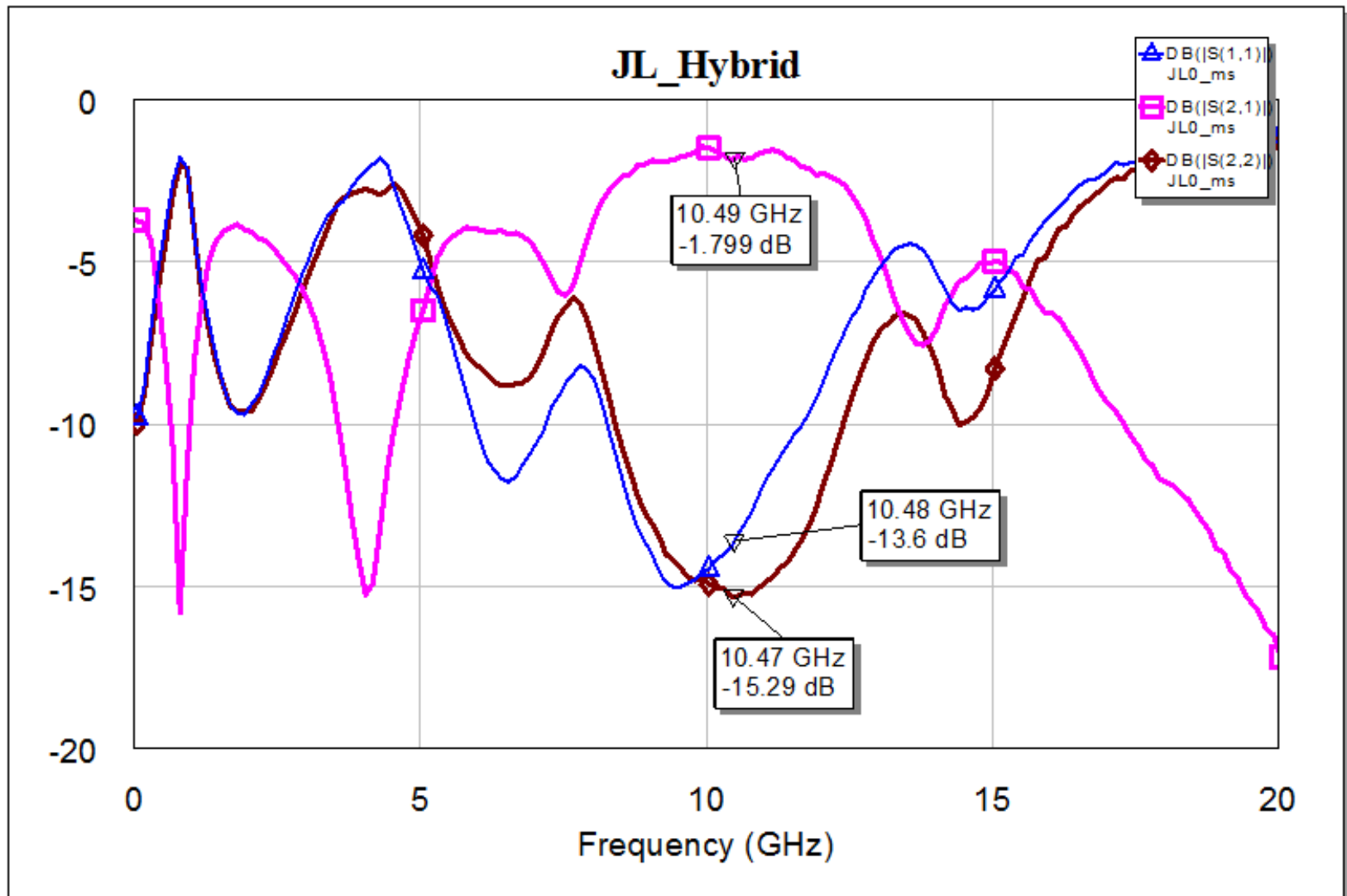
X-Band Power Amp--Again low frequency oscillation problems, particularly in the NWA measurements, but the amplifier did output >100 mW of RF power at 9.5 GHz. Gain was a little lower than expected but this is another one that could benefit from 100 pF caps on the DC bias supplies close to the MMIC.

VCO--Very nice C-Band voltage controlled oscillator. Just to get the VCO to work is quite a challenge, but to actually be so close to the design frequency with good tuning range was pretty amazing.



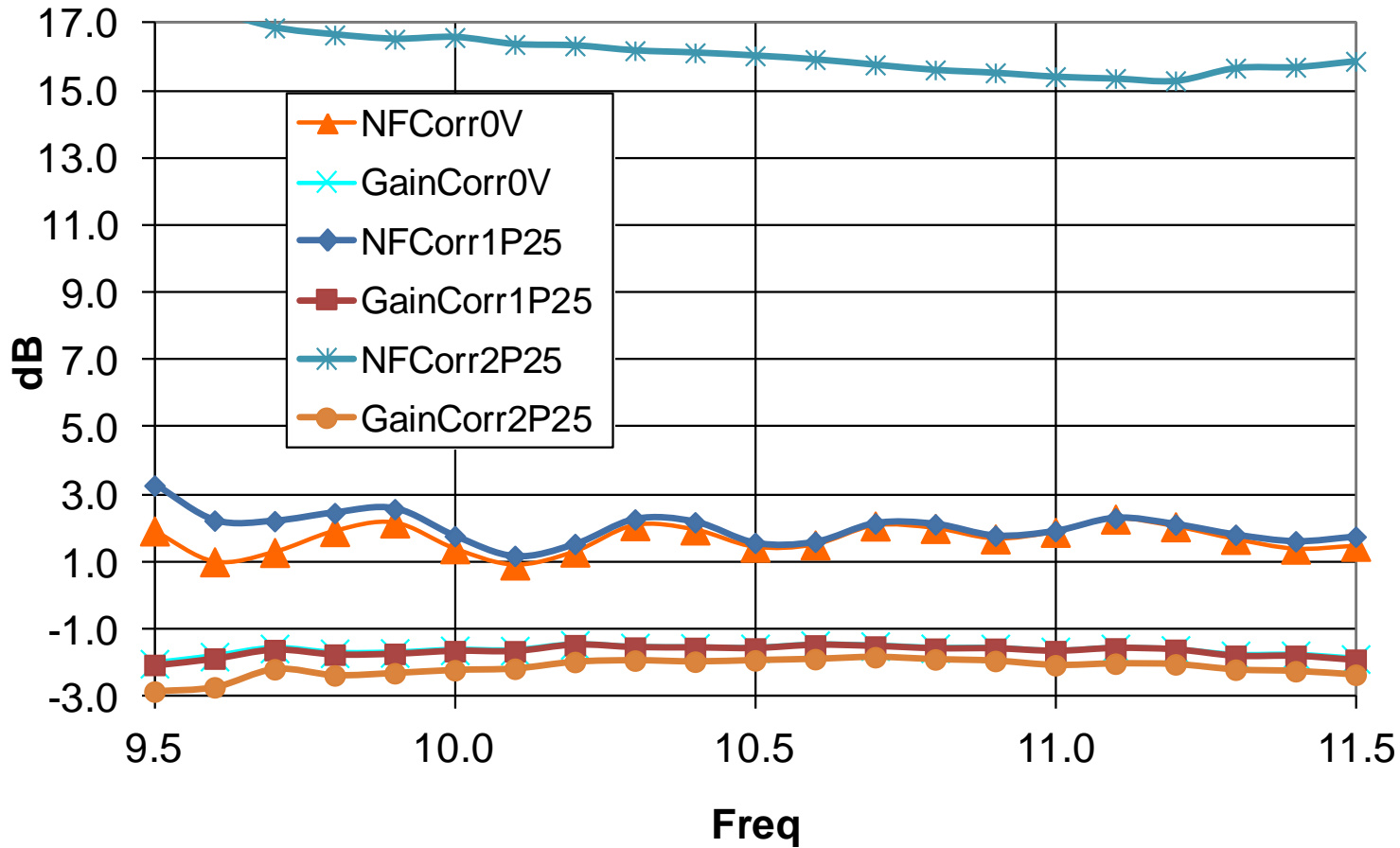
- 1) Jared Lucey
Noise Diode
Worked Well!
Reverse bias beyond
breakdown did create
additional noise,
particularly in one of
the two diodes. This
was not something
that could be
modeled with the
current design kit.
Resistors limited the
current when 25V
was applied to $\sim 7\text{mA}$.

1) Jared Lucey
Noise Diode



JL_NDiode

1) Jared Lucey; Noise Diode



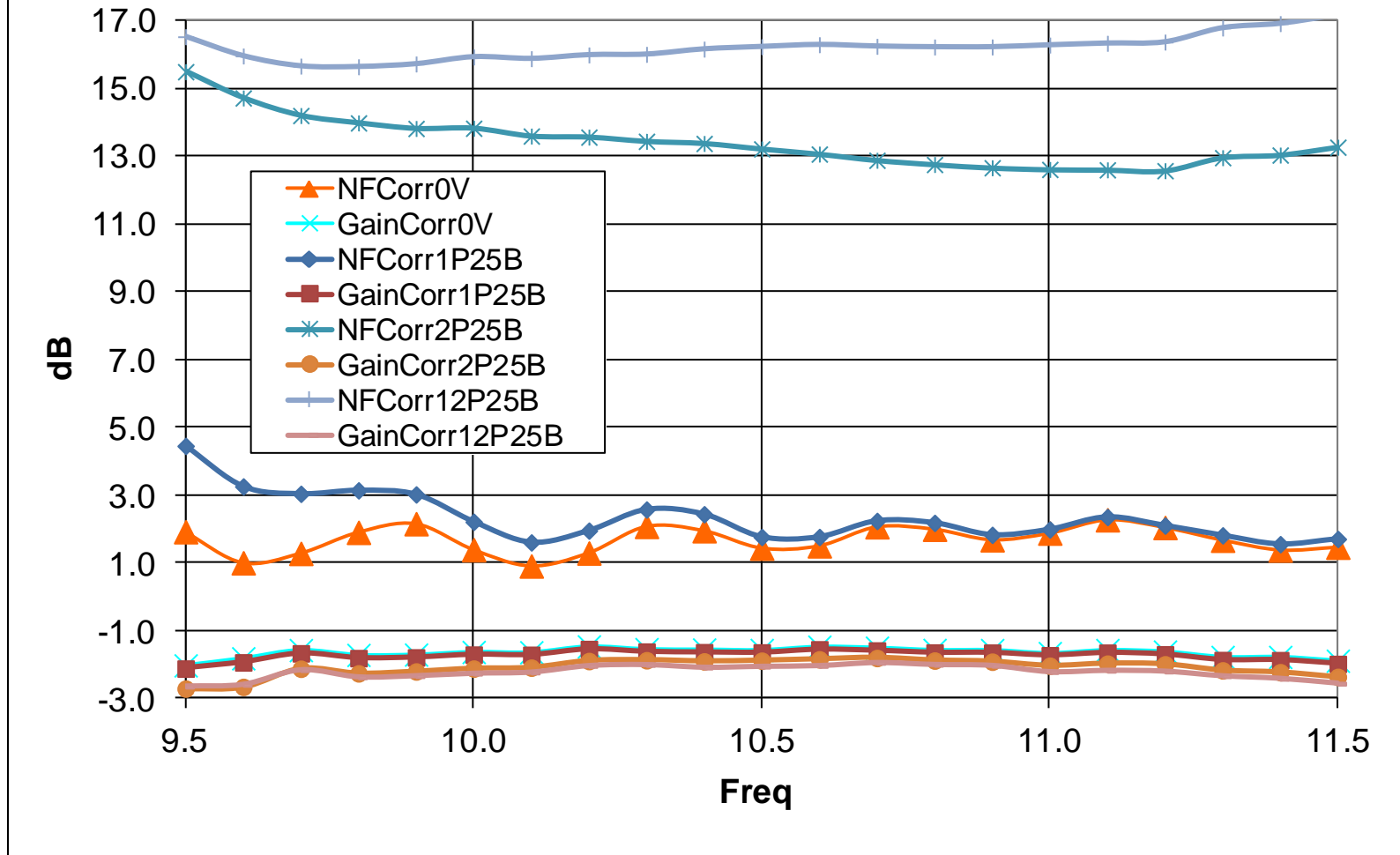
0V, is reference for Die #1 with Diodes UnBiased

1P25 is Reverse Bias of Diode 1; 25V, 7mA (Some Noise Increase)

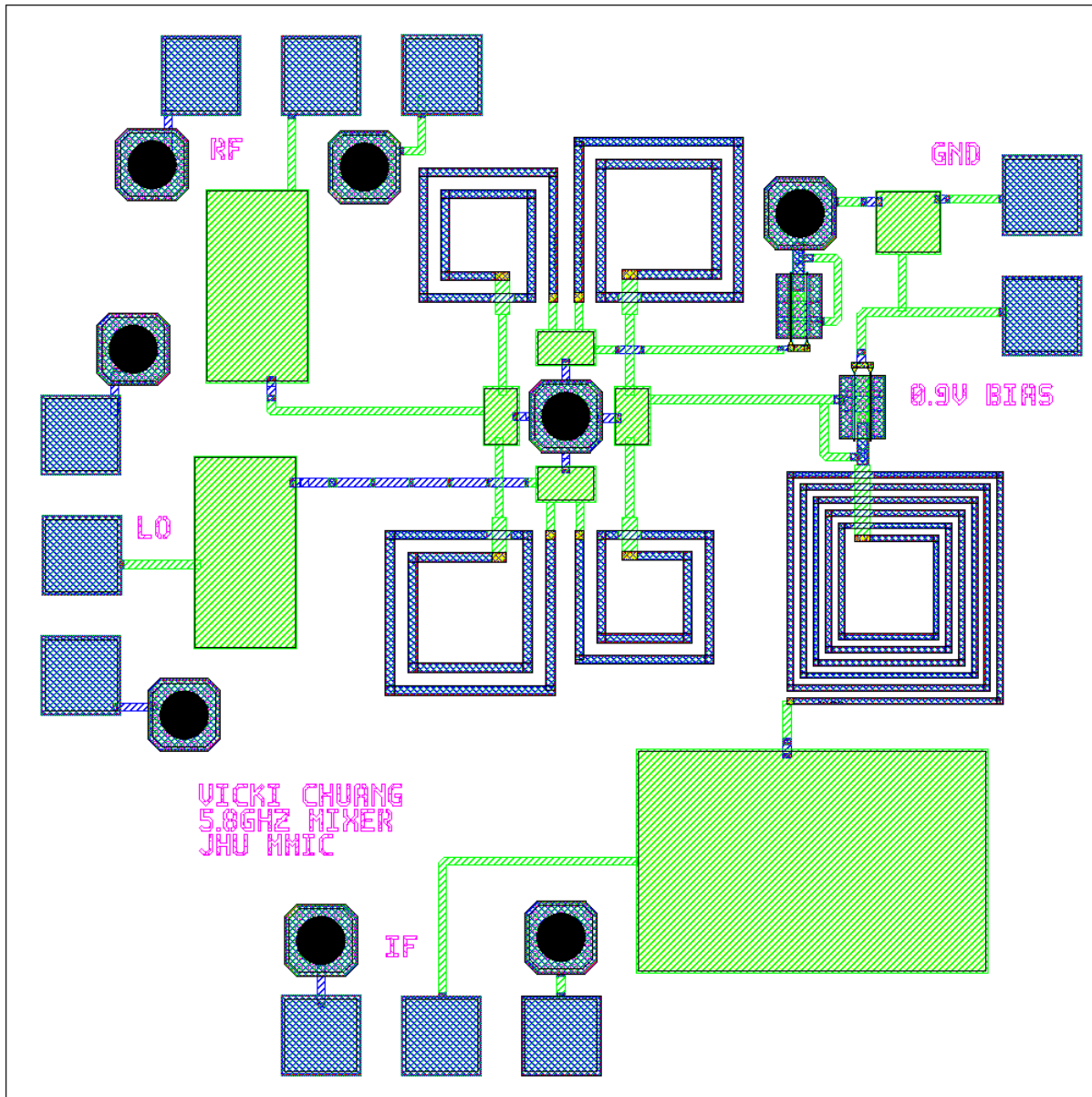
2P25 is Reverse Bias of Diode 2; 25V, 7mA (Note Large Noise Increase!)

Gain Should be approx 1.7 dB loss of hybrid, note it is slightly higher when Diode2 is ON

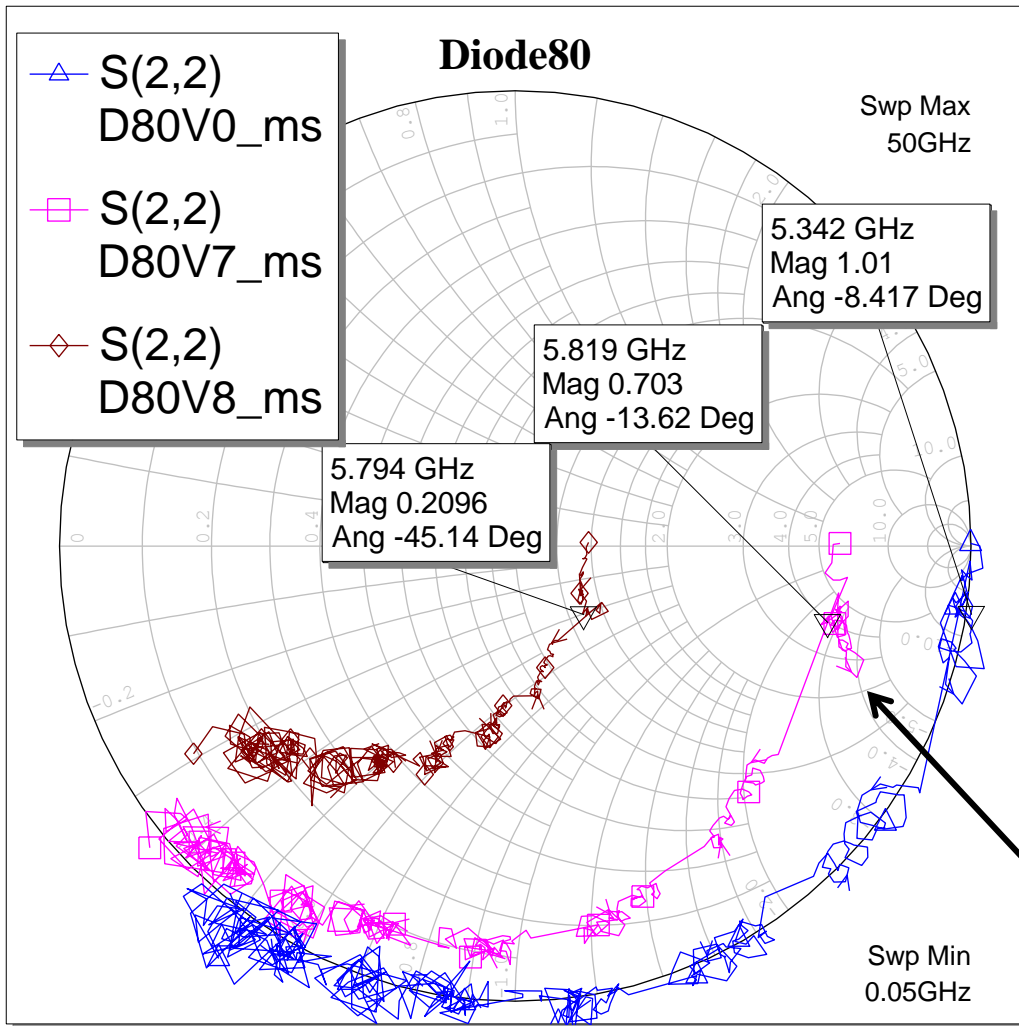
JL_NDiode¹⁾ Jared Lucey; Noise Diode



0V, is reference for Die #1 with Diodes UnBiased, but following is Die #2 Measurements
1P25B is Reverse Bias of Diode 1; 25V, 7mA (Some Noise Increase)
2P25B is Reverse Bias of Diode 2; 25V, 7mA (Note Large Noise Increase!)
12P25B is Reverse Bias of Diode 1 & 2; 25V, 13mA (Note Larger Noise Increase!)

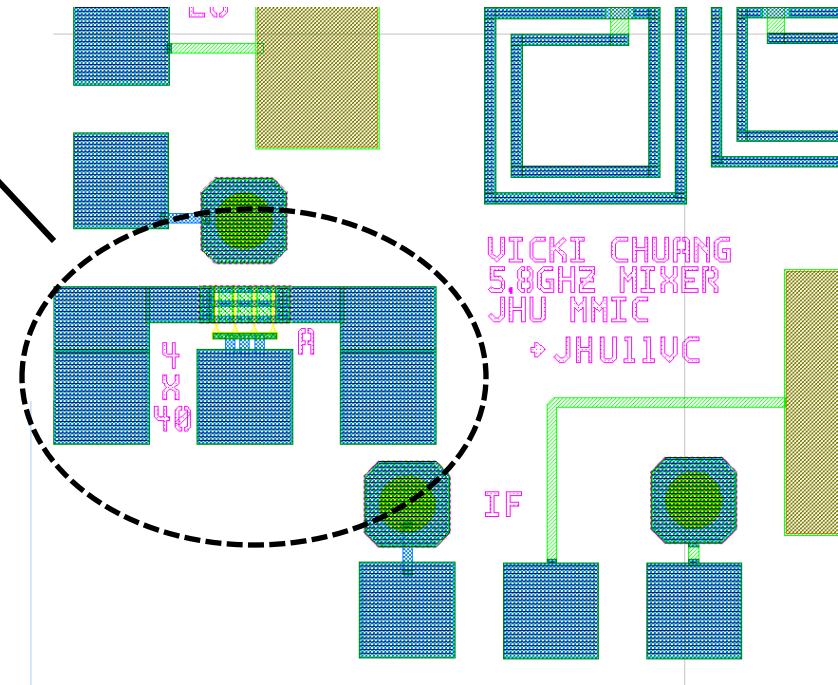


- 2) Vicki Chuang
Diode Mixer
- Mixer worked great, but definitely wanted a forward bias. Test diodes were measured and showed that the match of the 80um PHEMT/Diode was good with about 0.8V of forward bias but looked like a capacitor—reflecting all signals with no DC bias.



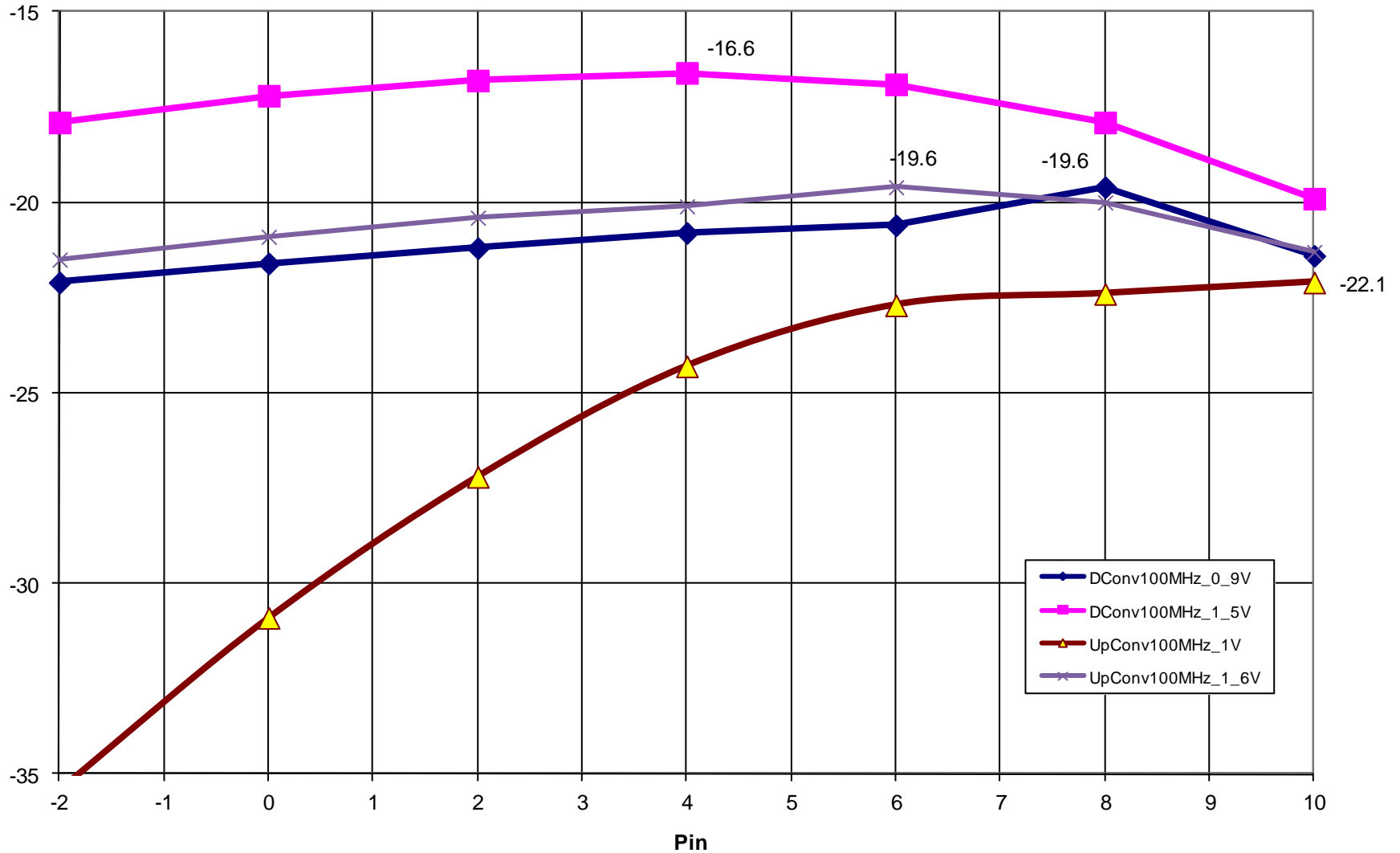
2) Vicki Chuang Diode Mixer

Test Diode 4x40 (0, 0.7, 0.8V):
 Match Best at 0.8V forward bias.
 Poor w/o Bias (0V)



Vicki Chuang Diode Mixer Best Conversion at 1.5-1.6V, Better Down Conv, but Up Conv OK

VC Meas 11 Mixer Down Conversion



Vicki Chuang Diode Mixer Best Conversion at 1.5-1.6V, Better Down Conv, but Up Conv OK

Down Conversion		IF=100 MHz Vb=1.0V			IF=100 MHz Vb=1.5V			IF=100 MHz Vb=1.6V	
LO 5.8G	LO (corr)	IF (meas)	RF (corr)	Loss (gain)	IF (meas)	Loss (gain)	IF (meas)	Loss (gain)	
0	-4	-39.2	-11.6	-27.1	-30.6	-18.5	-30.0	-17.9	
2	-2	-37.7	-11.6	-25.6	-29.8	-17.7	-29.3	-17.2	
4	0	-35.6	-11.6	-23.5	-29.2	-17.1	-28.8	-16.7	
6	2	-33.1	-11.6	-21.0	-28.8	-16.7	-28.5	-16.4	
8	4	-31.2	-11.6	-19.1	-28.6	-16.5	-28.3	-16.2	
10	6	-30.6	-11.6	-18.5	-28.9	-16.8	-28.7	-16.6	
12	8	-31.4	-11.6	-19.3	-30.0	-17.9	-29.7	-17.6	
14	10	-33.6	-11.6	-21.5	-32.3	-20.2	-32.0	-19.9	

Up Conversion		RF=5.9 GHz Vb=1.0V			RF=5.9 GHz Vb=1.6V	
LO 5.8G	LO (corr)	RF (meas)	RF (corr)	Loss (gain)	RF (meas)	Loss (gain)
0	-4	-52.0	-10.5	-39.9	-34.3	-22.2
2	-2	-47.5	-10.5	-35.4	-33.6	-21.5
4	0	-43.0	-10.5	-30.9	-33.0	-20.9
6	2	-39.3	-10.5	-27.2	-32.5	-20.4
8	4	-36.4	-10.5	-24.3	-32.2	-20.1
10	6	-34.8	-10.5	-22.7	-31.7	-19.6
12	8	-34.5	-10.5	-22.4	-32.1	-20.0
14	10	-34.2	-10.5	-22.1	-33.4	-21.3

RF 5.9 GHz and IF 100 MHz -10 dBm setting

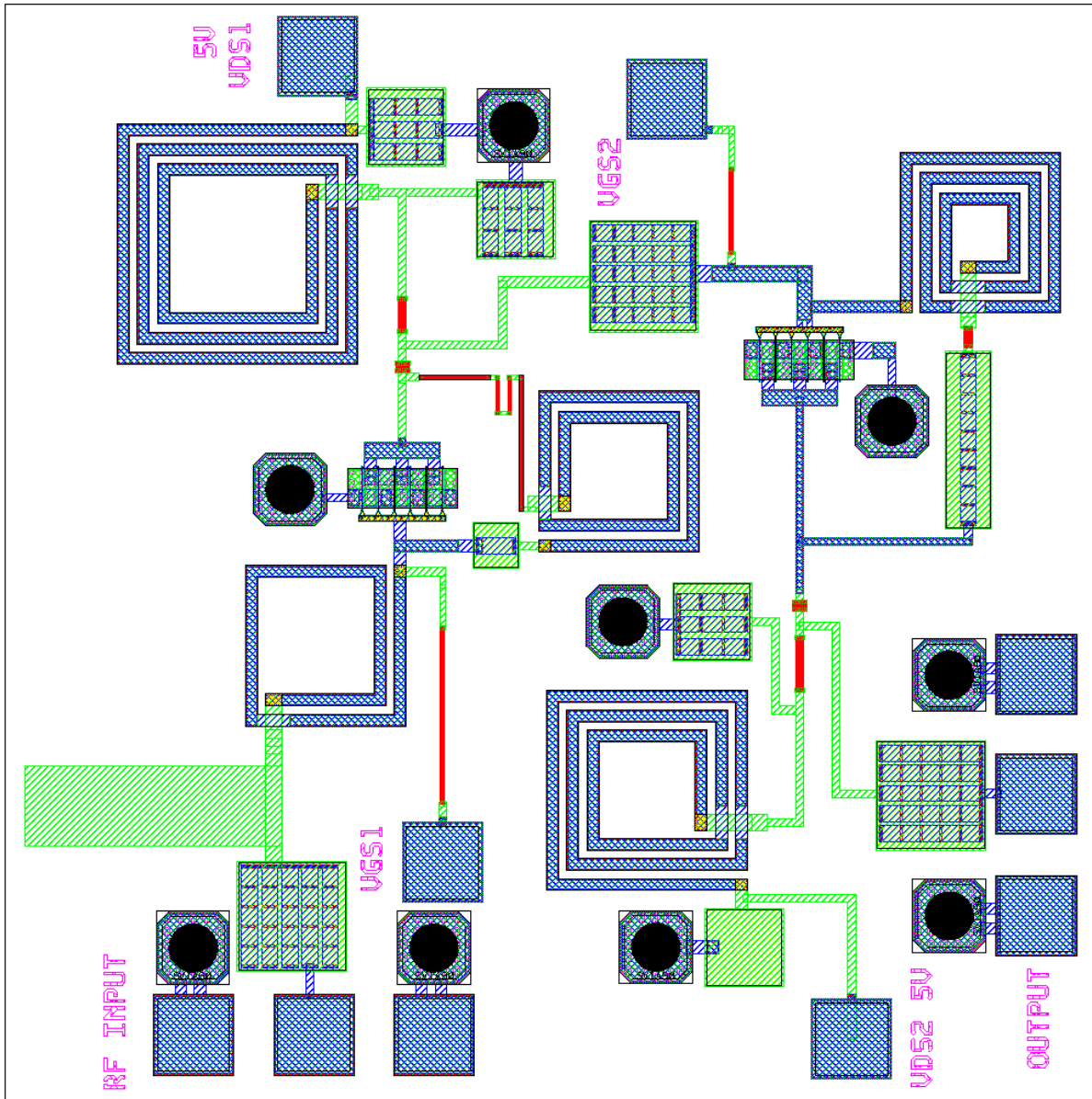
~4dB loss to LO

~0.5 dB loss to IF

Notes:

meas--measured

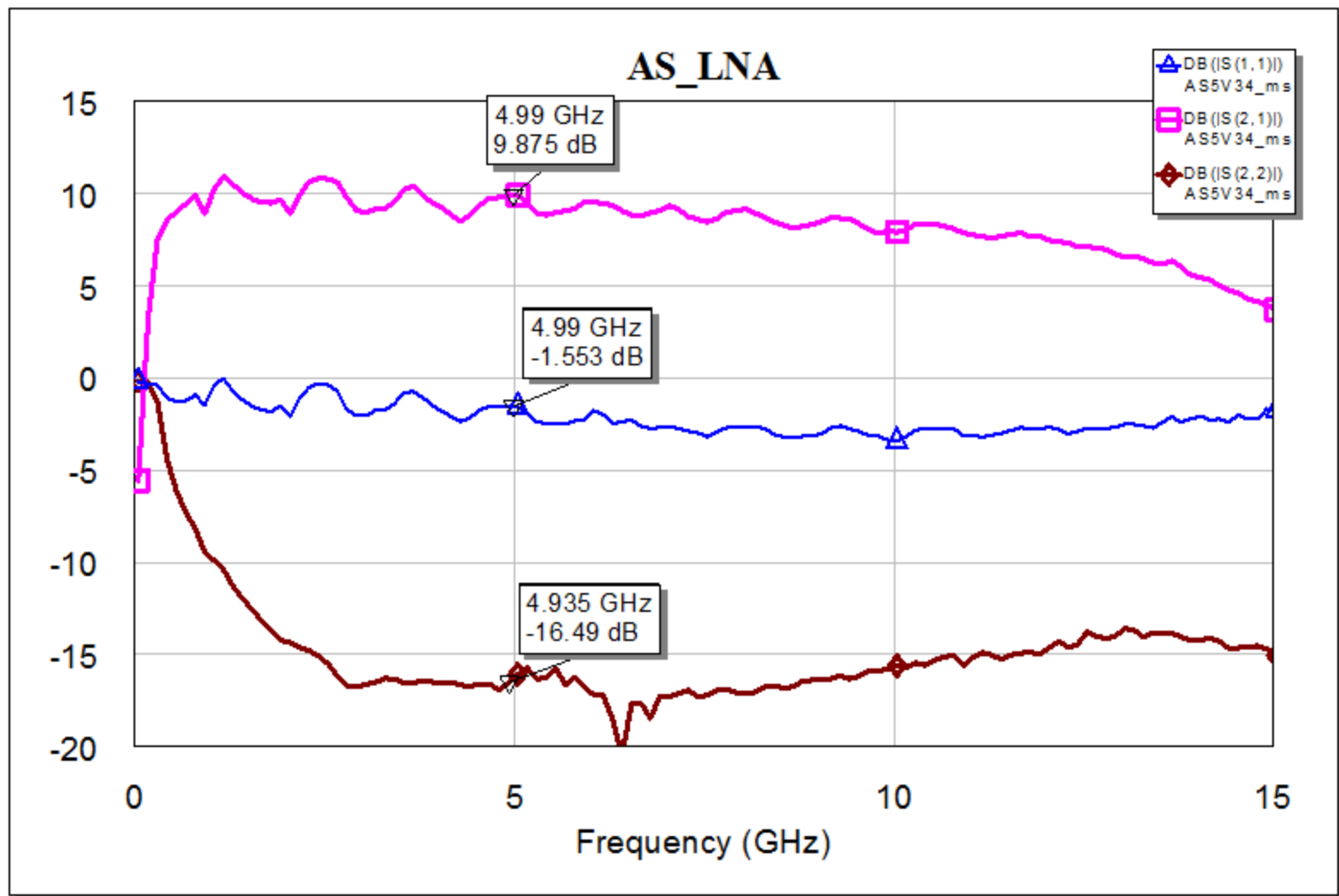
corr—corrected



3) Avi Sharma
 Broad Band LNA
 Measured at 5V ~34mA.
 Gain Low, but then
 Input return loss is
 also poor. Output
 return loss is very
 good and gain is
 broadband. Noise
 figure is a little
 higher than expected
 but follows shape of
 simulations.

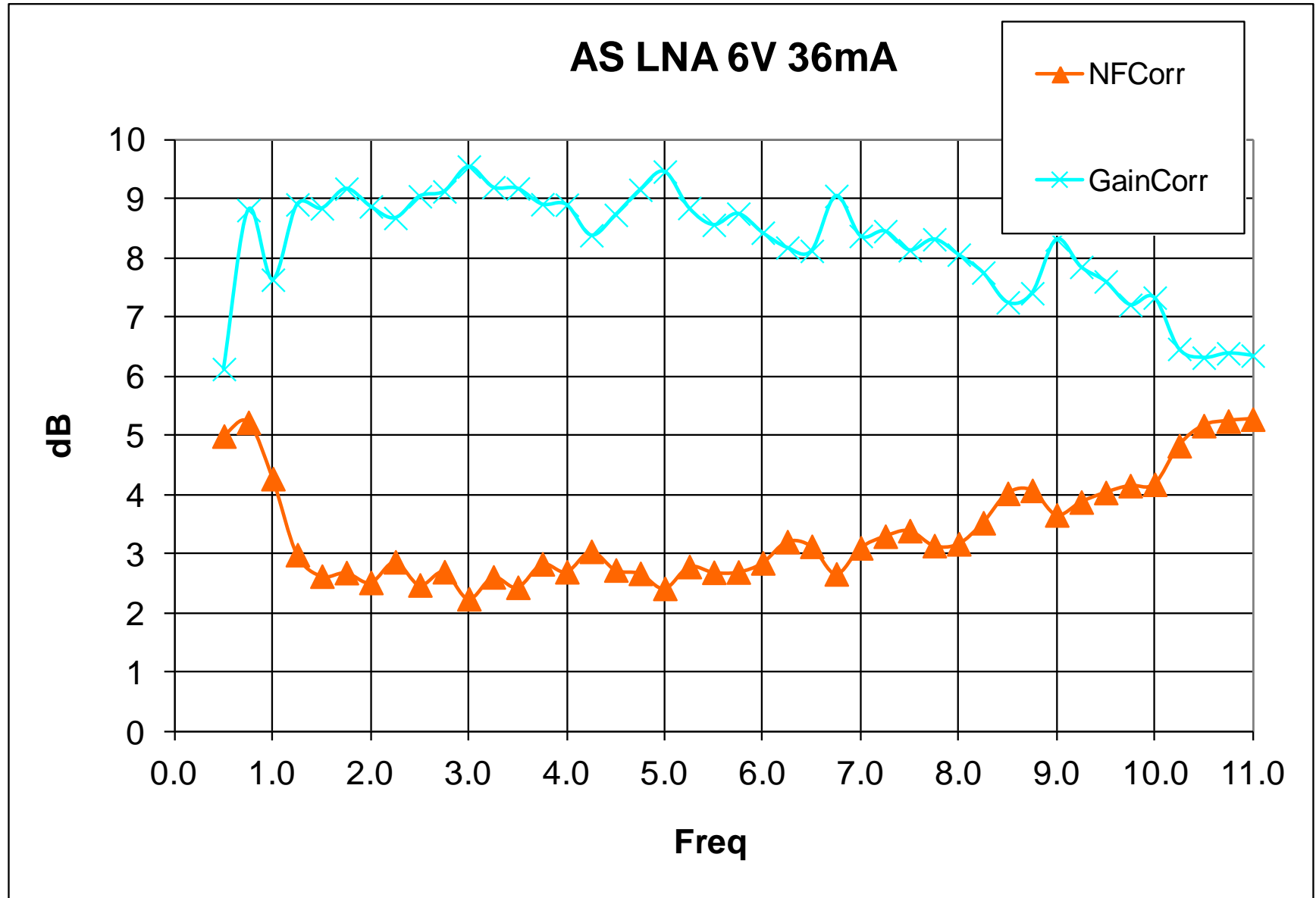
3) Avi Sharma Broad Band LNA

Measured at 5V ~34mA. Gain Low but broadband. Input return loss is poor. Output return loss is very good and broadband.



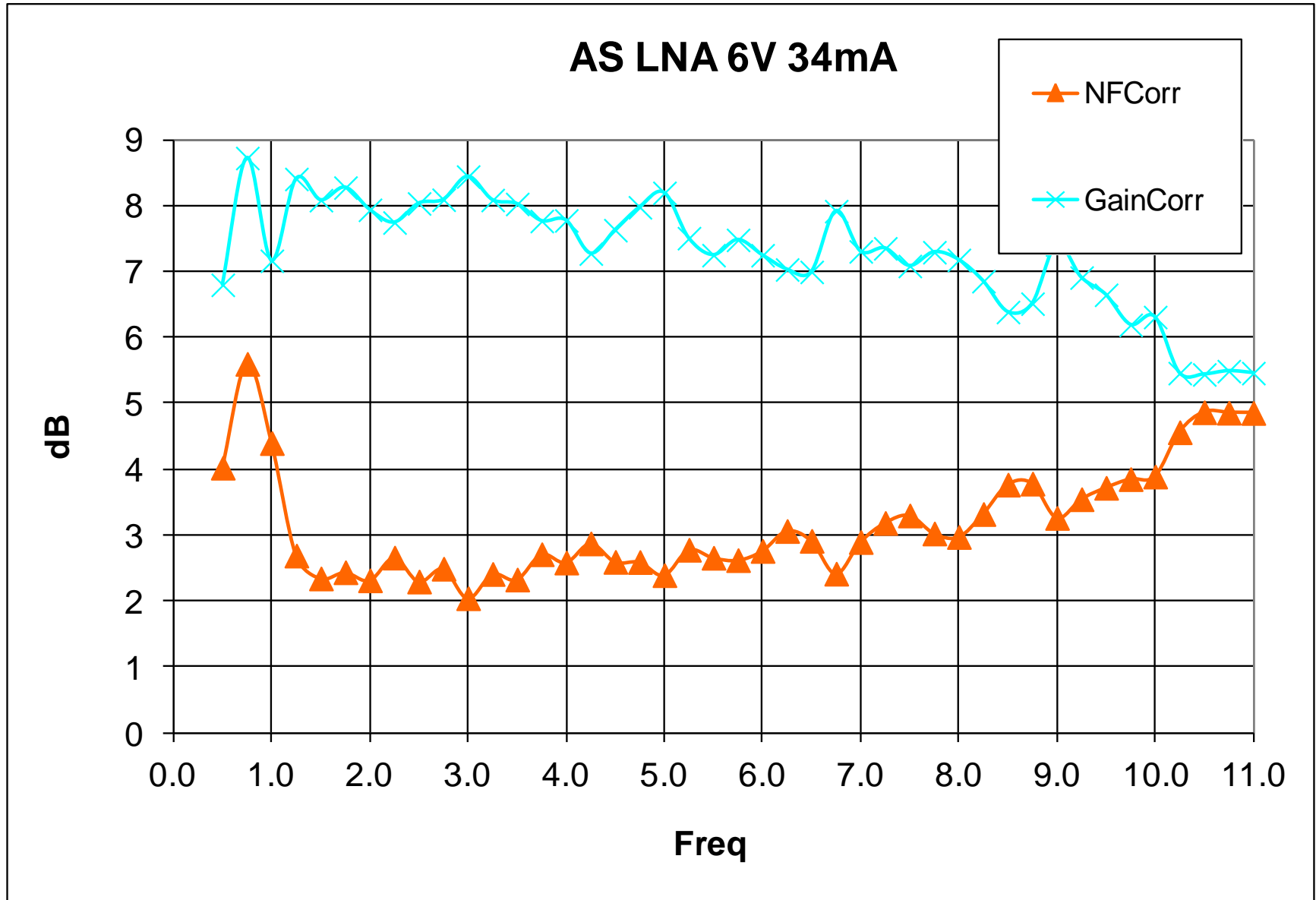
3) Avi Sharma Broad Band LNA

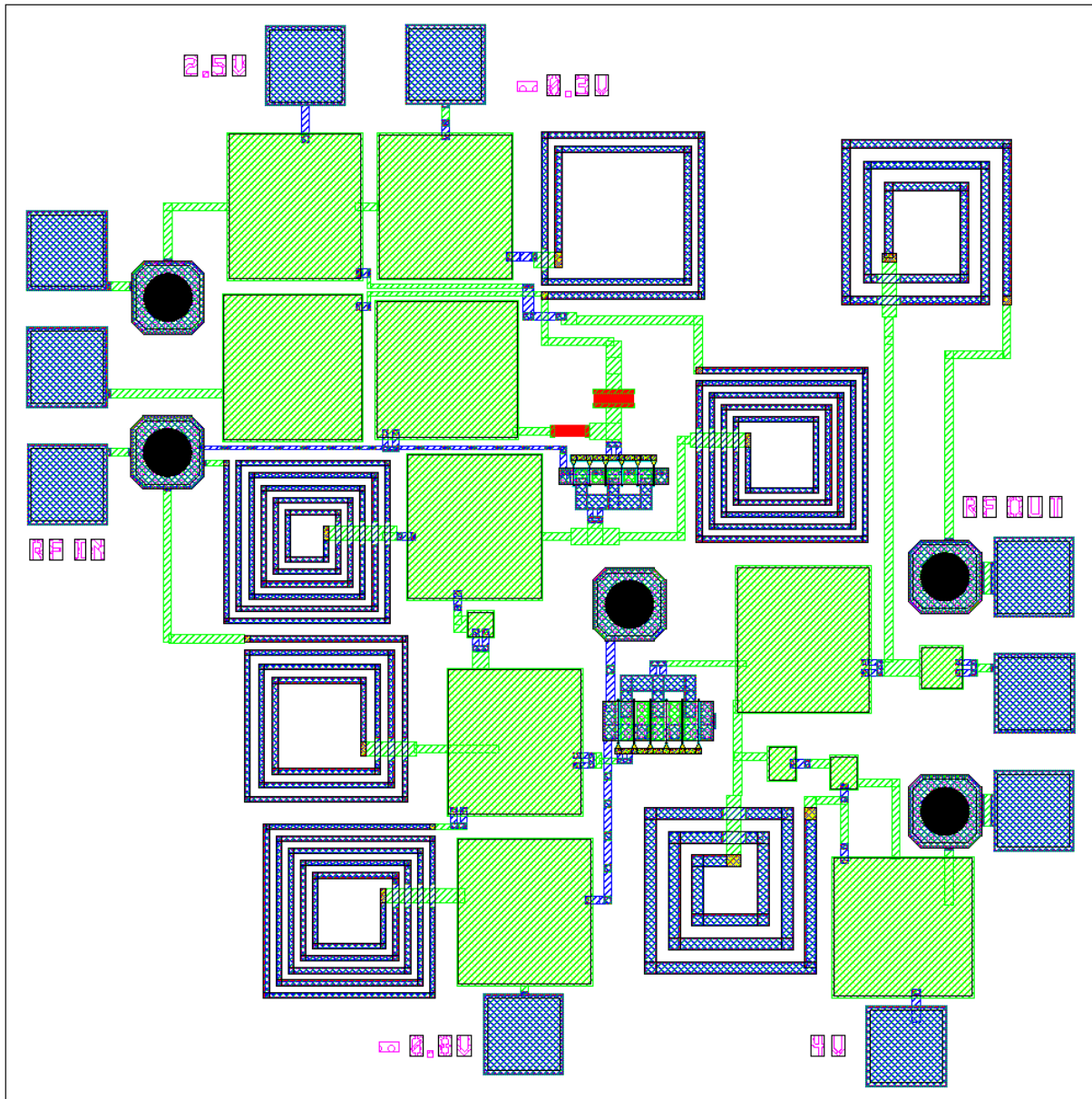
Measured at 6V ~36mA. Comparable Gain with good Noise Figure.



3) Avi Sharma Broad Band LNA

Measured at 6V ~34mA, Die #2. Comparable Gain with good Noise Figure.





4) Muhammed Usman
C Band PA

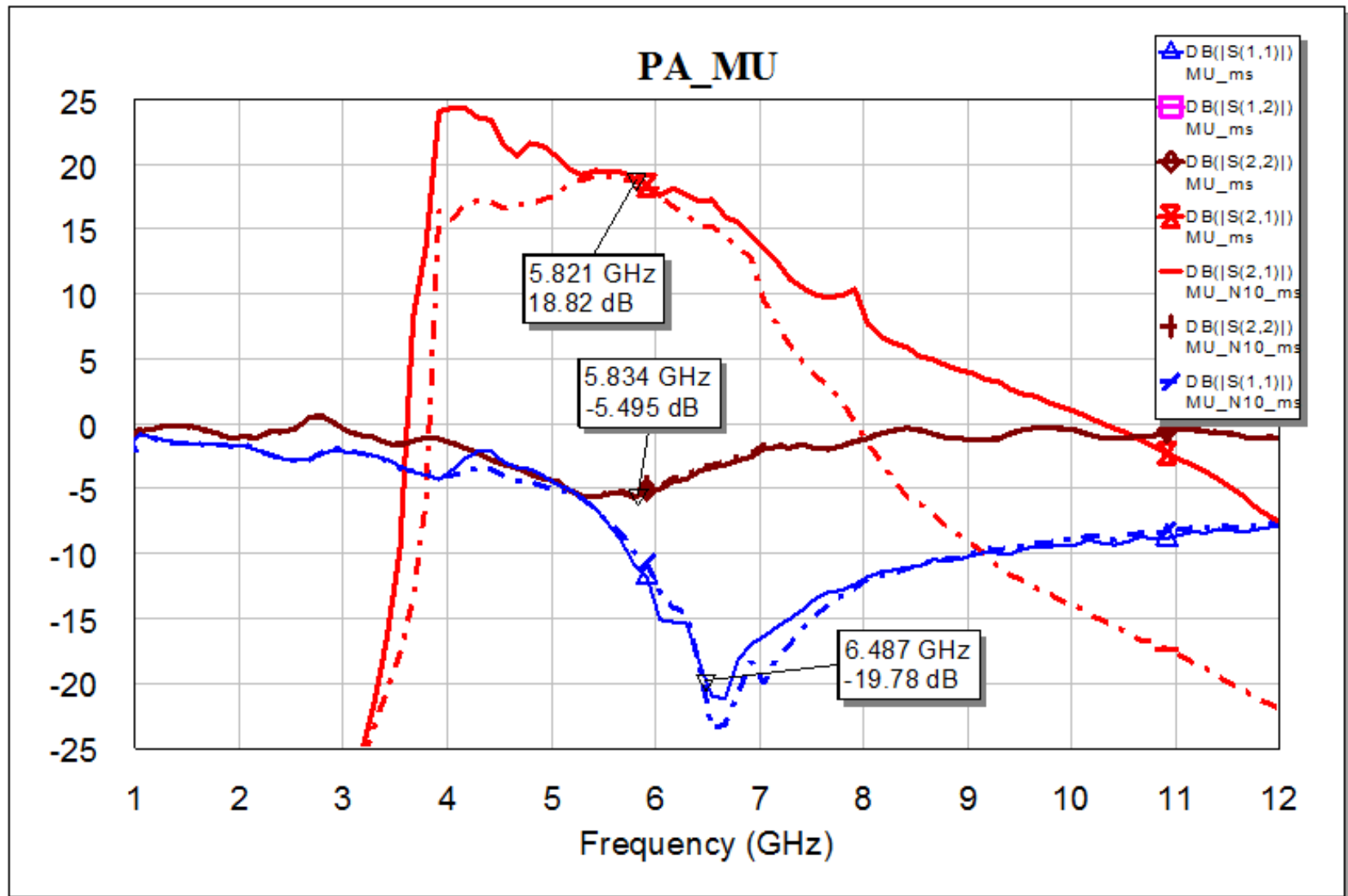
Had difficulty with low frequency oscillations during testing, and also with getting the desired bias. One stage was intended to be strongly Class C bias. Definitely had gain as shown in the following measurements.

Attaching 100pF caps to the DC bias inputs and retesting would probably quell the ~30-40MHz oscillations.

4) Muhammed Usman

Measured C Band PA

Low freq. oscillations? Approx. Bias $vg1=-0.5V$, $vd1=4V$; $vg2=0v$, $vd2=2.0V$; Plots with $-2dBm$ and $-10dBm$ Power (8510)



4) Muhammed Usman Performance Measurements C Band PA 5.6/5.8 GHz

Low freq. oscillations died out at higher input levels; Bold is “clean” looking spectrum on analyzer.

Approx. Bias $v_{g1}=-0.5V$, $v_{d1}=4V$; $v_{g2}=0V$, $v_{d2}=2.5V$ first stage is Class A DC bias, second stage is Class B...

Measured 7/31/12					Loss 3.6-3.7 dB for thru	Low Frequency Oscillations; $V_g \sim 0V$			
5.8 GHz	Die#1	5.8 GHz Fall11 TQP13			$V_{g2}=-0.5V$	4V ; 9 mA	1st stage: 2.5V ; ~42 m		
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC2(mw)	Pout(mw)	Drn Eff?%	
-10.0	1.00	-11.85	2.85	14.70	9	36.0	1.93	5.4	
-8.0	3.92	-9.85	5.77	15.62	11	44.0	3.78	8.6	
-6.0	7.27	-7.85	9.12	16.97	13	52.0	8.17	15.7	
-4.0	10.06	-5.85	11.91	17.76	17	68.0	15.52	22.8	
-2.0	12.02	-3.85	13.87	17.72	20	80.0	24.38	30.5	
0.0	13.90	-1.85	15.75	17.60	24	96.0	37.58	39.1	
2.0	15.25	0.15	17.10	16.95	28	112.0	51.29	45.8	
3.0	15.59	1.15	17.44	16.29	30	120.0	55.46	46.2	
4.0	15.80	2.15	17.65	15.50	31	124.0	58.21	46.9	
No Oscillations at Higher Drive--Bold!									

5.6 GHz	Die#1	5.8 GHz Fall11 TQP13			$V_{g2}=-0.5V$	4V ; 9 mA	1st stage: 2.5V ; ~42		
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC2(mw)	Pout(mw)	Drn Eff?%	
-10.0	3.03	-11.80	4.83	16.63	10	40.0	3.04	7.6	
-8.0	6.45	-9.80	8.25	18.05	13	52.0	6.68	12.9	
-6.0	10.12	-7.80	11.92	19.72	18	72.0	15.56	21.6	
-4.0	12.67	-5.80	14.47	20.27	22	88.0	27.99	31.8	
-2.0	14.84	-3.80	16.64	20.44	27	108.0	46.13	42.7	
0.0	15.72	-1.80	17.52	19.32	31	124.0	56.49	45.6	
2.0	16.37	0.20	18.17	17.97	34	136.0	65.61	48.2	
3.0	16.51	1.20	18.31	17.11	35	140.0	67.76	48.4	
No Oscillations at Higher Drive--Bold!									

Notes:

corr—corrected

SG—Signal Generator

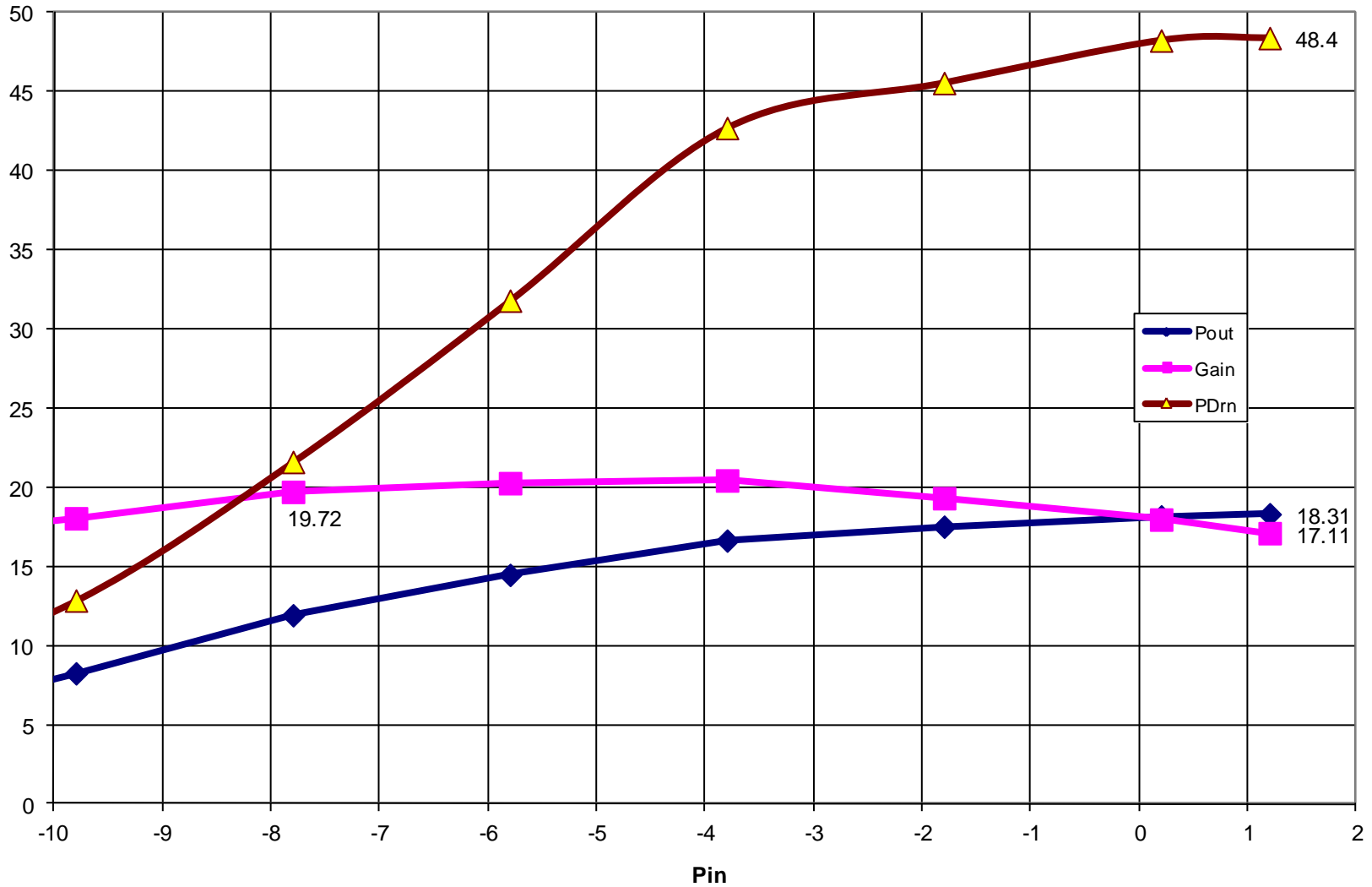
SA—Spectrum Analyzer

4) Muhammed Usman

Performance Measurements C Band PA 5.6 GHz

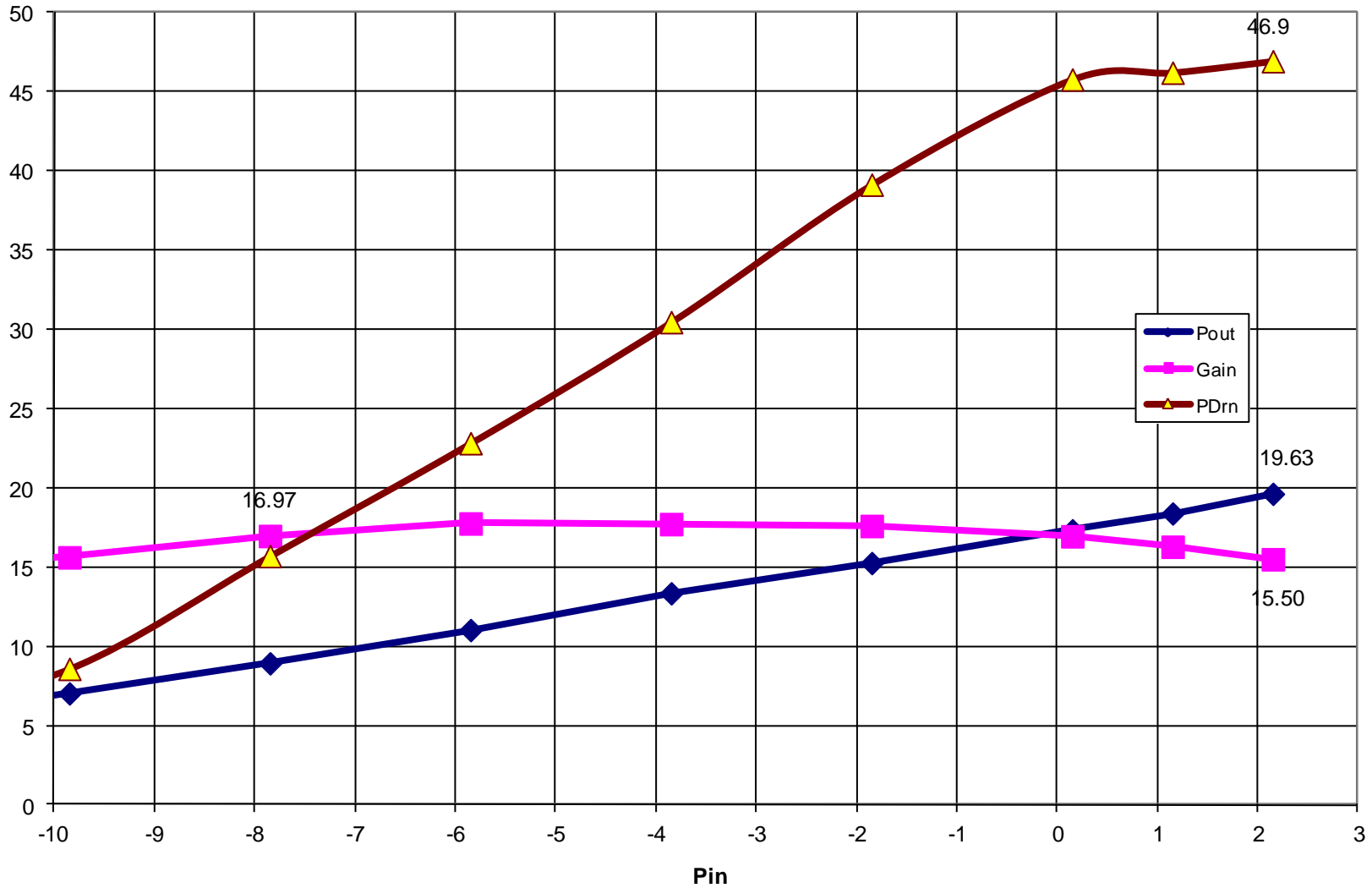
Pout, Gain, Pdrn (Drain Efficiency of Stage 2 only) vs. Pin

WU5.6GHz Meas 11
4V 10-35mA 2nd stage + 2.5V ~42mA 1st stage

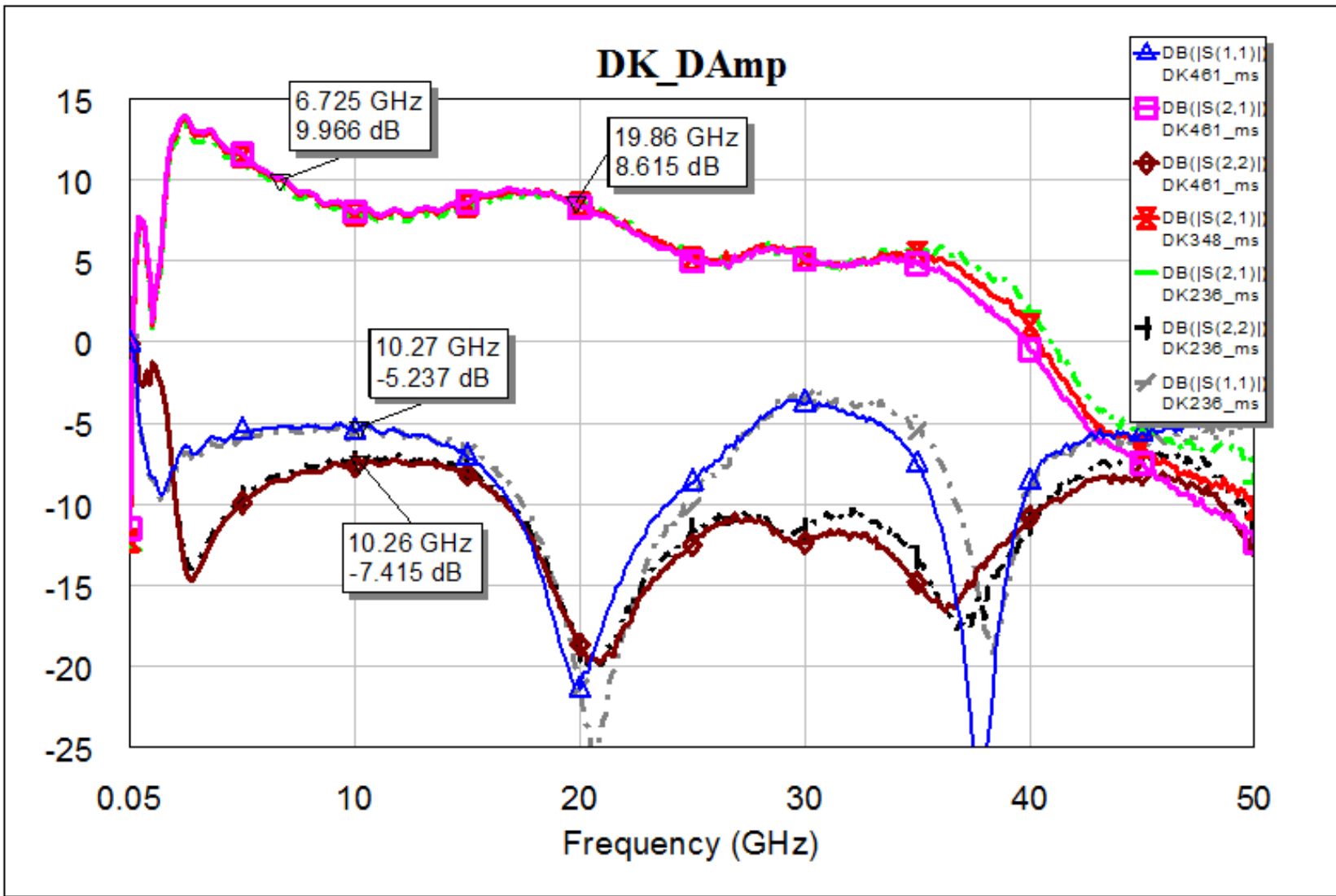


4) Muhammed Usman Performance Measurements C Band PA 5.8 GHz Pout, Gain, Pdrn (Drain Efficiency of Stage 2 only) vs. Pin

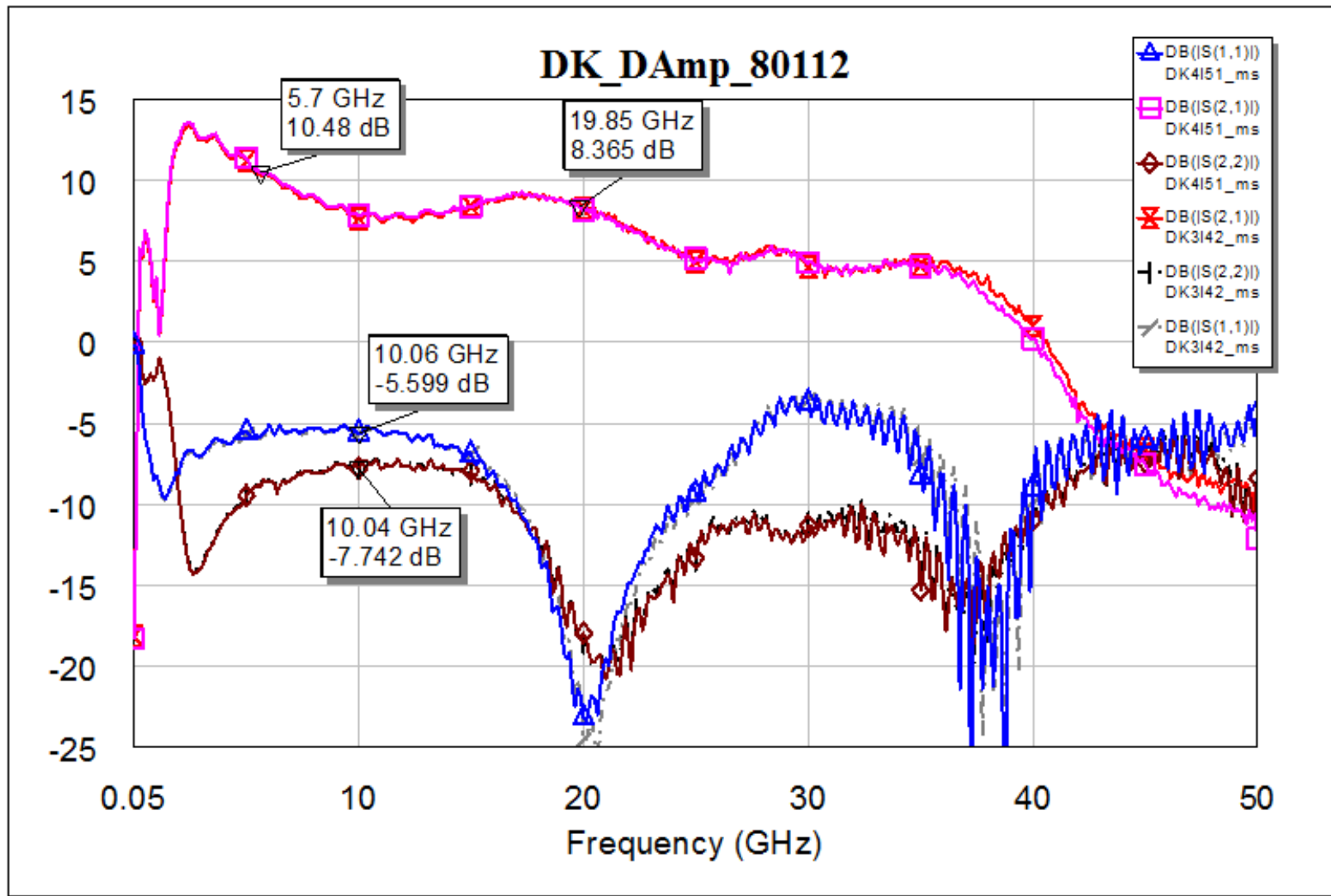
WU5.8GHz Meas 11
4V 10-35mA 2nd stage + 2.5V ~42mA 1st stage



5) Drew King 4V 61 mA
1-30 GHz Dist Amp

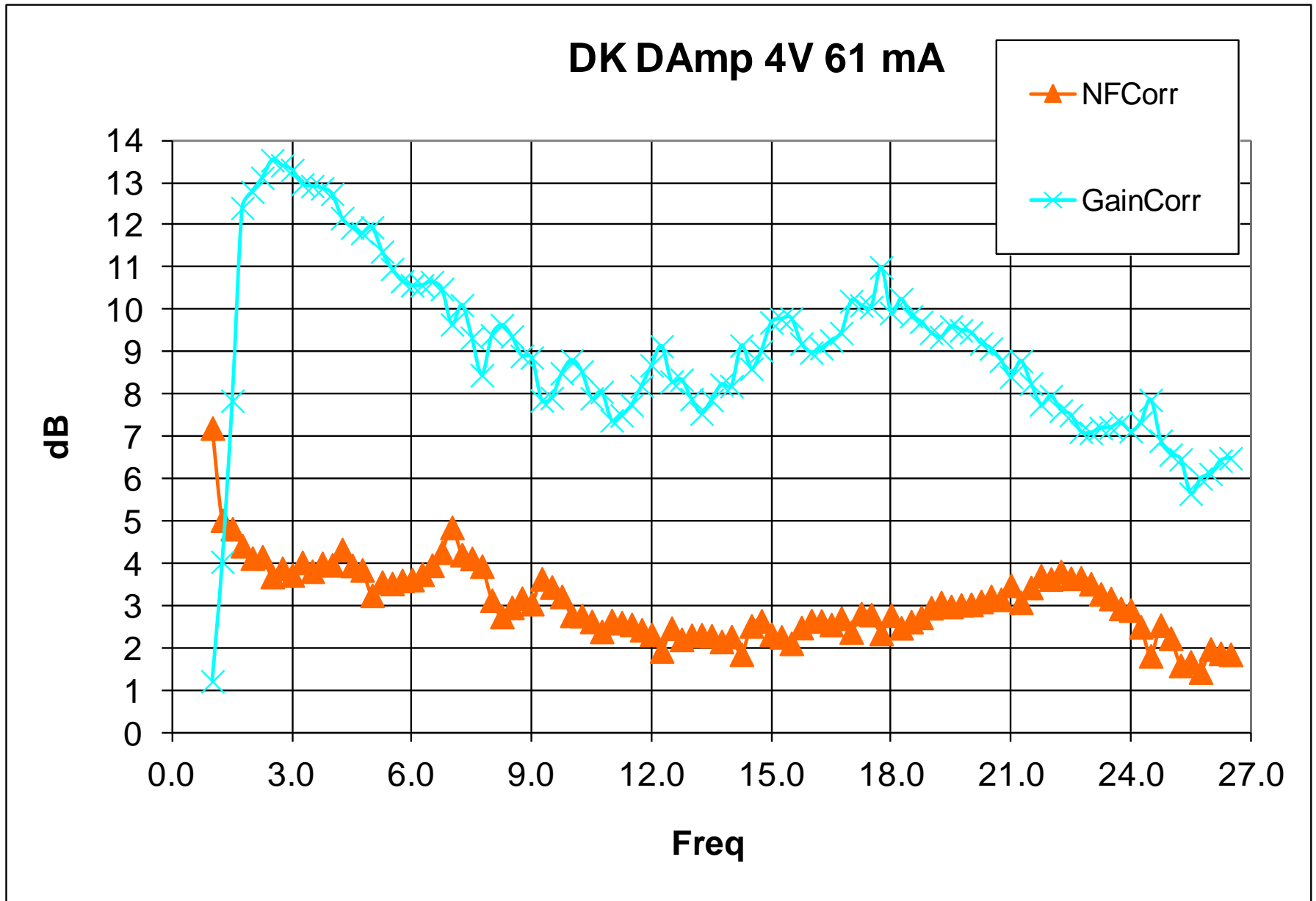


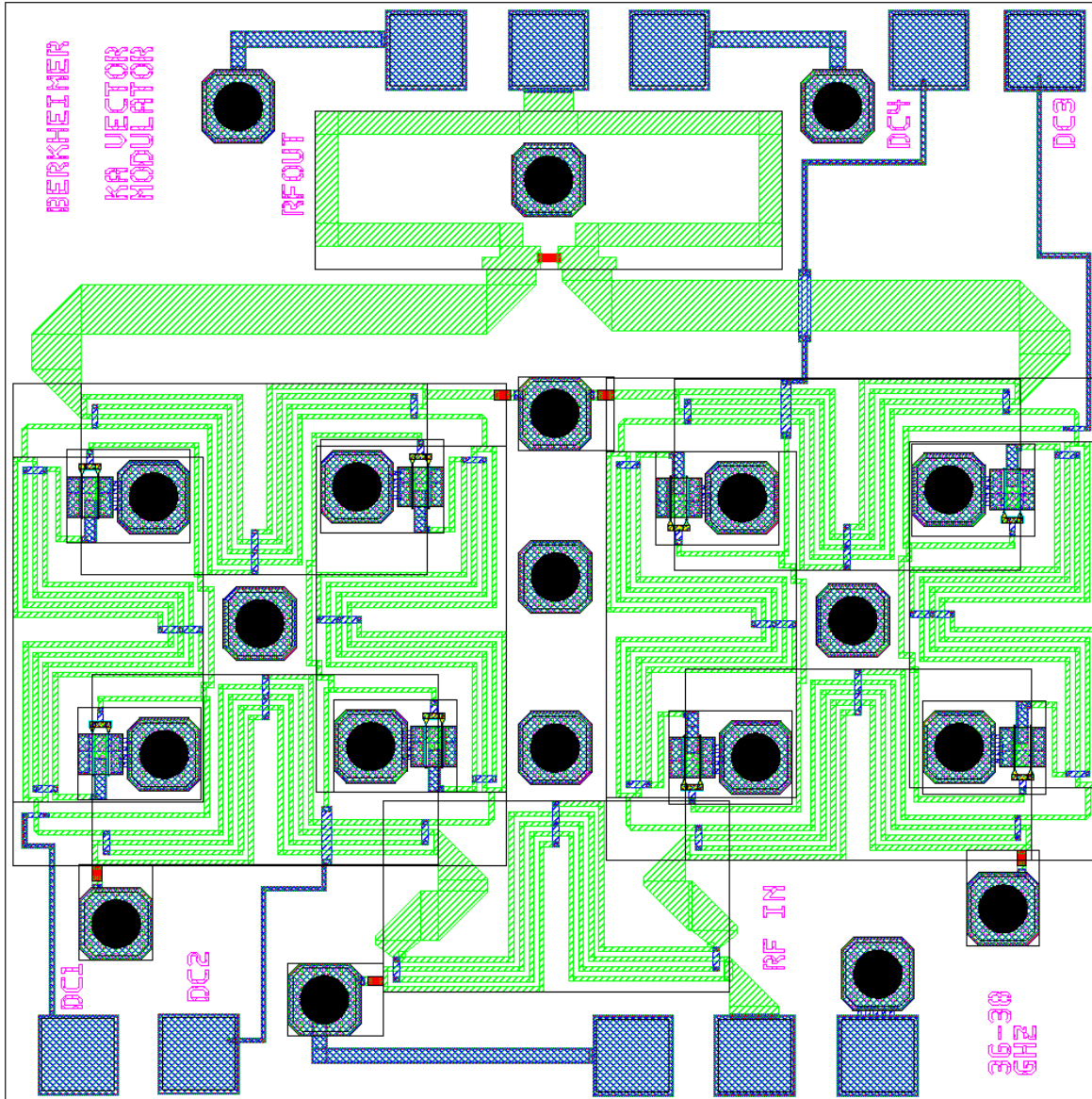
5) Drew King 4V 51 mA
1-30 GHz Dist Amp Re-Measured 8/1/12



5) Drew King 4V 61 mA

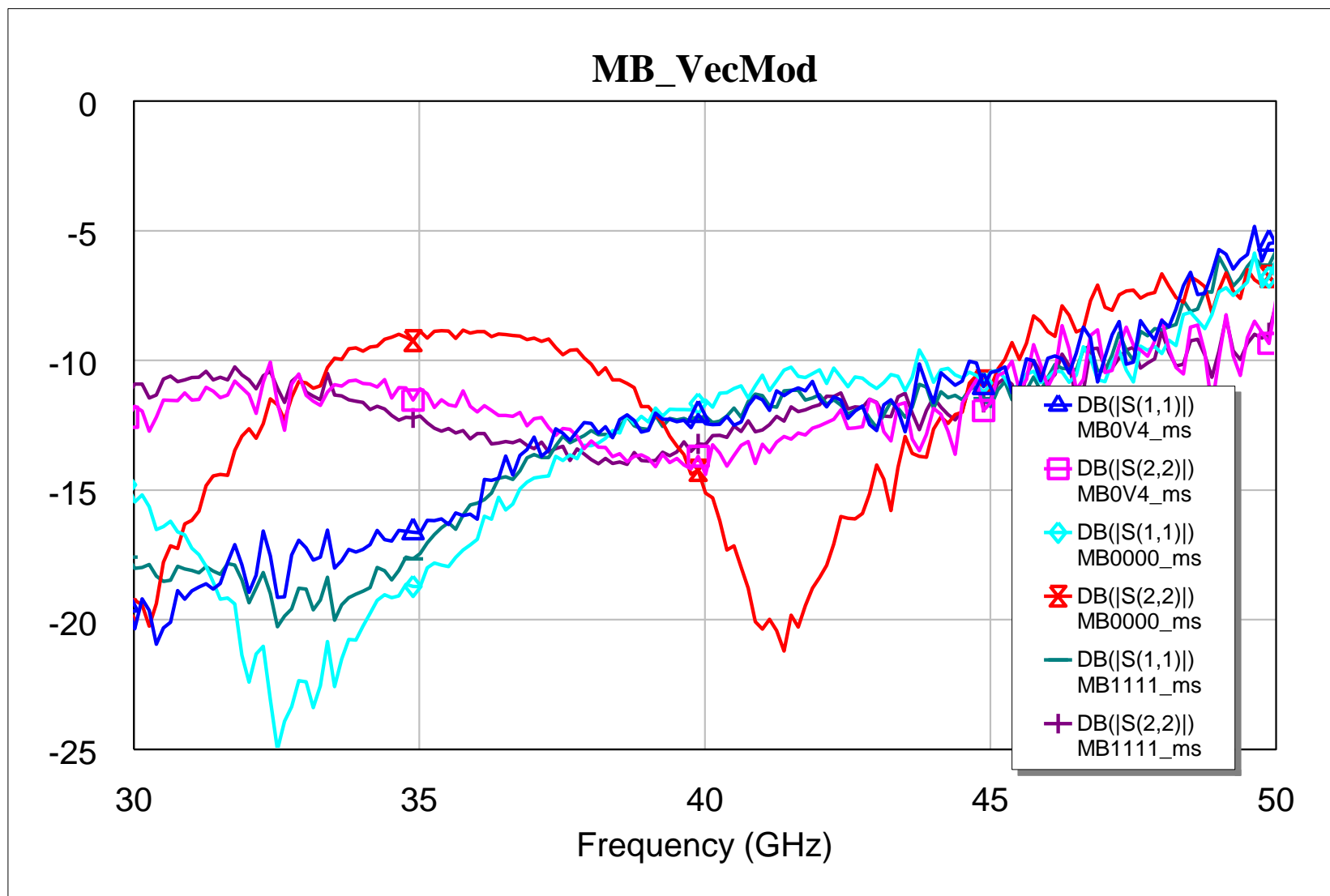
1-30 GHz Dist Amp NF Measured 7/12/12; Noisy Cal (esp. ~7 GHz)





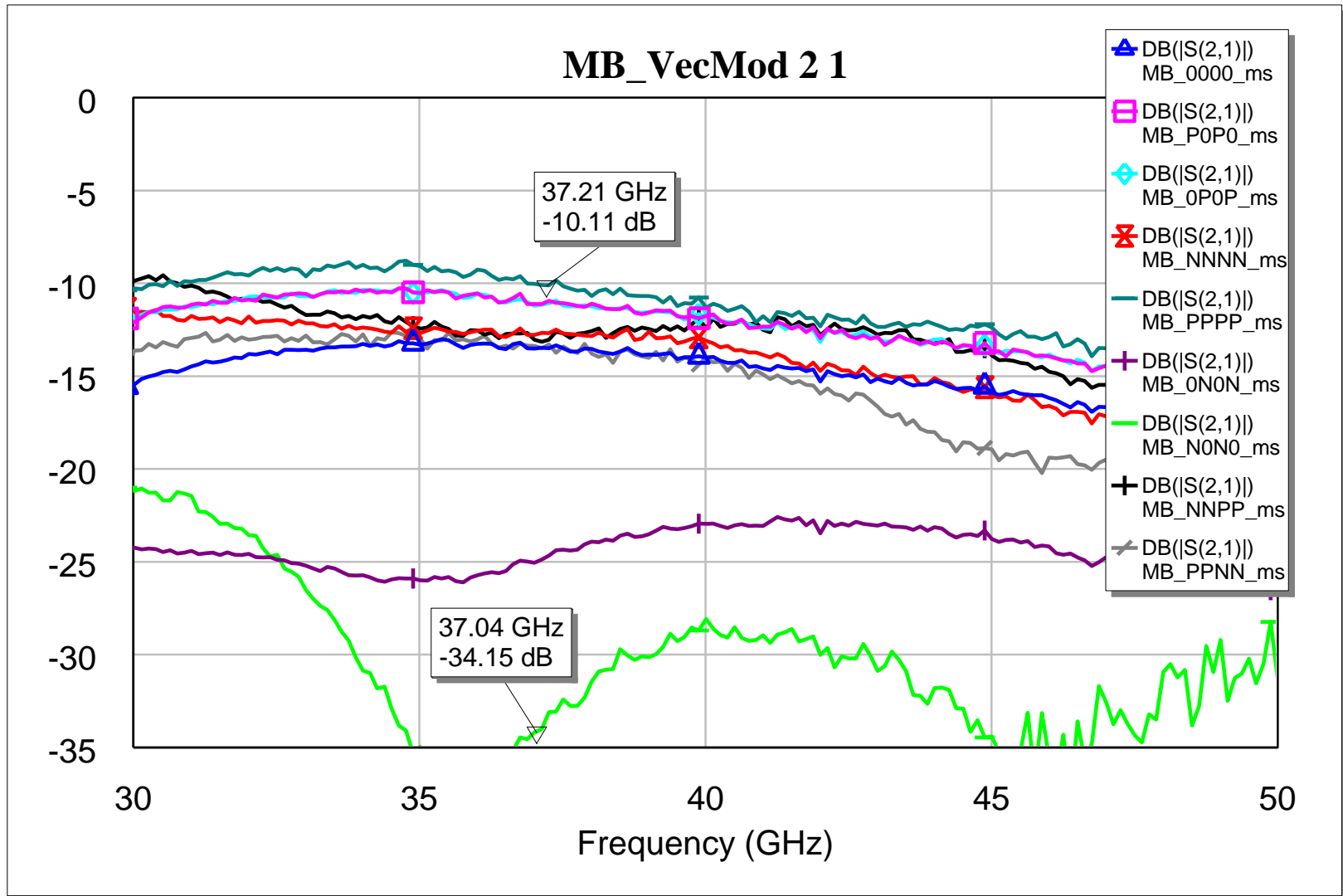
6) Mark Berheimer
 Vector Modulator
 Vector Modulator tested
 at various DC inputs.
 Not sure what the
 ideal levels should be
 but automated
 measurements and a
 lookup table could
 be used to control
 the amplitude and
 phase over a range
 of frequencies
 around 34-40 GHz.

6) Mark Berheimer Vector Modulator (Plot Showing Return Loss at Various DC Biases)

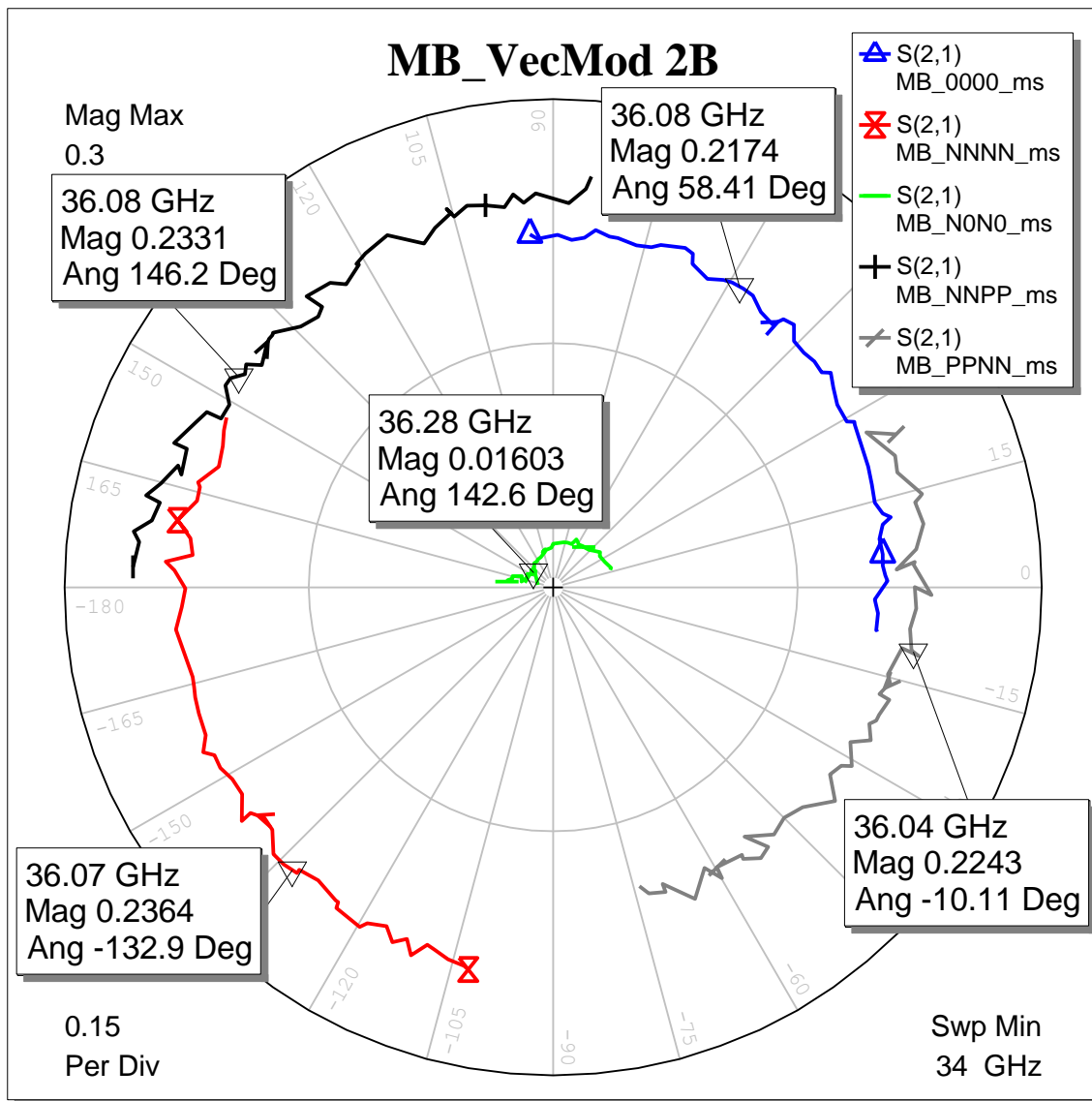


6) Mark Berheimer Vector Modulator

(Plot Showing Range of Insertion Loss S21 at Various DC Biases)

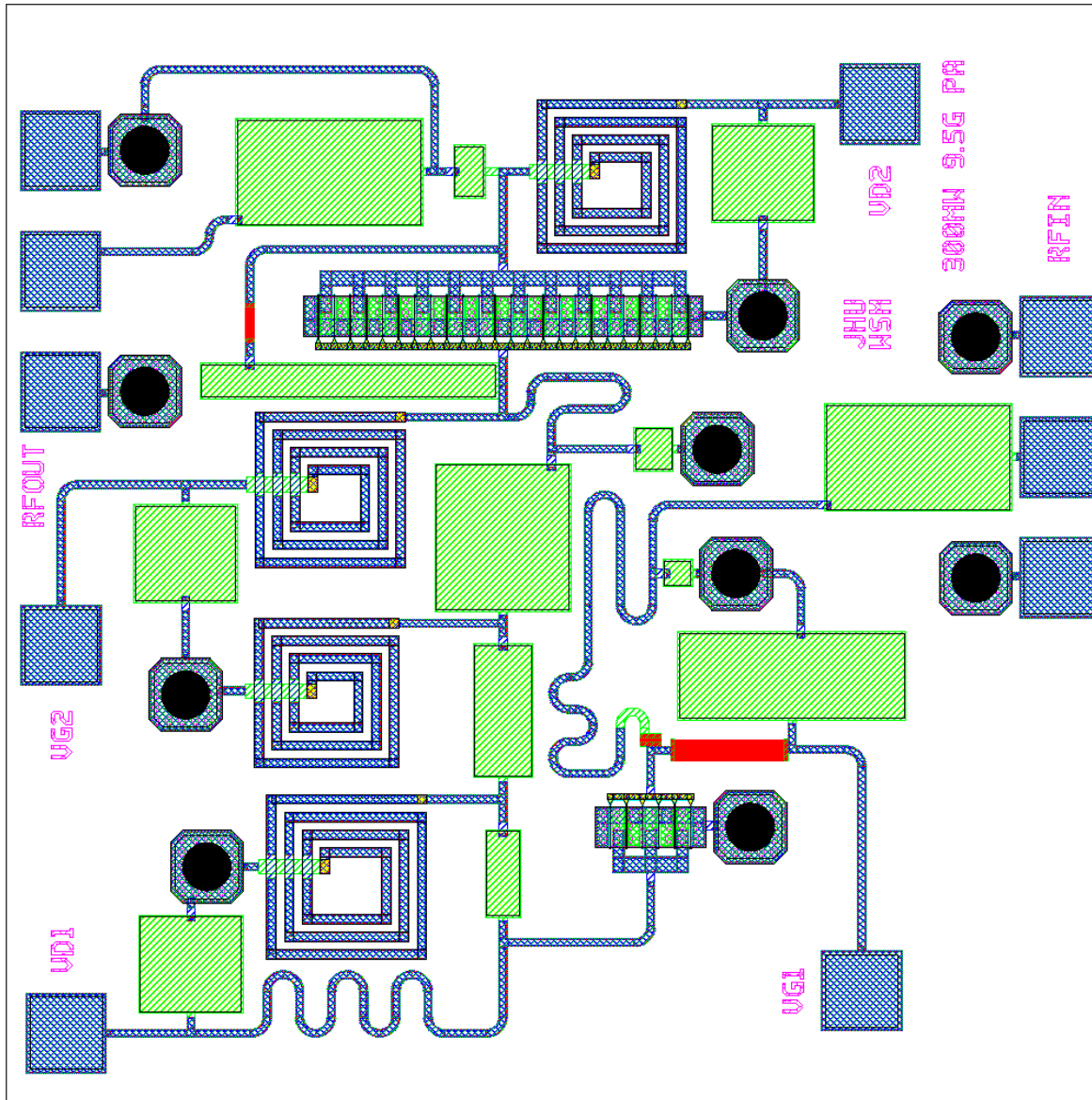


6) Mark Berheimer Vector Modulator (Plot Showing ~QPSK and min. Points 34-40 GHz)



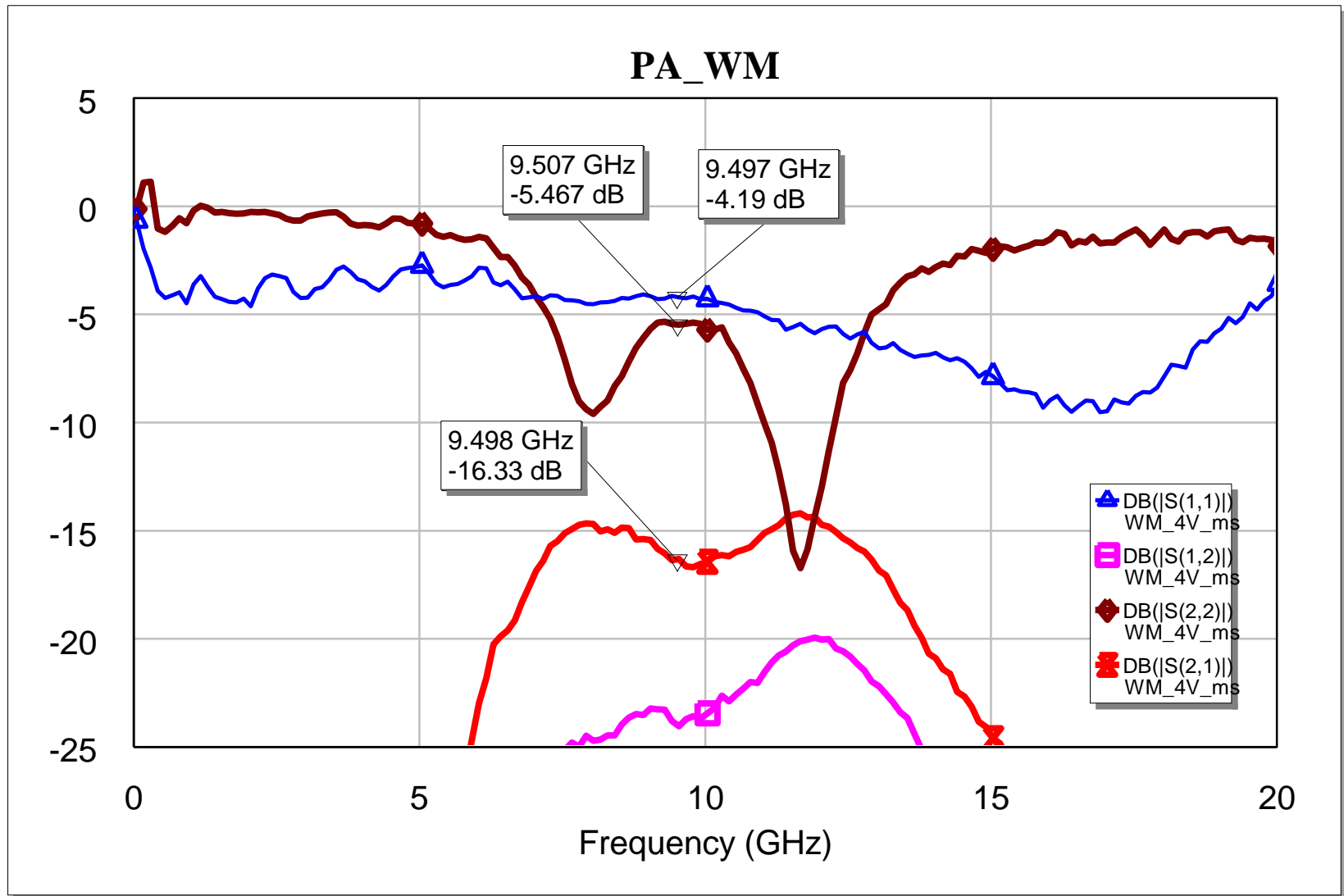
JHU11MB Re-Measured 7/31/12

Tried for "max" swing using +0.5V(P), -0.5V(N), & 0V
Max. swing seemed to be when "Both" diodes were full ON! So NNNN, PPPP, NNPP, PPNN are DC1,2,3,4
NNNN all -0.5V
PPPP all +0.5V
NNPP
PPNN
0000 all 0V
0N0N alternating 0, -0.5V
NON0 alternating -0.5V, 0V
0POP alternating 0, +0.5V
POPO alternating +0.5V, 0V



7) Wayne Miller
 X Band PA
 Another two stage
 amplifier with 4 DC
 bias inputs which
 created difficulty due
 to low frequency
 oscillations. Definitely
 had gain as shown in
 the following
 measurements.
 Achieved > 100 mW
 of output power at
 9.5 GHz.
 Attaching 100pF caps to
 the DC bias inputs
 and retesting would
 probably quell the
 ~30-40MHz
 oscillations.

7) Wayne Miller X Band PA S-parameters (Low Gain due to LF Oscillations?)



7) Wayne Miller

X Band PA

- Difficulty with Low Freq. Oscillations in Test
- Gain seems Low for 2 stage, output match looked OK, input match? Need to record current on 2nd stage for PAE measurement. >100 mW output!

Wayne Miller PA at 9.5 GHz										
Measured at 9.5 GHz 7/26/12					Loss 4.85 dB for thru					
9.5 GHz	Die#1	28 GHz Fall11 TQP13				4V ; 60 mA	1st stage: 3.3V ; ~35 mA?			
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC2(mw)	Pout(mw)	Drn Eff2?	PAE2?	
0.0	2.80	-2.43	5.23	7.66	60	240.0	3.33	1.4	1.2	
2.0	4.60	-0.43	7.03	7.46	64	256.0	5.05	2.0	1.6	
4.0	6.50	1.57	8.93	7.36	67	268.0	7.82	2.9	2.4	
6.0	8.60	3.57	11.03	7.46	71	284.0	12.68	4.5	3.7	
8.0	10.92	5.57	13.35	7.78	76	304.0	21.63	7.1	5.9	
10.0	12.83	7.57	15.26	7.69	81	324.0	33.57	10.4	8.6	
12.0	14.90	9.57	17.33	7.76	90	360.0	54.08	15.0	12.5	
13.0	15.96	10.57	18.39	7.82	97	388.0	69.02	17.8	14.9	
14.0	17.20	11.57	19.63	8.06	104	416.0	91.83	22.1	18.6	
15.0	17.80	12.57	20.23	7.66	112	448.0	105.44	23.5	19.5	
16.0	18.20	13.57	20.63	7.06	115	460.0	115.61	25.1	20.2	

Notes:

corr—corrected

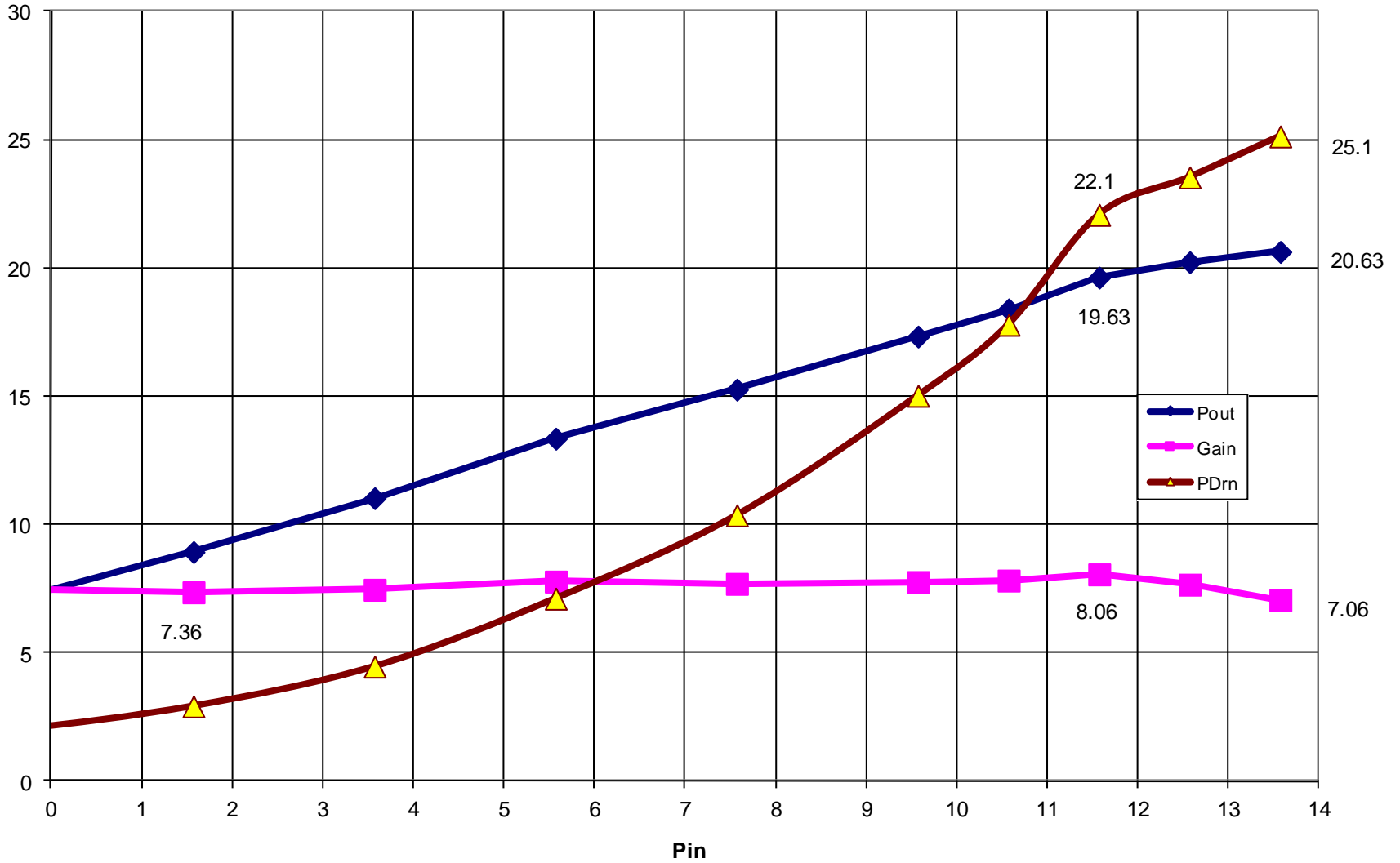
SG—Signal Generator

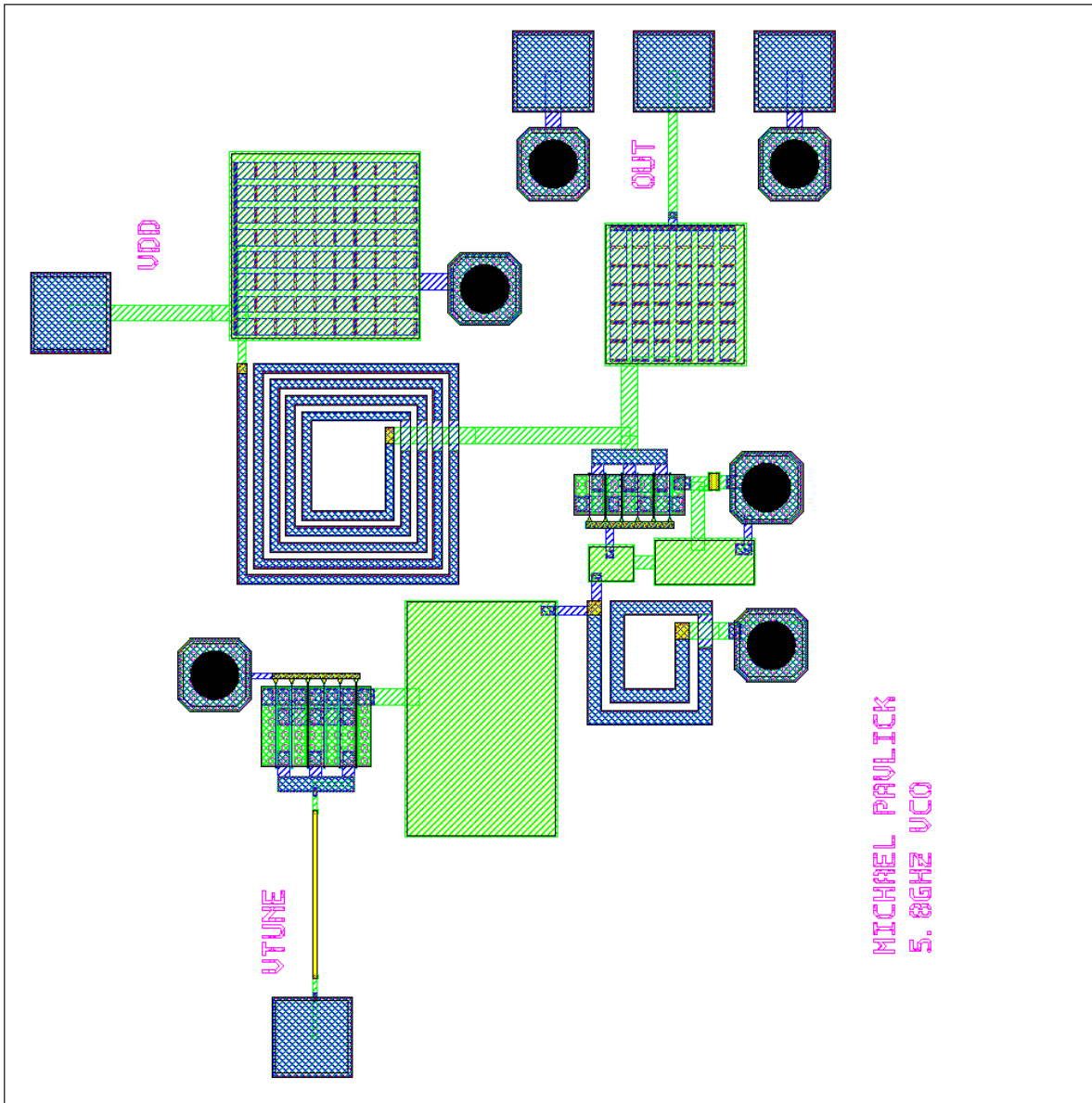
SA—Spectrum Analyzer

7) Wayne Miller X Band PA

* Difficulty with Low Freq. Oscillations in Test

WM 9.5Hz Meas 11
4V ~60mA 2nd stage + 3.3V ~35mA 1st stage

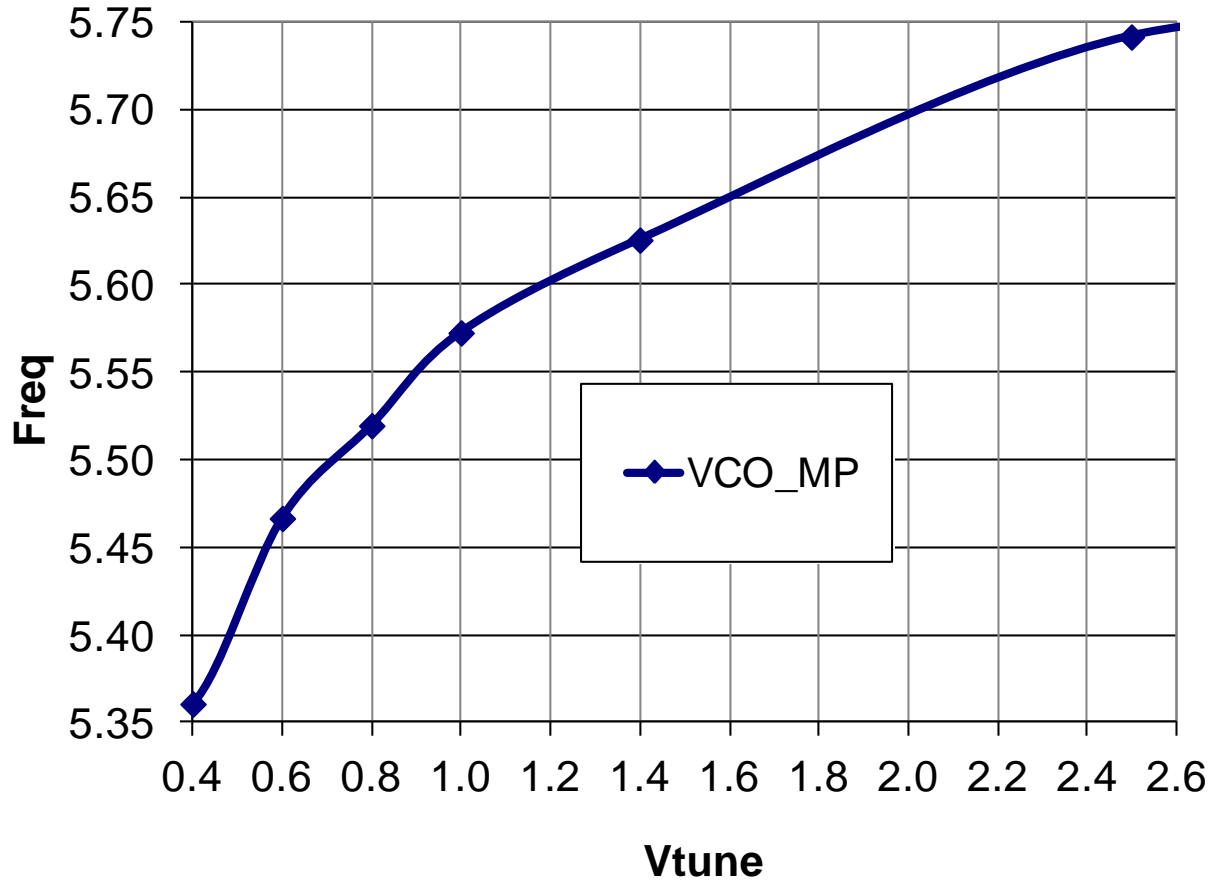




MICHAEL PAVLICK
5.8GHZ VCO

8) Mike Pavlick
VCO
VCO worked great!
Very close to
expected frequency
with a decent
tuning range.

MP VCO Freq vs. Tune Voltage

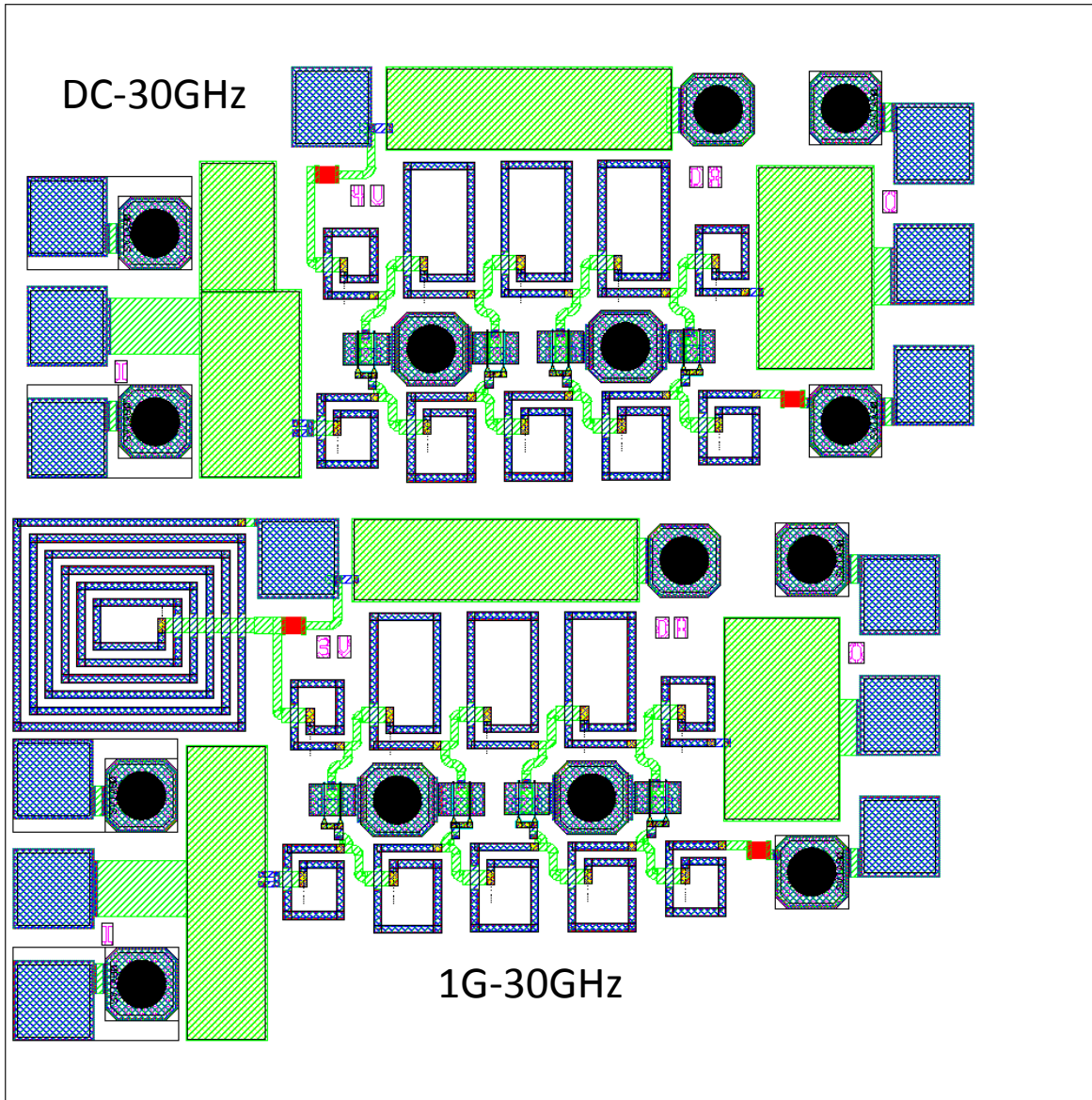


8) Mike Pavlick VCO

VCO	3.3V at 10mA		Die #2
VBias (V)	Freq (GHz)	Pout(ms)	Pout(corr)
0.2	5.361	-18.7	-16.9
0.4	5.361	1.9	3.8
0.6	5.467	1.3	3.1
0.8	5.520	1.7	3.6
1.0	5.573	3.3	5.2
1.4	5.626	2.2	4.0
2.5	5.742	1.2	3.0
3.5	5.746	2.2	4.0

Notes:
 ms—measured
 corr—corrected

Measured MWO VCO 5.8 GHz Fall 11			
Michael Pavlick			
7/17/2012			
Oscillated at Higher Biases, but not low Bias voltages			



9) JEP

Distributed Amp(s)

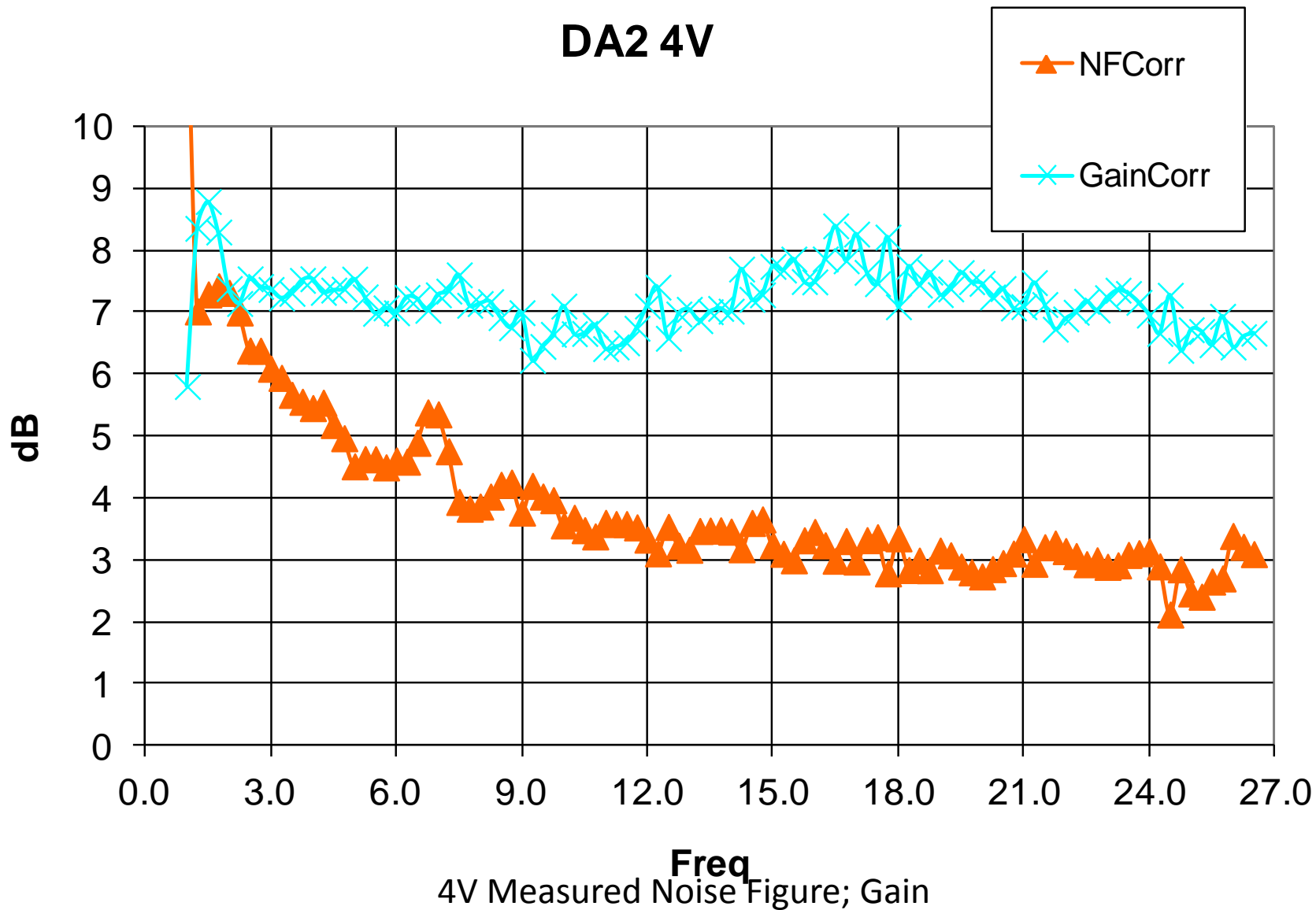
4V 30 mA (1 DC, 2RF)

3V 30 mA (1 DC, 2RF)

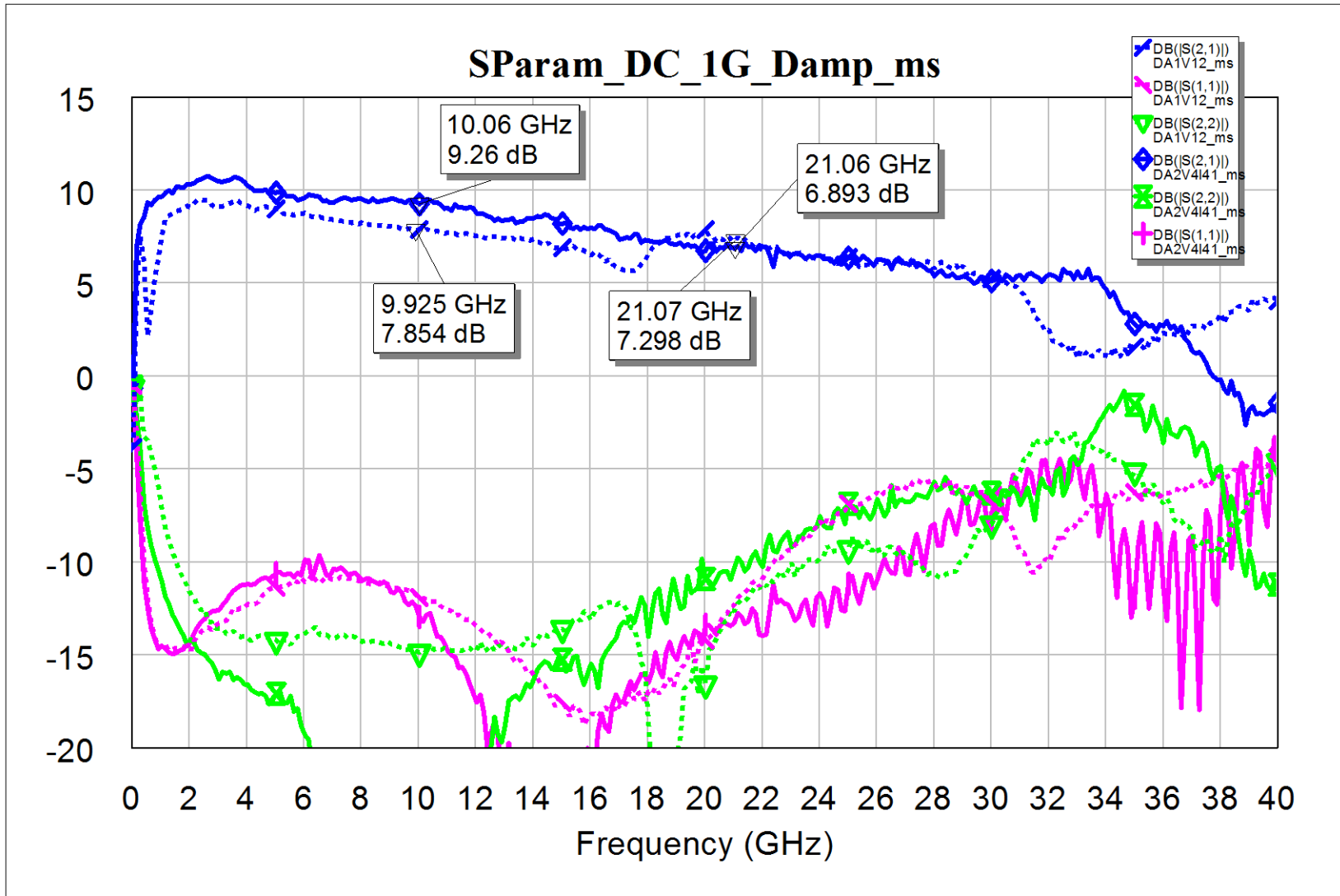
Initial simulations of Distributed Amplifier using Sonnet EM hinted at possible oscillation problems around 30 GHz. Resistors were supposed to have been added to the drains of the PHEMTs to reduce this possible problem, but inadvertently the original design was fabbed instead of the “fixed” version. The result in both similar designs is marginal stability problems around 45 GHz at some DC biases. Not clear if the ‘fixed’ version would have helped with this higher freq. issue or not.

Measured Results (DC-30G)

DA2 4V



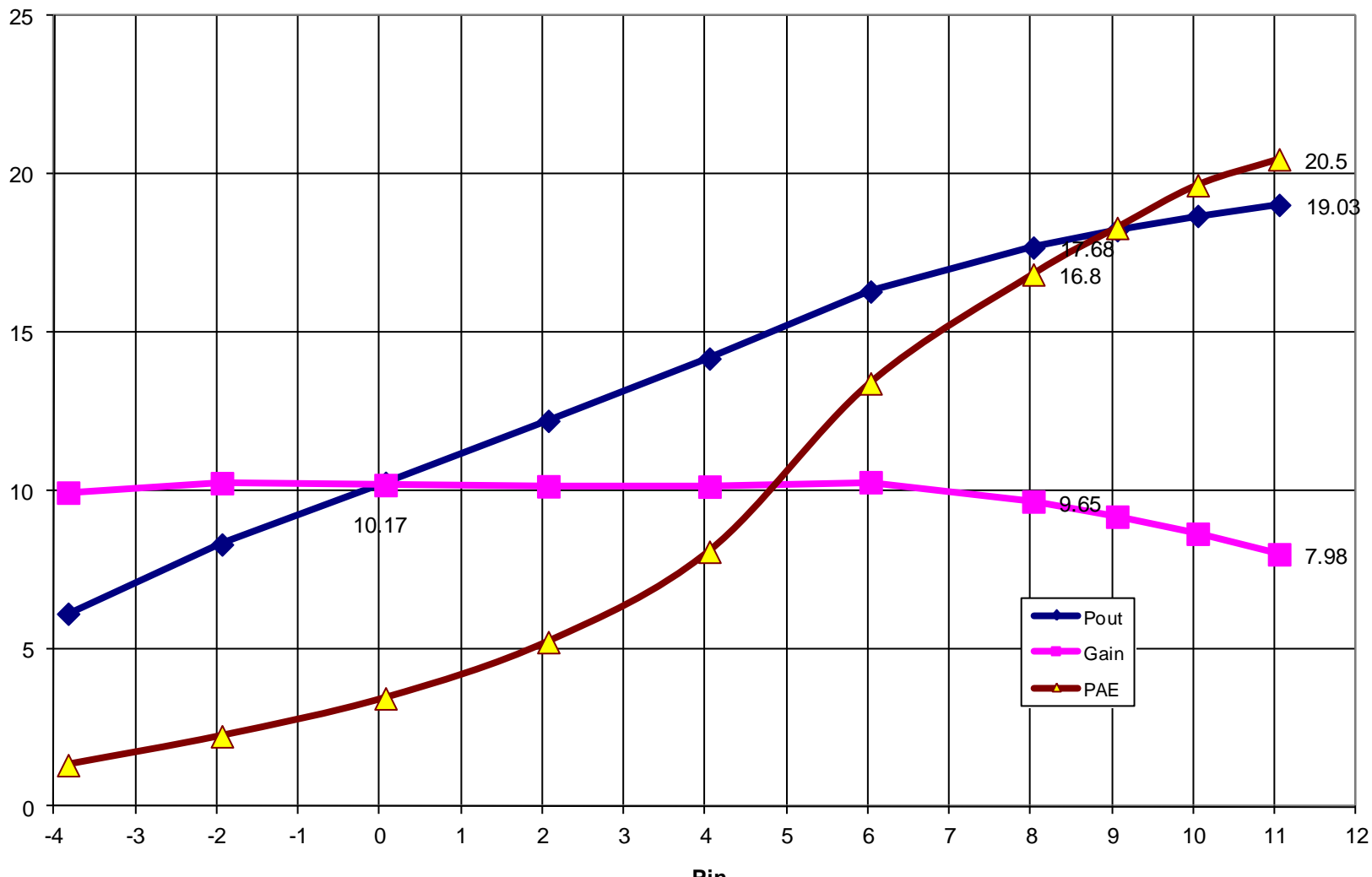
Measured Results (Both)



1.2V 1G; 4V DC; Similar Designs Except Bias

Measured Results (1G-30G)

DA1 10GHz Meas 11
4.5V ~43mA



No Oscillations at 4.5V DC; 1G-30GHz Dist. Amp at 10 GHz

Measured Results (1G-30G)

Higher DC bias, no oscillations!							
10 GHz	Die#1	DA1 4.5V 10 GHz Fall11 TQP13				4.5V ; 61 mA	
Pin(corr)	Pout(corr)	Gain	I1(4.5V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-3.83	6.10	9.93	62	279.0	4.07	1.5	1.3
-1.94	8.29	10.23	61	274.5	6.75	2.5	2.2
0.07	10.24	10.17	62	279.0	10.57	3.8	3.4
2.07	12.20	10.13	64	288.0	16.60	5.8	5.2
4.05	14.17	10.12	65	292.5	26.12	8.9	8.1
6.03	16.29	10.26	64	288.0	42.56	14.8	13.4
8.03	17.68	9.65	69	310.5	58.61	18.9	16.8
9.06	18.23	9.17	71	319.5	66.53	20.8	18.3
10.05	18.68	8.63	72	324.0	73.79	22.8	19.7
11.05	19.03	7.98	73	328.5	79.98	24.3	20.5

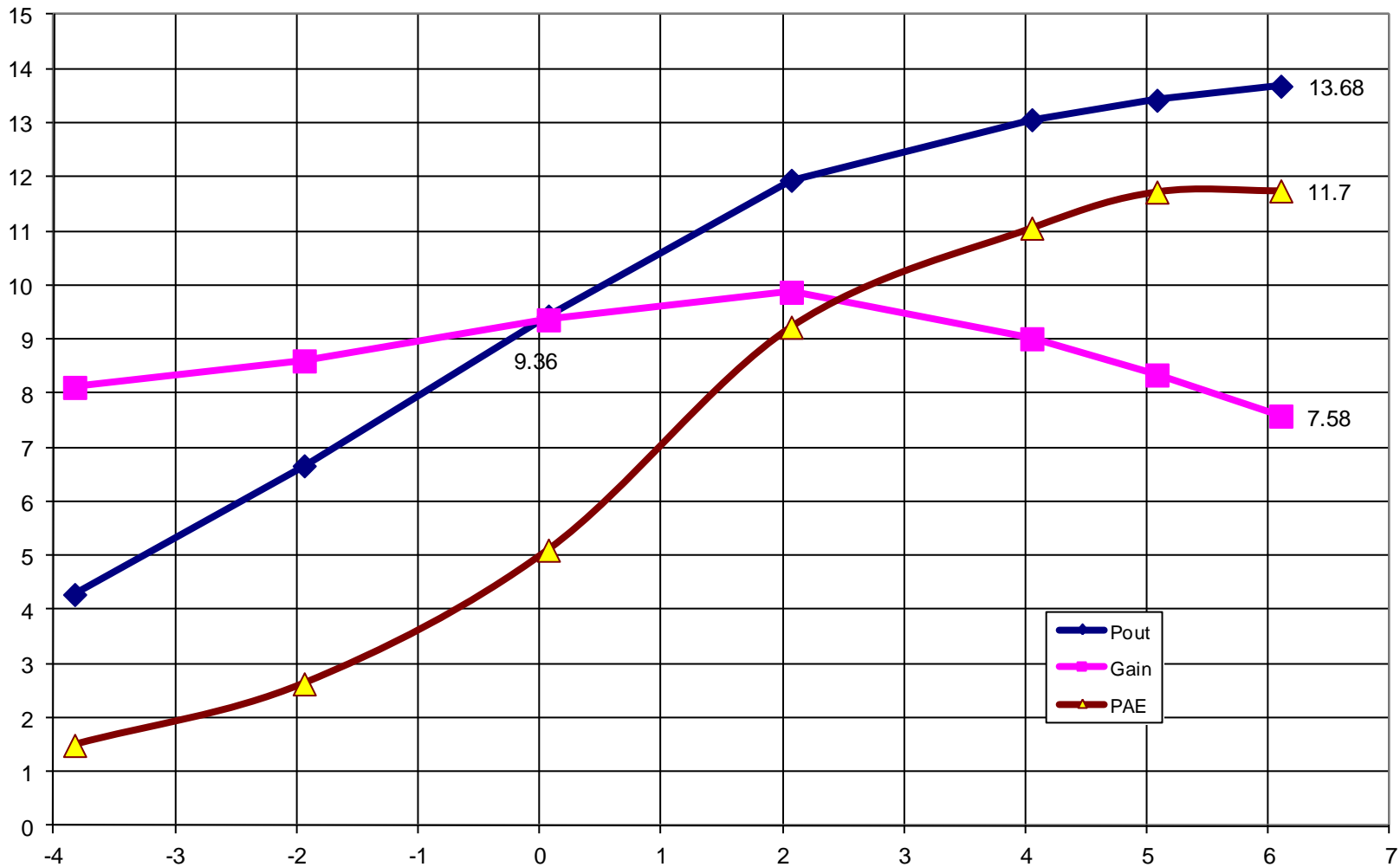
Notes:

corr—corrected

No Oscillations at 4.5V DC; 1G-30GHz Dist. Amp at 10 GHz

Measured Results (DC-30G)

DA2 10GHz Meas 11
4V ~38mA



No Oscillations at 4.0V DC; DC-30GHz Dist. Amp at 10 GHz

Measured Results (DC-30G)

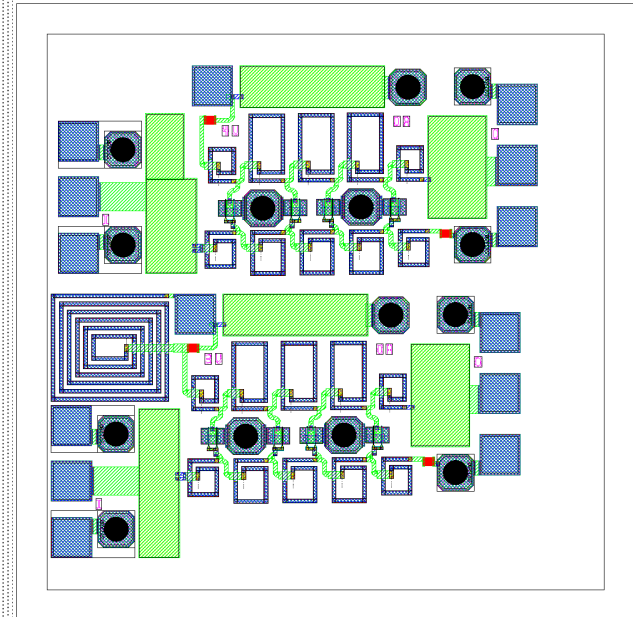
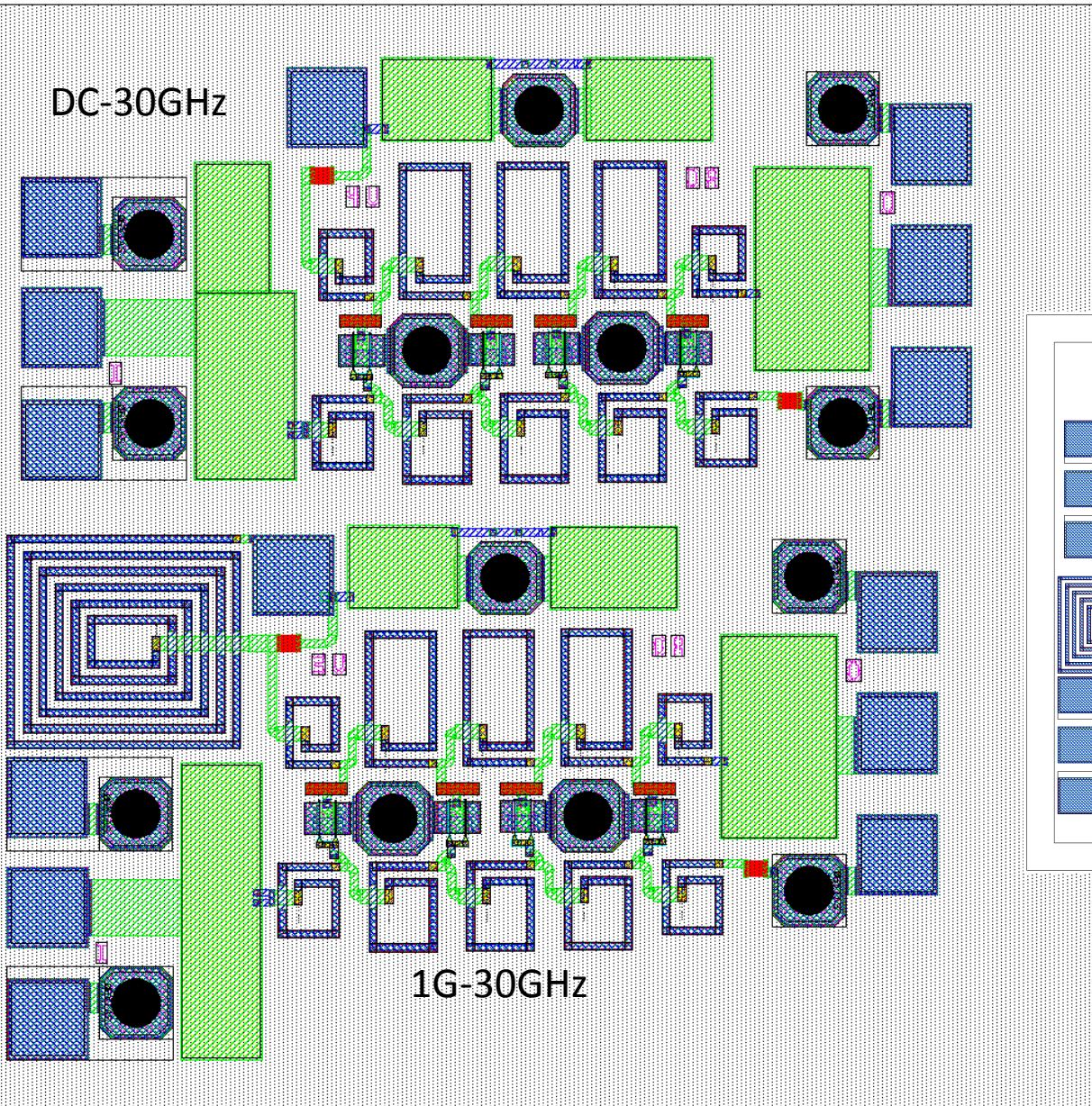
DA1 DC-30GHz 3V Bot		Re-Measured 8/10/12						
DA2 1-30GHz 4V Top		ARL		Loss 3.1 dB for thru				
10 GHz	Die#1	DA2 4V 10 GHz Fall11 TQP13				4V ; 43 mA		
Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-3.83	4.28	8.11	38	152.0	2.68	1.8	1.5	
-1.94	6.66	8.60	38	152.0	4.63	3.0	2.6	
0.07	9.43	9.36	38	152.0	8.77	5.8	5.1	
2.07	11.94	9.87	38	152.0	15.63	10.3	9.2	
4.05	13.06	9.01	40	160.0	20.23	12.6	11.1	
5.08	13.42	8.34	40	160.0	21.98	13.7	11.7	
6.10	13.68	7.58	41	164.0	23.33	14.2	11.7	

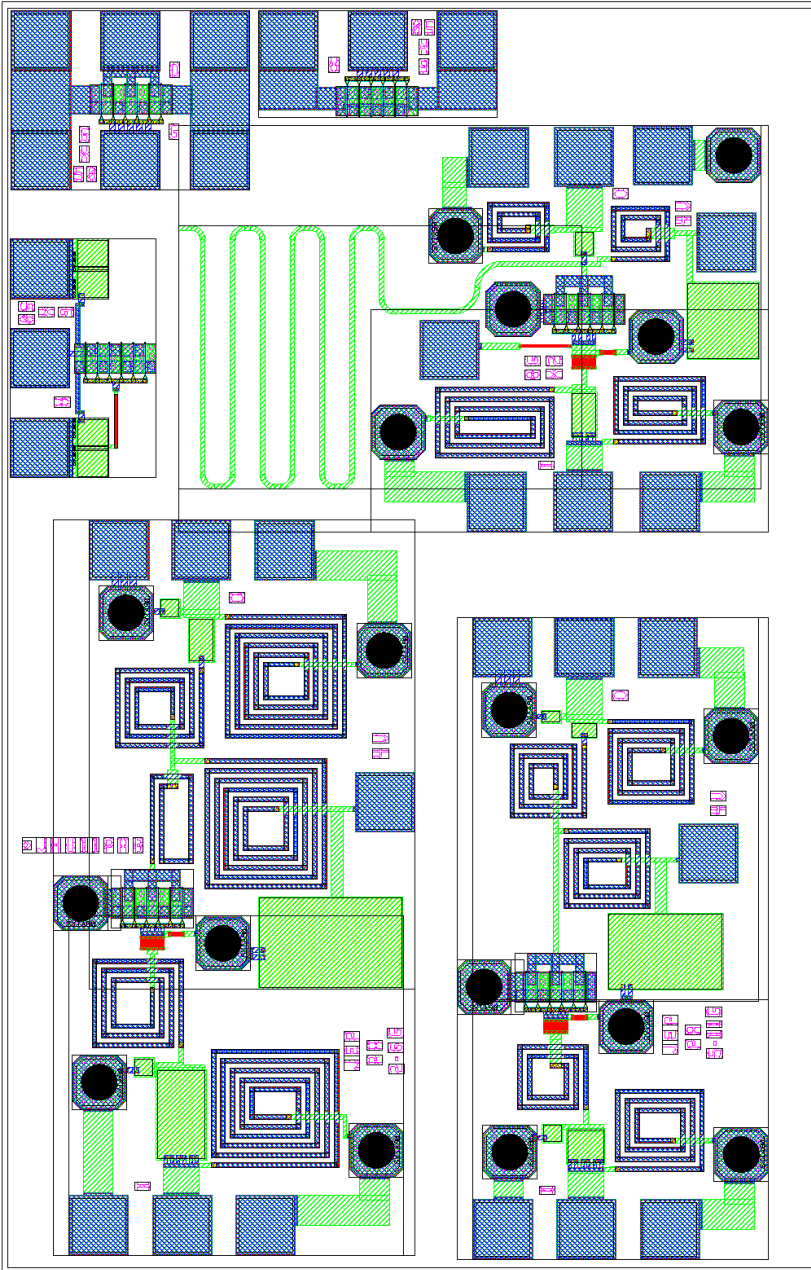
Notes:

corr—corrected

No Oscillations at 4.0V DC; DC-30GHz Dist. Amp at 10 GHz

9) JEP *Should have fabbed this one!
Distributed Amp(s) V2
4V 30 mA (1 DC, 2RF)
3V 30 mA (1 DC, 2RF)





10) JHU11PAB -- JEP

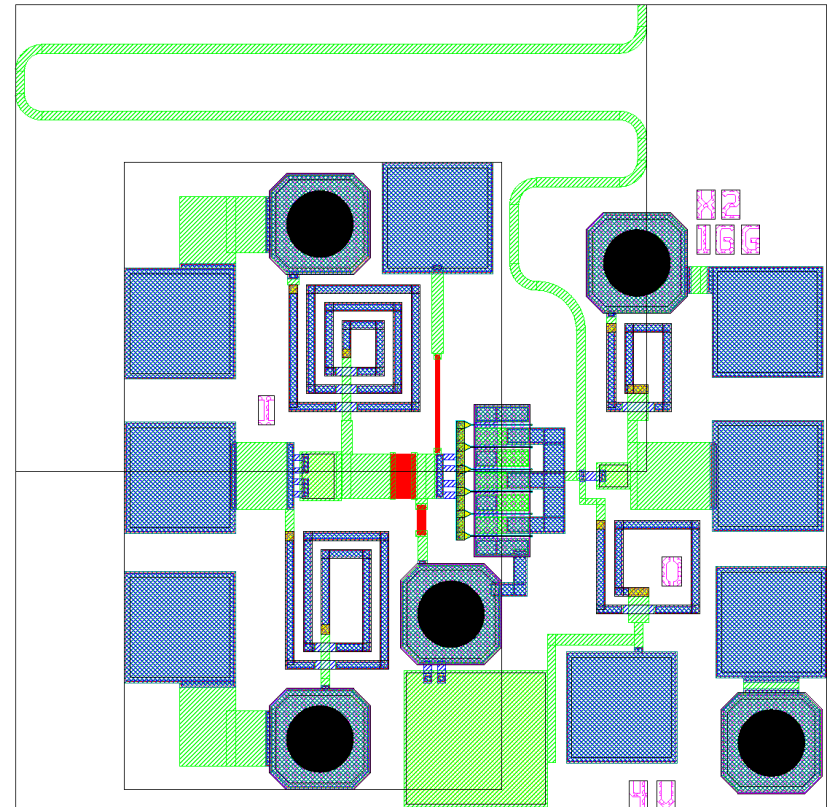
BB 2-6, 5-11 GHz PA

X2 8 GHz

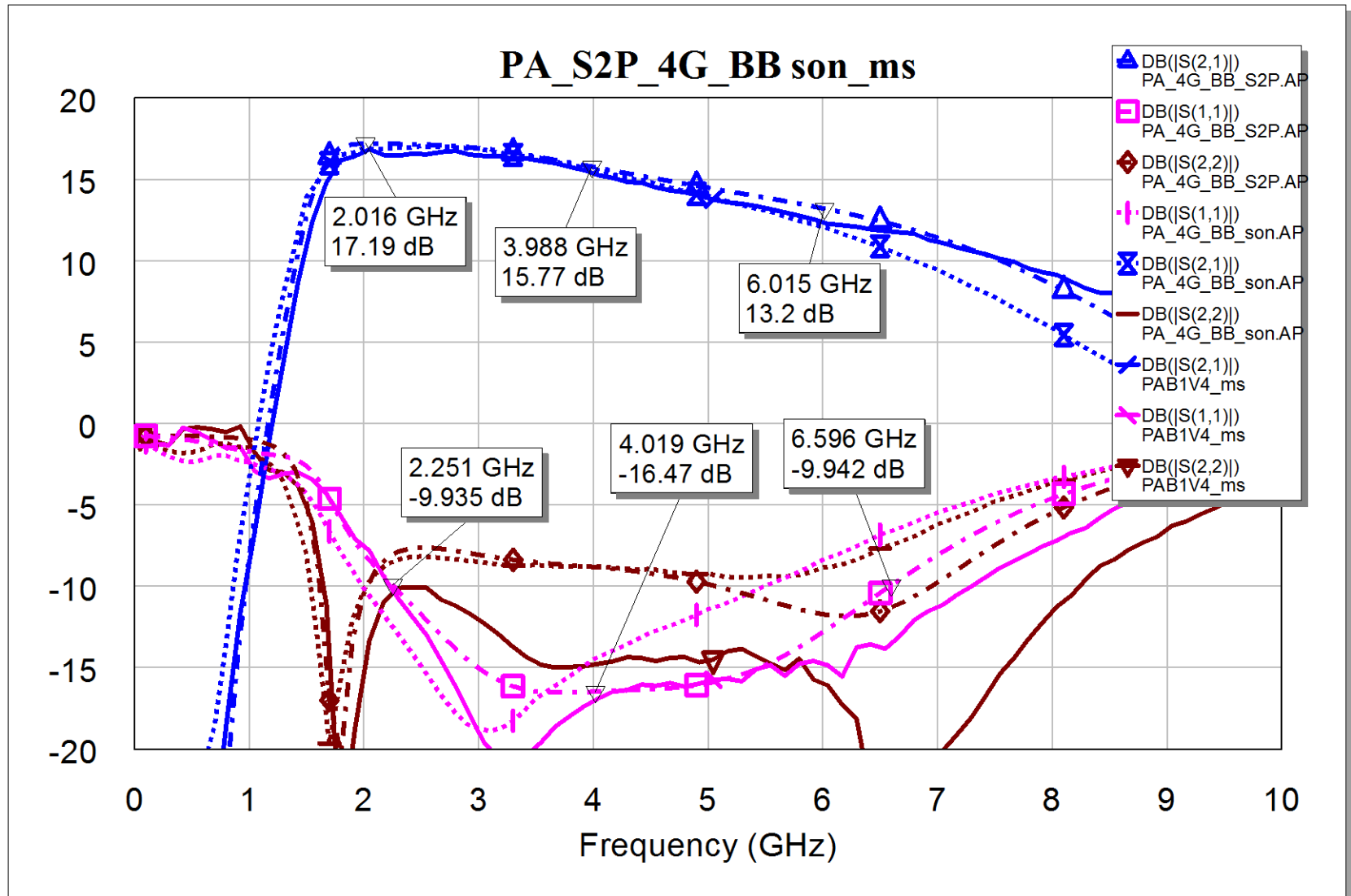
4V 35-55 mA (1 DC, 2RF)

4V 35-55 mA (1 DC, 2RF)

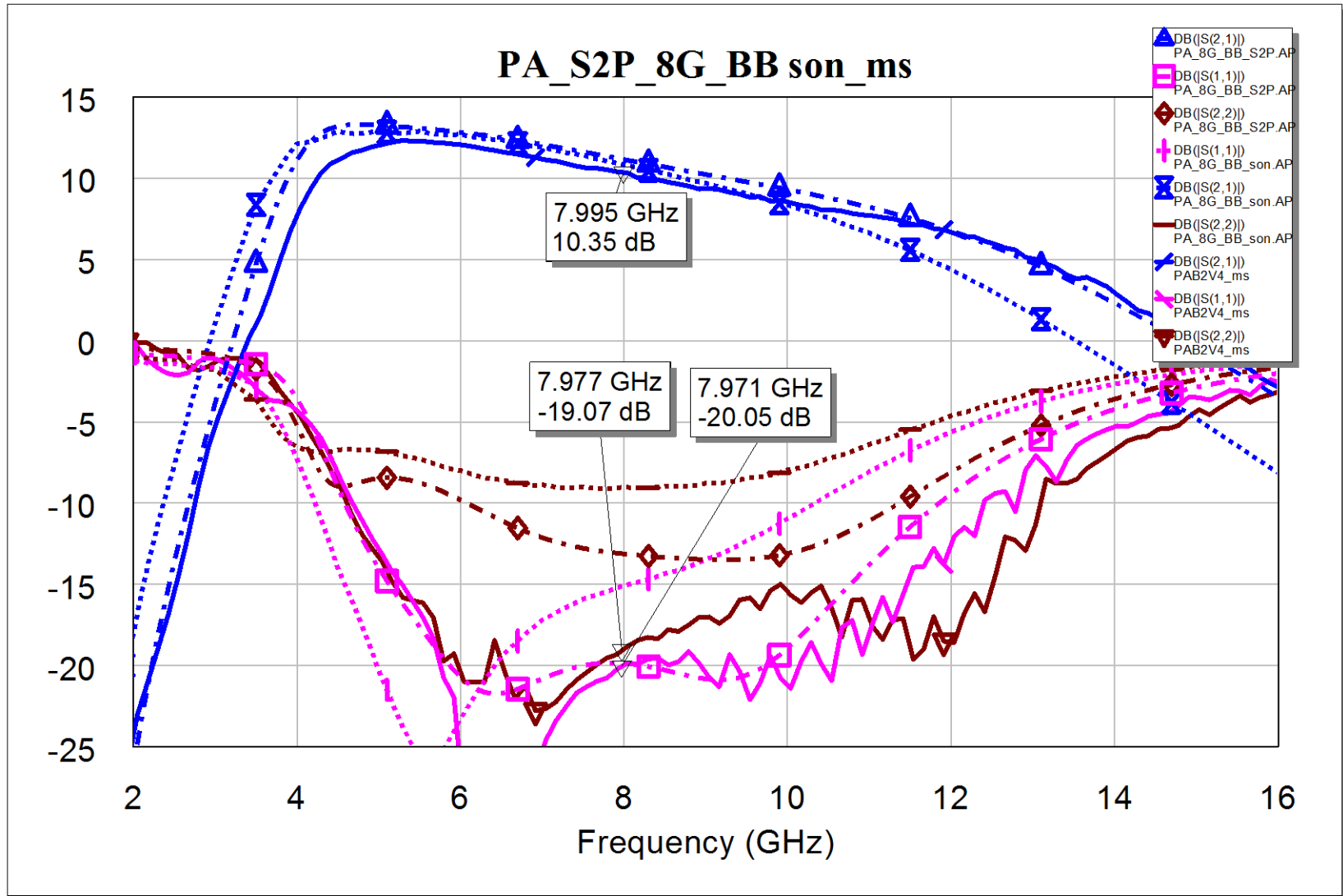
4V 35-55 mA (1 DC, 2RF)



Broadband PA 2-6GHz—Measured vs. Sonnet, AWR



Broadband PA 5-11GHz—Measured vs. Sonnet, AWR



Frequency Doubler 8 to 16 GHz

Measured 7.5, 8, 8.5 Ghz Input

7/11/2012		4.6 dB loss thru				
Doubler 8G		4V at 47mA, vg=0v		Die #1		
SG	Pin(corr)	Pout8G(m	Pout16G(ms)	Pout(corr)	Pout2X(corr)	Cnvloss
6.0	3.7	7.2	-14.0	9.5	-10.5	14.2
8.0	5.7	9.0	-10.1	11.3	-6.6	12.3
10.0	7.7	10.6	-6.2	12.9	-2.7	10.4
12.0	9.7	11.9	-3.3	14.2	0.3	9.5
14.0	11.7	12.9	-1.0	15.2	2.5	9.2
16.0	13.7	13.6	1.2	15.9	4.7	9.0

Doubler 8G		4V at 40mA, vg=-3v		Die #1		
SG	Pin(corr)	Pout8G(m	Pout16G(ms)	Pout(corr)	Pout2X(cc	Cnvloss
6.0	3.7	6.5	-12.7	8.8	-9.2	12.9
8.0	5.7	8.3	-8.4	10.6	-4.9	10.6
10.0	7.7	10.0	-4.4	12.3	-0.9	8.6
12.0	9.7	11.5	-1.8	13.8	1.7	8.0
14.0	11.7	12.7	0.0	15.0	3.5	8.2
16.0	13.7	13.5	1.7	15.8	5.2	8.5

Notes:

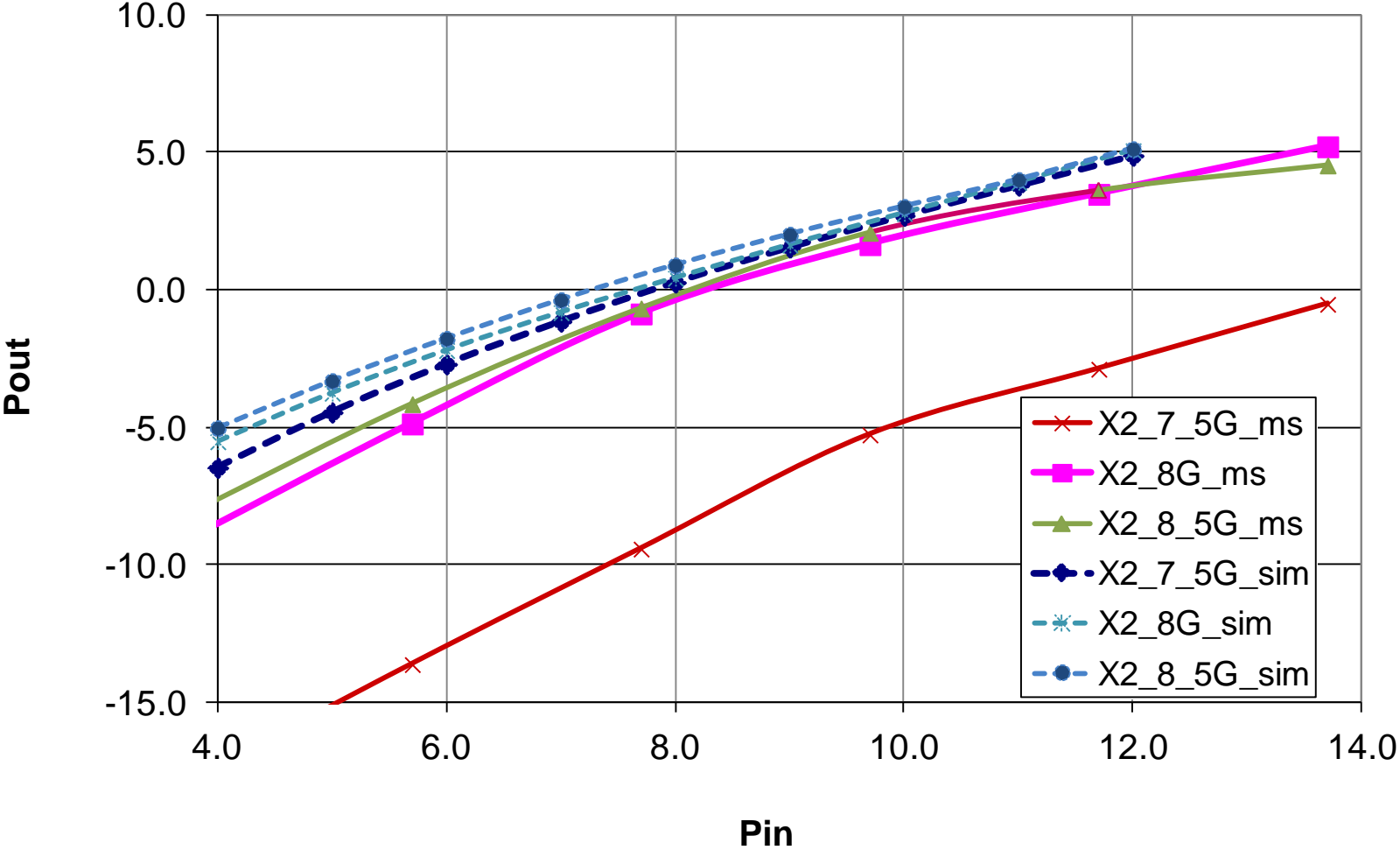
- ms--measured
- corr--corrected
- Pout--Fundamental
- Pout2X--2nd Harmonic
- Cnvloss--2nd Harm Conversion Loss

8.5 GHz						
Doubler 8G		4V at 40mA, vg=-3v		Die #1		
SG	Pin(corr)	Pout8G(m	Pout16G(r	Pout(corr)	Pout2X(cc	Cnvloss
6.0	3.7	7.5	-11.8	9.8	-8.3	12.0
8.0	5.7	9.2	-7.6	11.5	-4.1	9.8
10.0	7.7	10.8	-4.2	13.1	-0.7	8.4
12.0	9.7	12.4	-1.4	14.7	2.1	7.6
14.0	11.7	13.7	0.1	16.0	3.6	8.1
16.0	13.7	14.7	1.1	17.0	4.6	9.2

7.5 GHz						
Doubler 8G		4V at 40mA, vg=-3v		Die #1		
SG	Pin(corr)	Pout8G(m	Pout16G(r	Pout(corr)	Pout2X(cc	Cnvloss
6.0	3.7	4.9	-21.5	7.2	-18.0	21.7
8.0	5.7	6.9	-17.1	9.2	-13.6	19.3
10.0	7.7	9.0	-12.9	11.3	-9.4	17.1
12.0	9.7	10.9	-8.8	13.2	-5.3	15.0
14.0	11.7	12.4	-6.4	14.7	-2.9	14.6
16.0	13.7	13.4	-4.0	15.7	-0.5	14.2

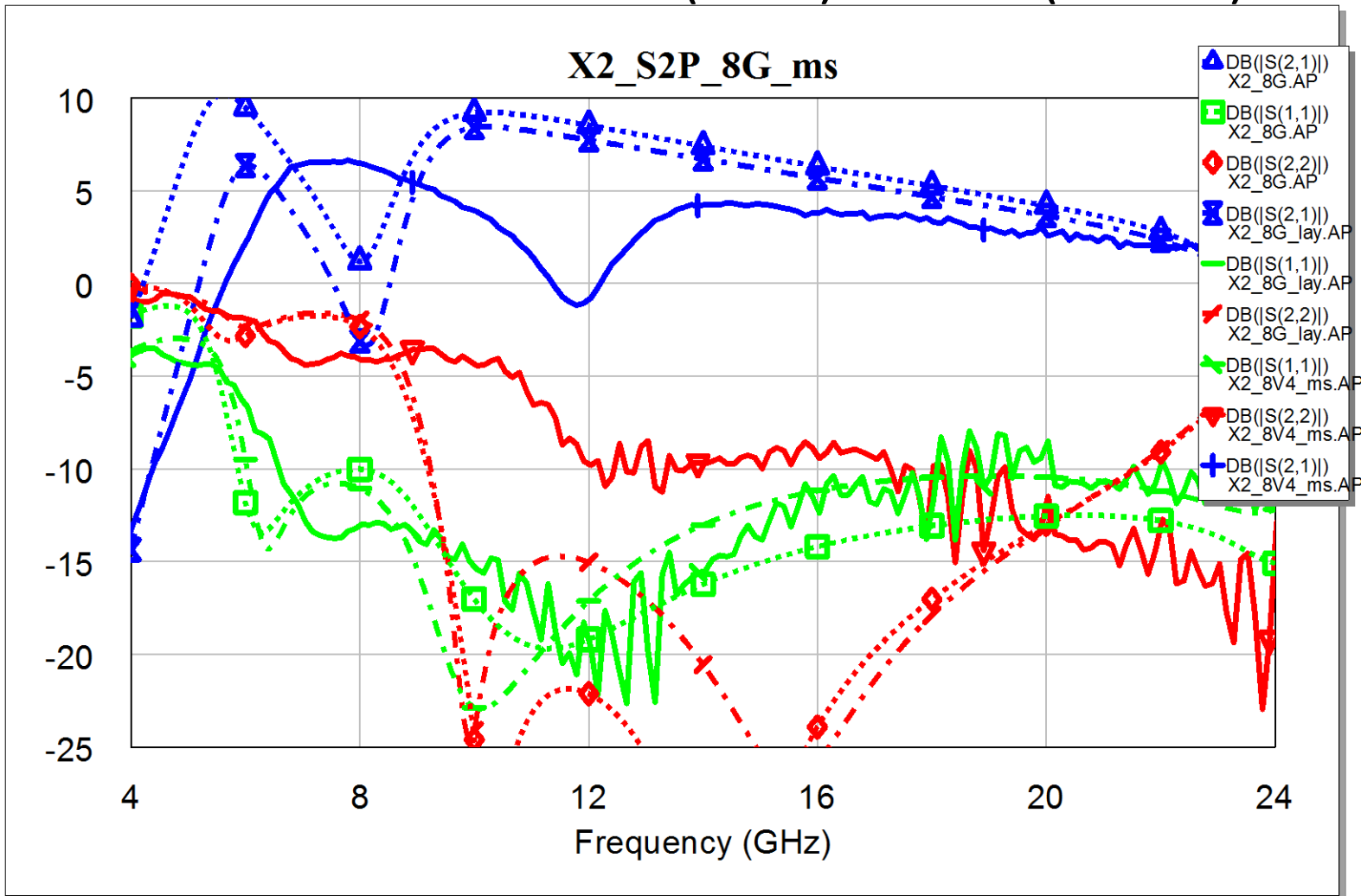
Frequency Doubler 8 to 16 GHz

Measured 7.5, 8, & 8.5 GHz Input
X2 8 GHz P2X vs. P1In Meas/Sim 7/11/12



Frequency Doubler 8 to 16 GHz

Measured S-Parameters (solid) vs. Sim (dotted)



11) JHU11PL8 -- JEP

8 GHz PA, LNA

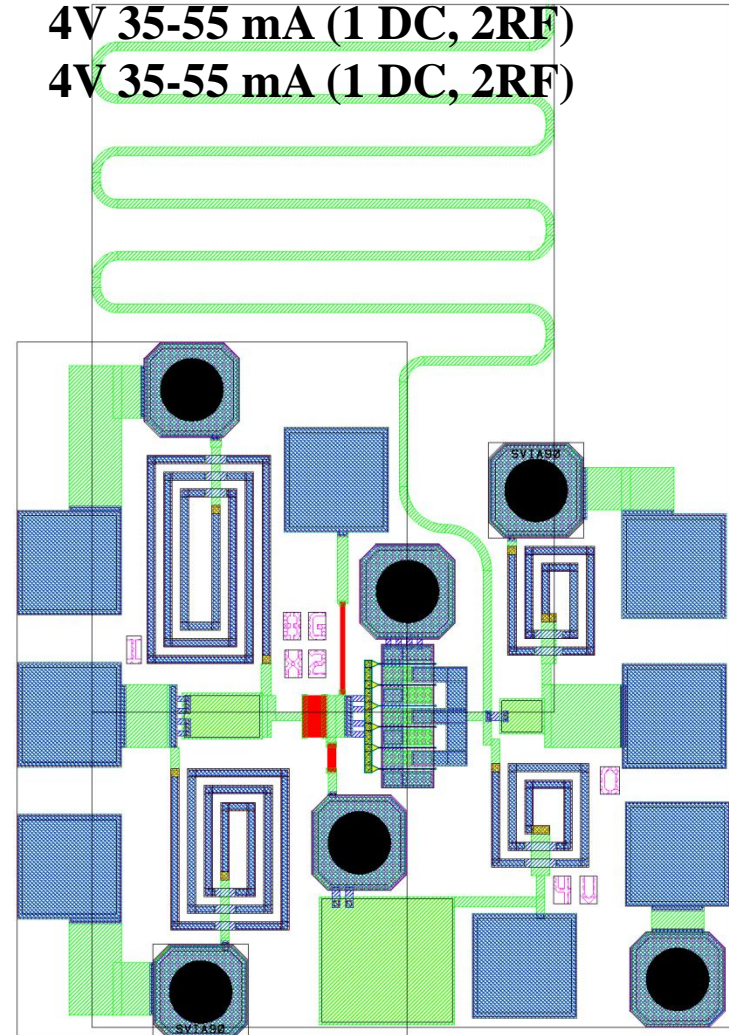
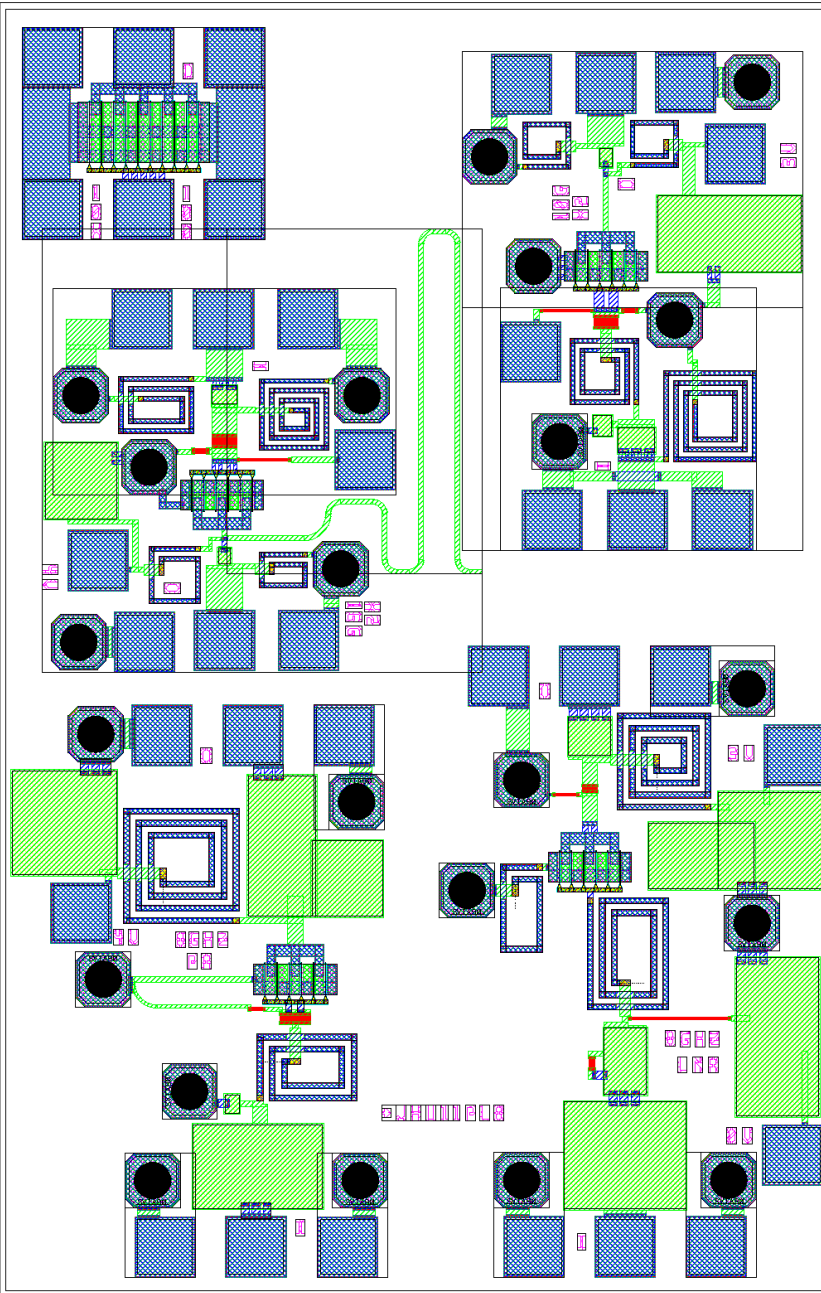
X2 10, 16 GHz

4V 35 mA (1 DC, 2RF)

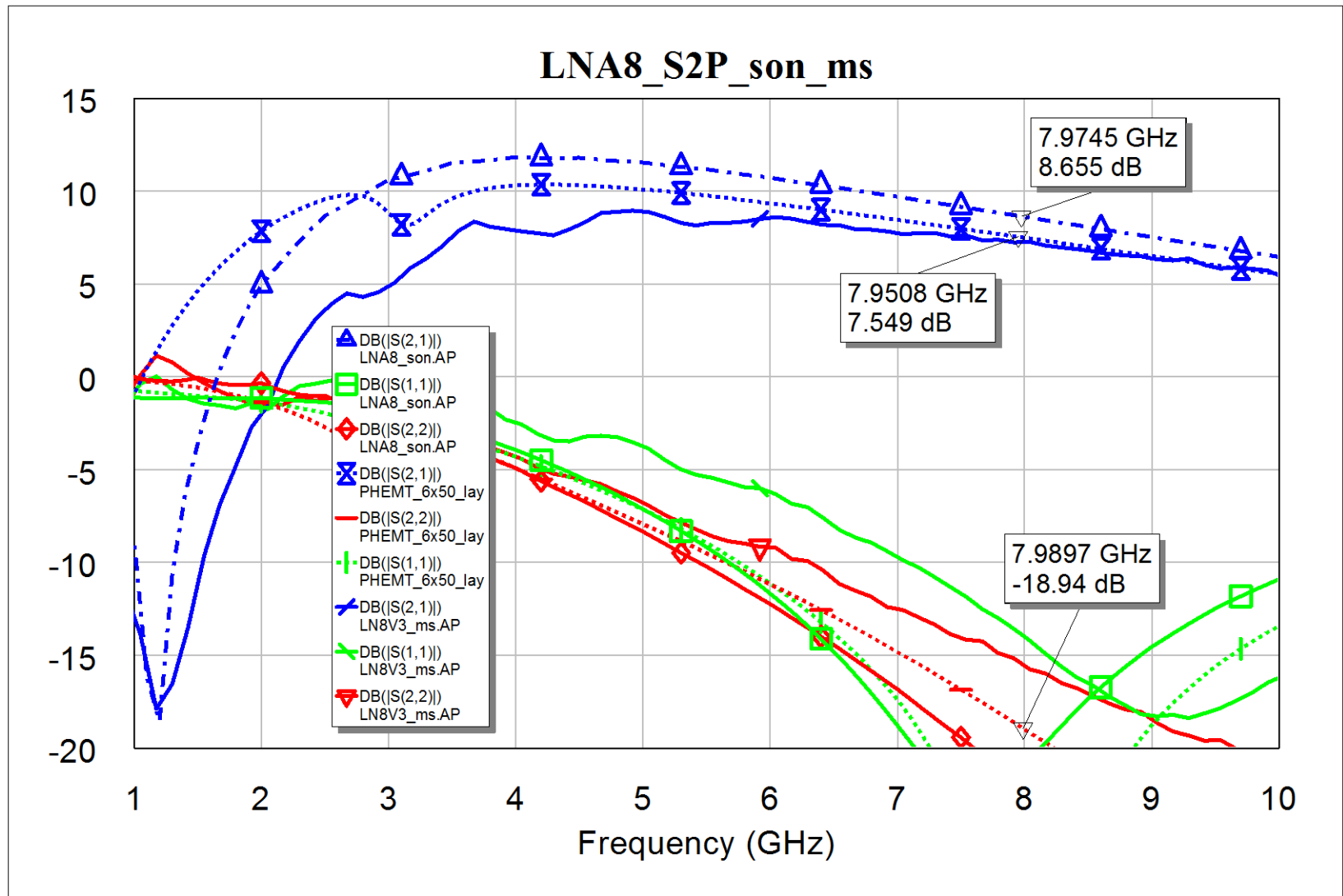
3V 27 mA (1 DC, 2RF)

4V 35-55 mA (1 DC, 2RF)

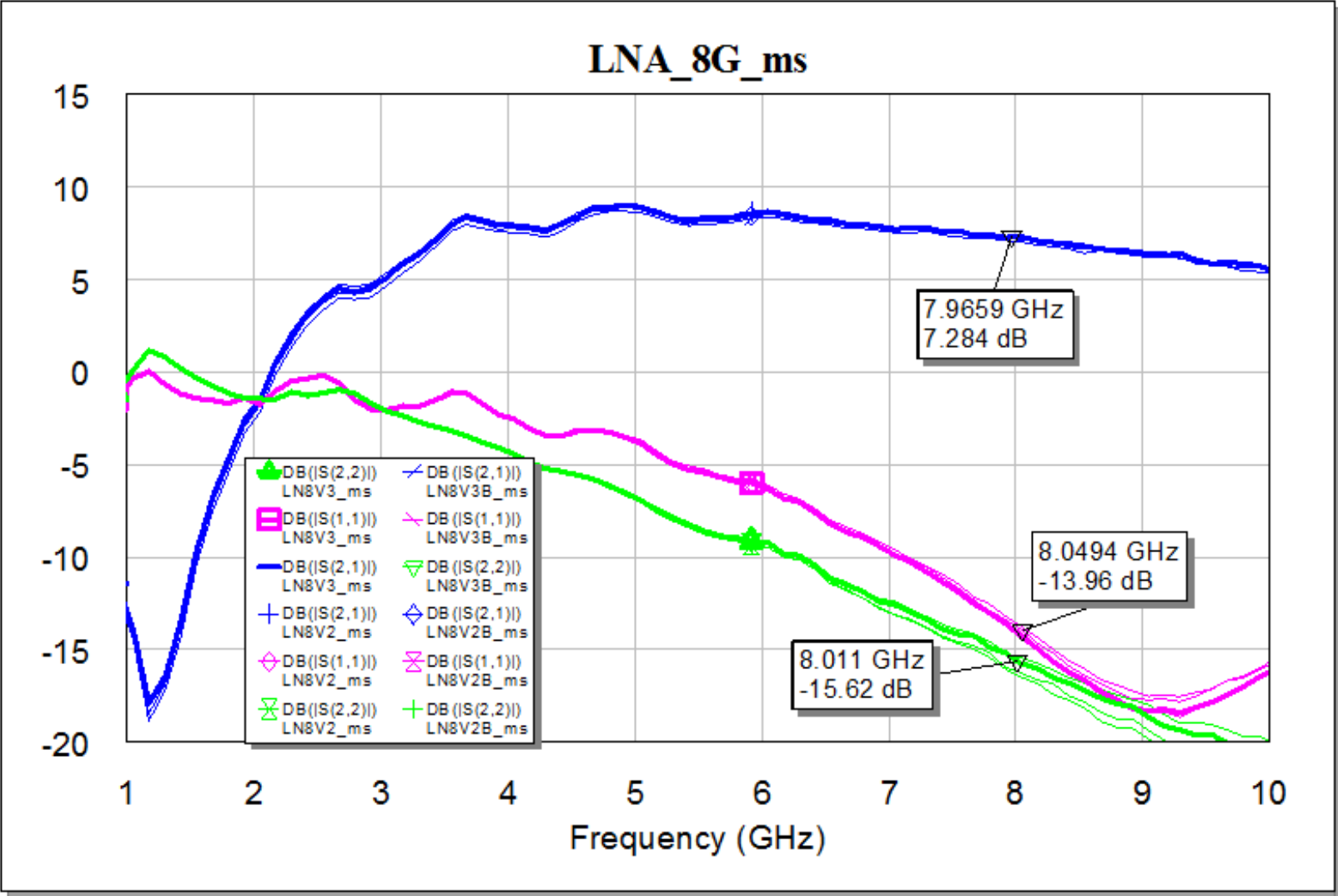
4V 35-55 mA (1 DC, 2RF)



LNA 8GHz—Measured vs. Sonnet, AWR

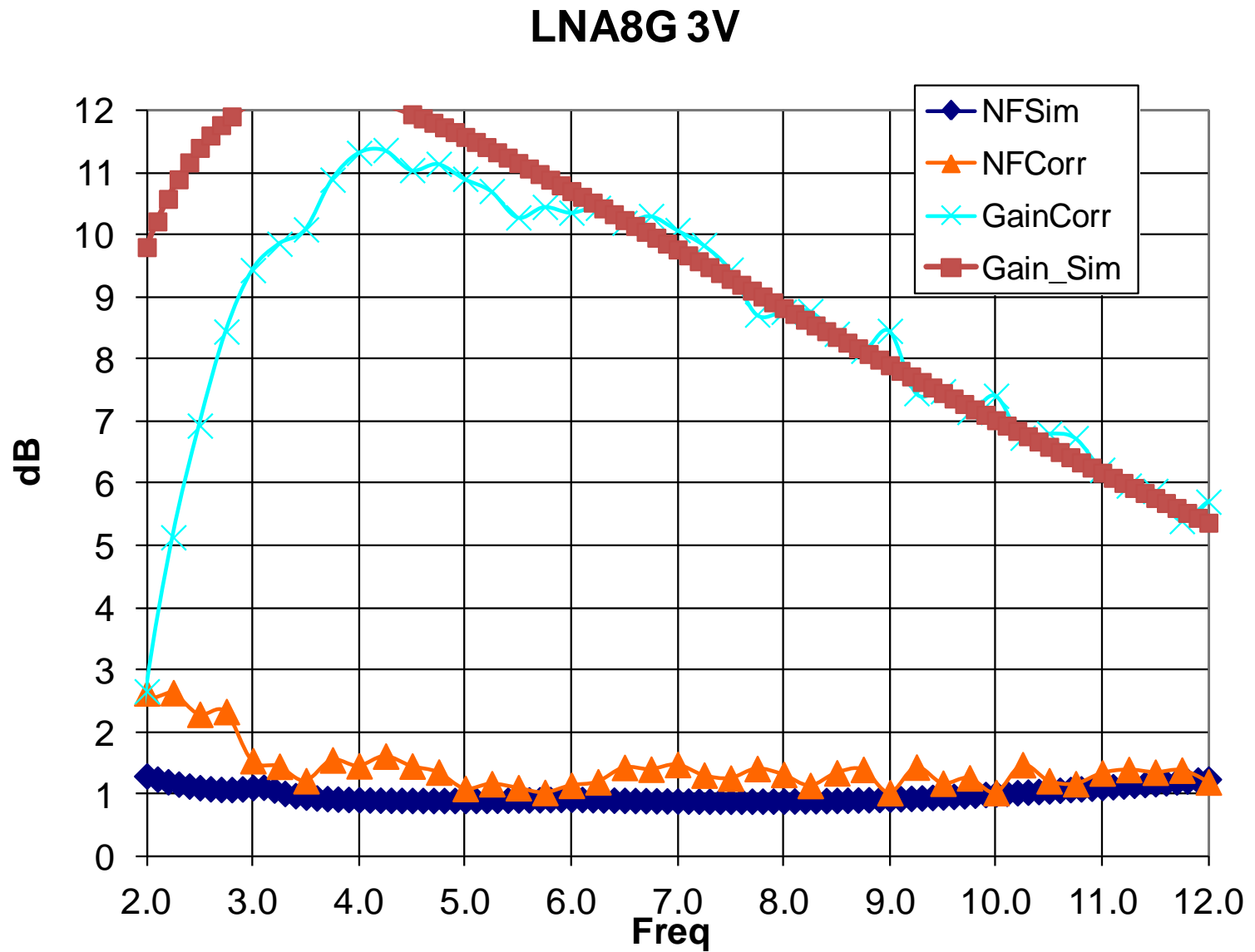


LNA 8GHz—Measured 2V, 3V, and two Die

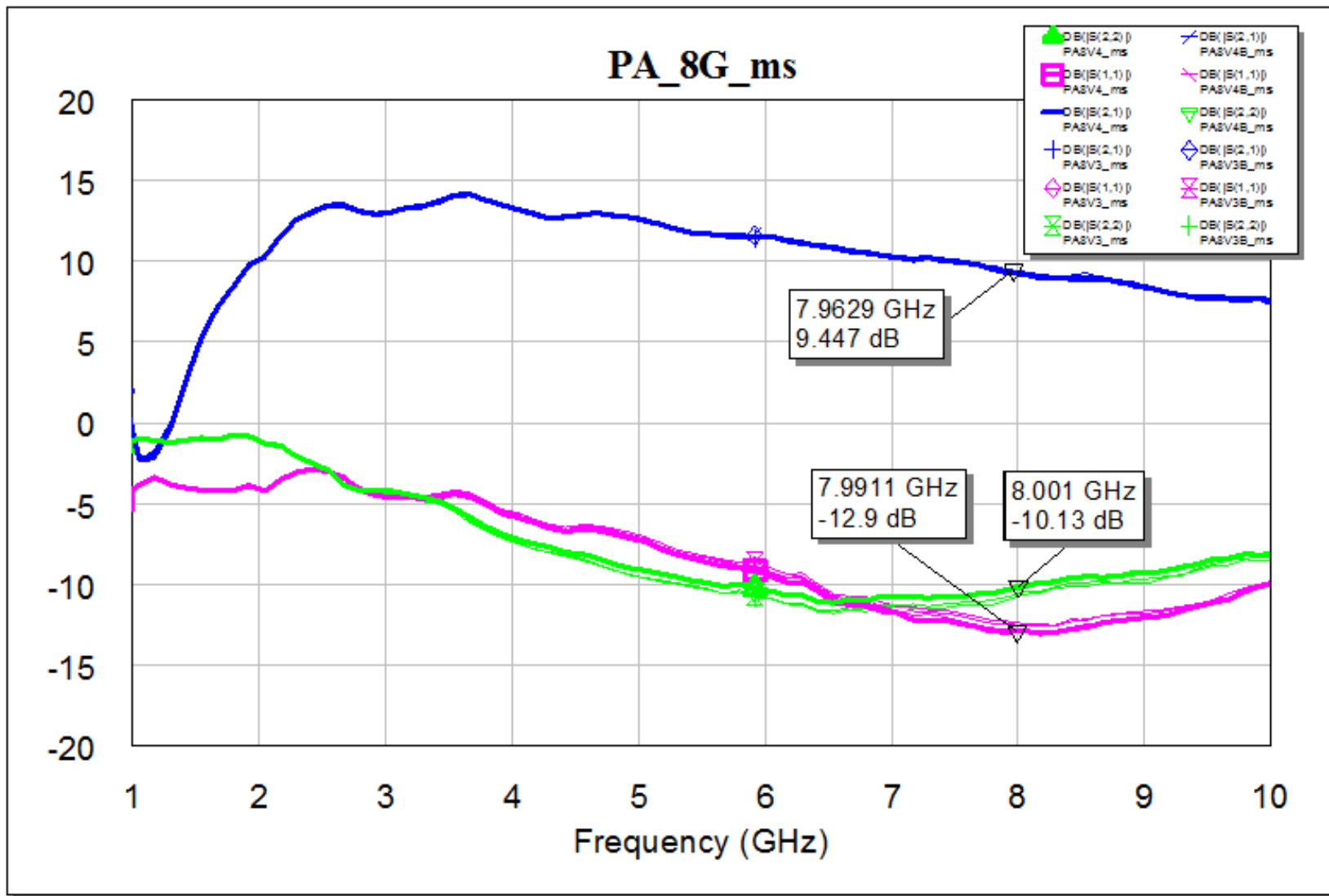


Blue-S21, Green-S22, Magenta-S11; Re-scaled

LNA 8GHz—Measured Performance

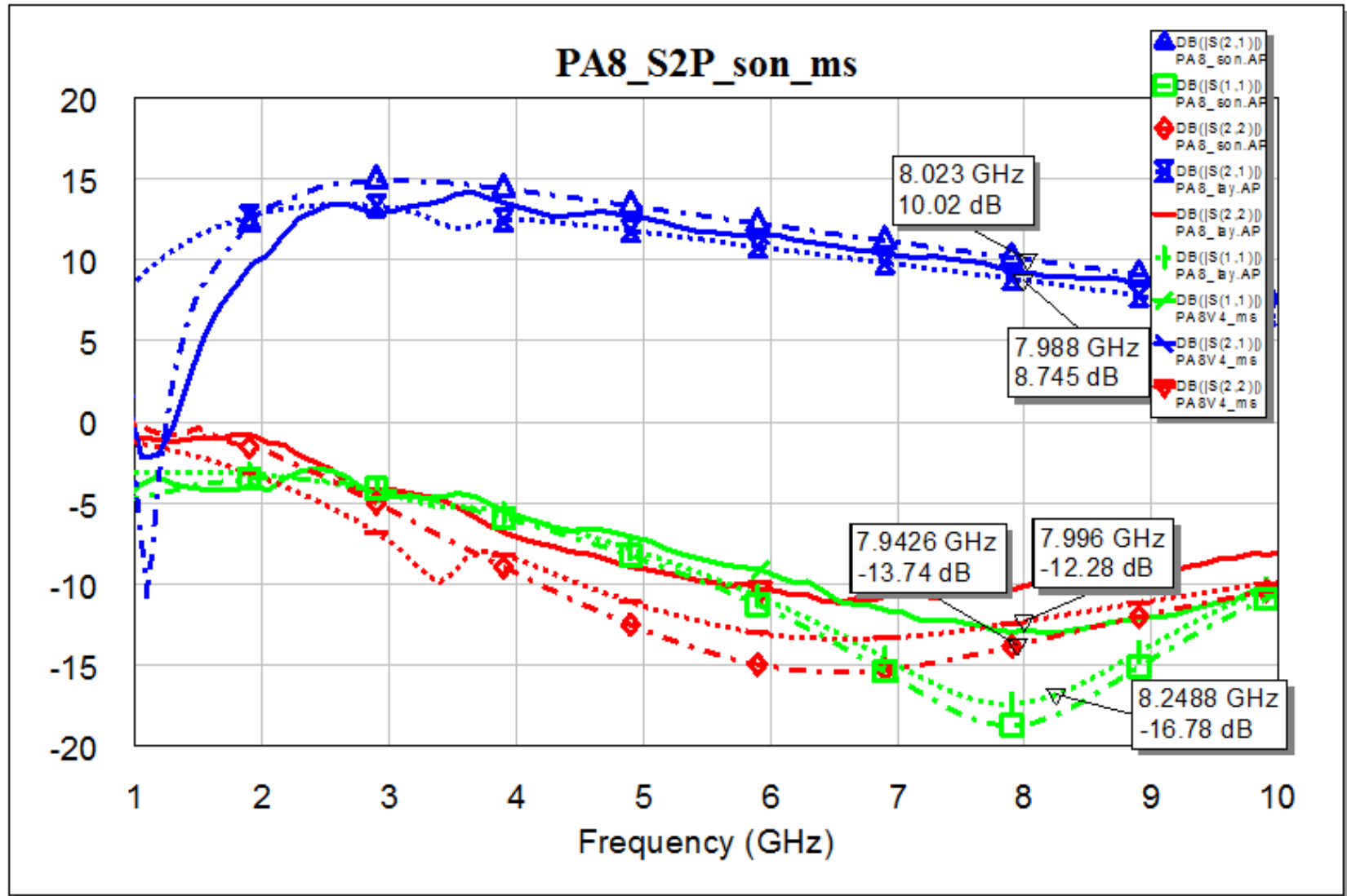


PA 8GHz—Measured 3V, 4V, and two Die



Blue-S21, Green-S22, Magenta-S11

PA 8GHz—Measured vs. Sonnet, AWR



PA 8GHz—Measured Performance vs. Sim

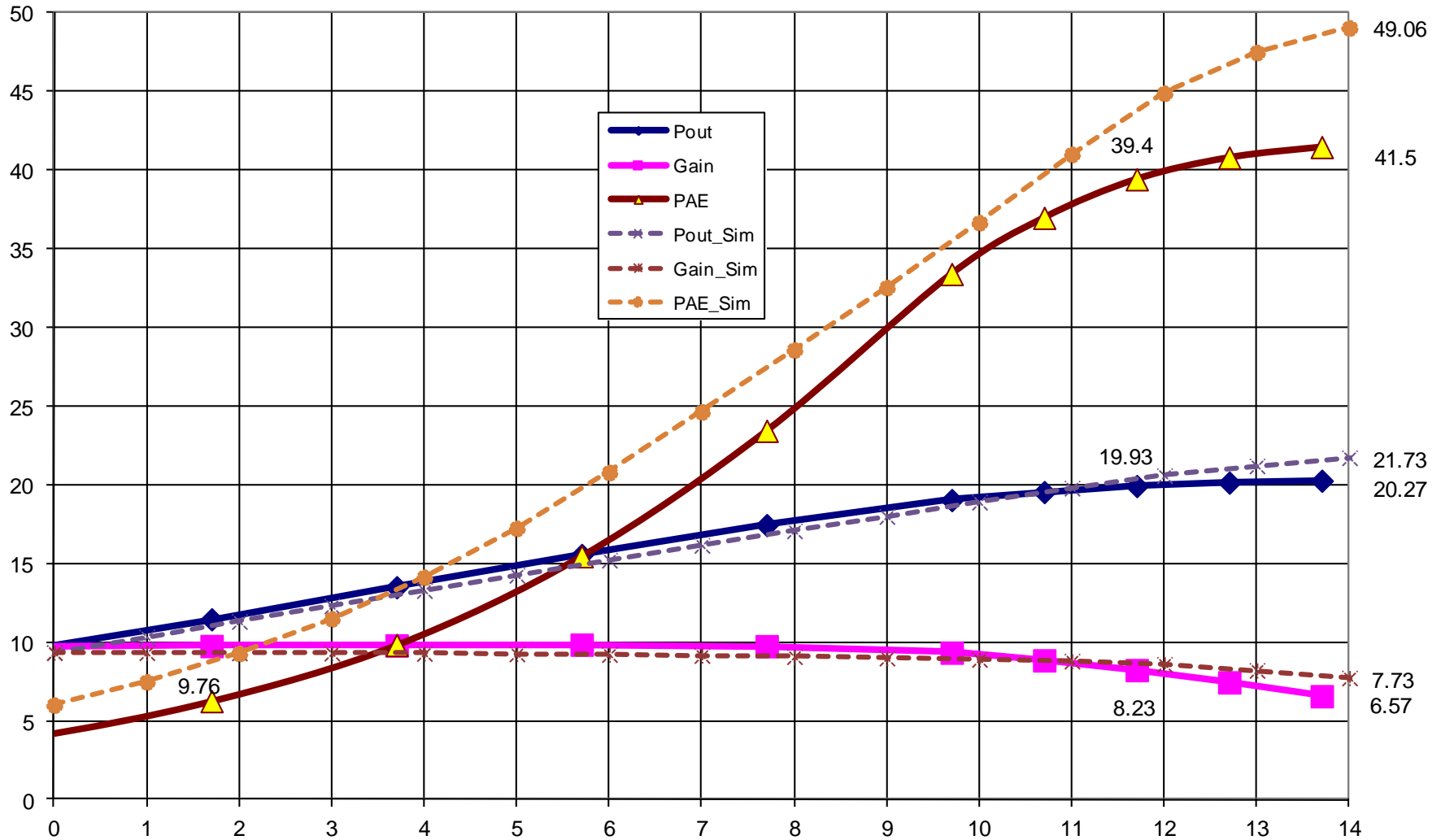
8 GHz	Die#1	8 GHz Fall11 TQP13				4V ; 50 mA			
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
0.0	5.15	-2.30	7.45	9.75	50	200.0	5.56	2.8	2.5
2.0	7.14	-0.30	9.44	9.74	50	200.0	8.79	4.4	3.9
4.0	9.16	1.70	11.46	9.76	50	200.0	14.00	7.0	6.3
6.0	11.20	3.70	13.50	9.80	51	204.0	22.39	11.0	9.8
8.0	13.25	5.70	15.55	9.85	52	208.0	35.89	17.3	15.5
10.0	15.15	7.70	17.45	9.75	53	212.0	55.59	26.2	23.4
12.0	16.74	9.70	19.04	9.34	53	212.0	80.17	37.8	33.4
13.0	17.25	10.70	19.55	8.85	53	212.0	90.16	42.5	37.0
14.0	17.63	11.70	19.93	8.23	53	212.0	98.40	46.4	39.4
15.0	17.85	12.70	20.15	7.45	52	208.0	103.51	49.8	40.8
16.0	17.97	13.70	20.27	6.57	50	200.0	106.41	53.2	41.5

MWO Simulation (Layout) 4V 31mA				
Pin (dBm)	Pout (dBm)	PAE	Pgain	
0	9.34	6.00	9.34	9.34
1	10.33	7.48	9.33	9.33
2	11.32	9.29	9.32	9.32
3	12.30	11.49	9.30	9.30
4	13.28	14.13	9.28	9.28
5	14.25	17.24	9.25	9.25
6	15.21	20.79	9.21	9.21
7	16.16	24.64	9.16	9.16
8	17.08	28.58	9.08	9.08
9	17.99	32.55	8.99	8.99
10	18.90	36.68	8.90	8.90
11	19.80	41.02	8.80	8.80
12	20.59	44.90	8.59	8.59
13	21.21	47.50	8.21	8.21
14	21.73	49.06	7.73	7.73

Notes:
 corr—corrected
 SG—Signal Generator
 SA—Spectrum Analyzer

PA 8GHz—Measured Performance vs. Sim

PA 8GHz Meas vs Sim 11
4V ~50mA



Frequency Doubler 10 to 20 GHz

Measured 9, 10, & 11 Ghz Input

7/11/2012		4.6 dB loss thru				
Doubler 10G		4V at 39mA, vg=0v		Die #1		
SG	Pin(corr)	Pout10G(r	Pout120G(m	Pout(corr)	Pout2X(corr)	Cnvloss
6.0	3.7	1.9	-19.2	4.2	-15.7	19.4
8.0	5.7	3.9	-15.5	6.2	-12.0	17.7
10.0	7.7	5.4	-10.9	7.7	-7.4	15.1
12.0	9.7	7.0	-5.6	9.3	-2.1	11.8
14.0	11.7	7.8	-1.0	10.1	2.5	9.2
16.0	13.7	8.3	1.9	10.6	5.4	8.4

Doubler 10G		4V at 13mA, vg=-3v		Die #1		
SG	Pin(corr)	Pout10G(r	Pout120G	Pout(corr)	Pout2X(cc	Cnvloss
6.0	3.7	-2.8	-10.1	-0.5	-6.6	10.3
8.0	5.7	0.4	-7.7	2.7	-4.2	9.9
10.0	7.7	2.1	-5.2	4.4	-1.7	9.4
12.0	9.7	4.5	-2.8	6.8	0.7	9.0
14.0	11.7	6.6	-0.5	8.9	3.1	8.7
16.0	13.7	7.8	1.7	10.1	5.2	8.6

Notes:

- ms--measured
- corr--corrected
- Pout--Fundamental
- Pout2X--2nd Harmonic
- Cnvloss--2nd Harm Conversion Loss

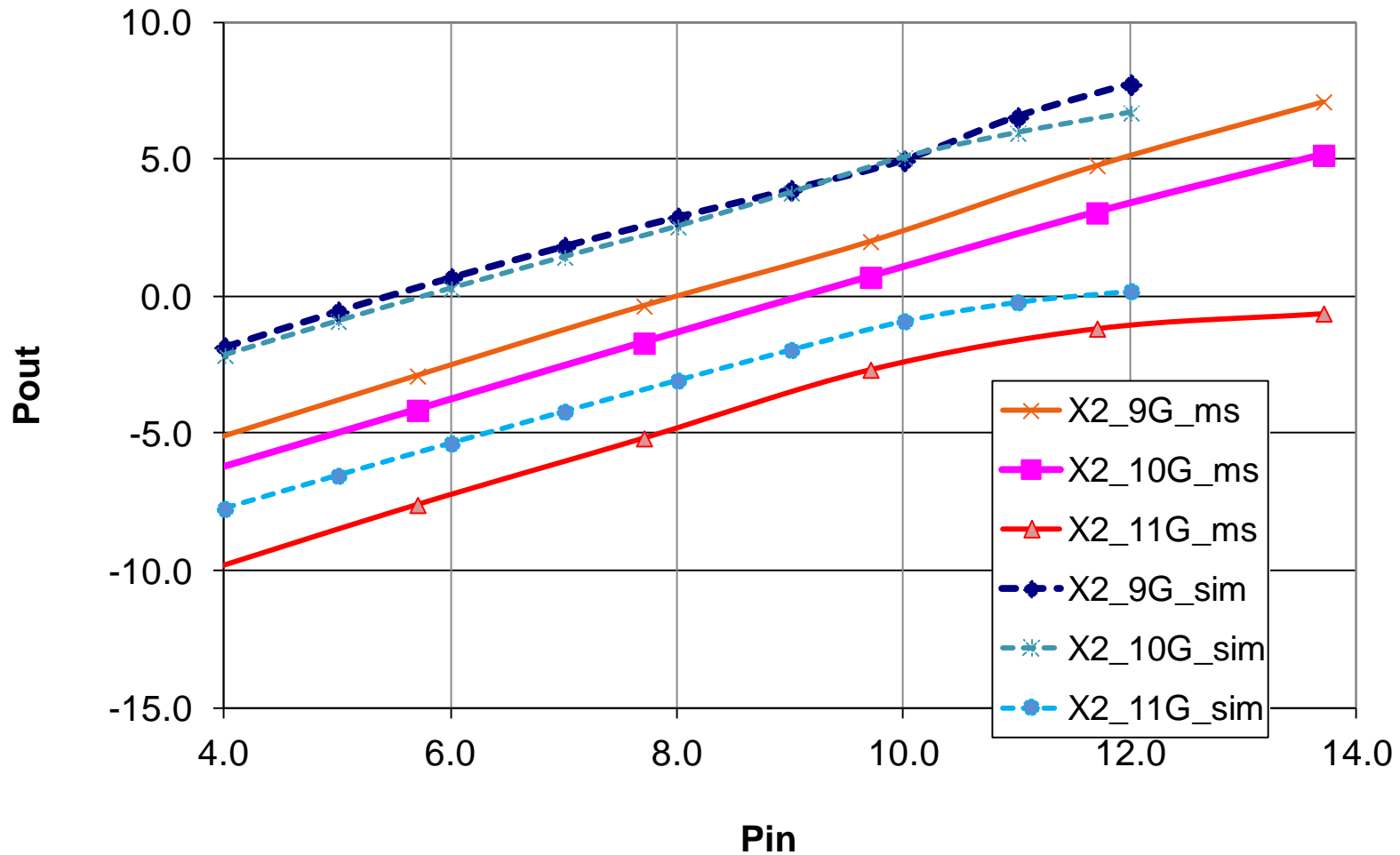
11 GHz						
Doubler 10G		4V at 13mA, vg=-3v		Die #1		
SG	Pin(corr)	Pout10G(r	Pout120G	Pout(corr)	Pout2X(cc	Cnvloss
6.0	3.7	0.2	-13.7	2.5	-10.2	13.9
8.0	5.7	2.4	-11.1	4.7	-7.6	13.3
10.0	7.7	4.7	-8.7	7.0	-5.2	12.9
12.0	9.7	6.9	-6.2	9.2	-2.7	12.4
14.0	11.7	8.6	-4.7	10.9	-1.2	12.9
16.0	13.7	9.5	-4.1	11.8	-0.6	14.3

9 GHz						
Doubler 10G		4V at 13mA, vg=-3v		Die #1		
SG	Pin(corr)	Pout10G(r	Pout120G	Pout(corr)	Pout2X(cc	Cnvloss
6.0	3.7	-5.0	-9.0	-2.7	-5.5	9.2
8.0	5.7	-2.5	-6.4	-0.2	-2.9	8.6
10.0	7.7	0.0	-3.9	2.3	-0.4	8.1
12.0	9.7	2.6	-1.5	4.9	2.0	7.7
14.0	11.7	4.5	1.3	6.8	4.8	6.9
16.0	13.7	5.4	3.6	7.7	7.1	6.6

Frequency Doubler 10 to 20 GHz

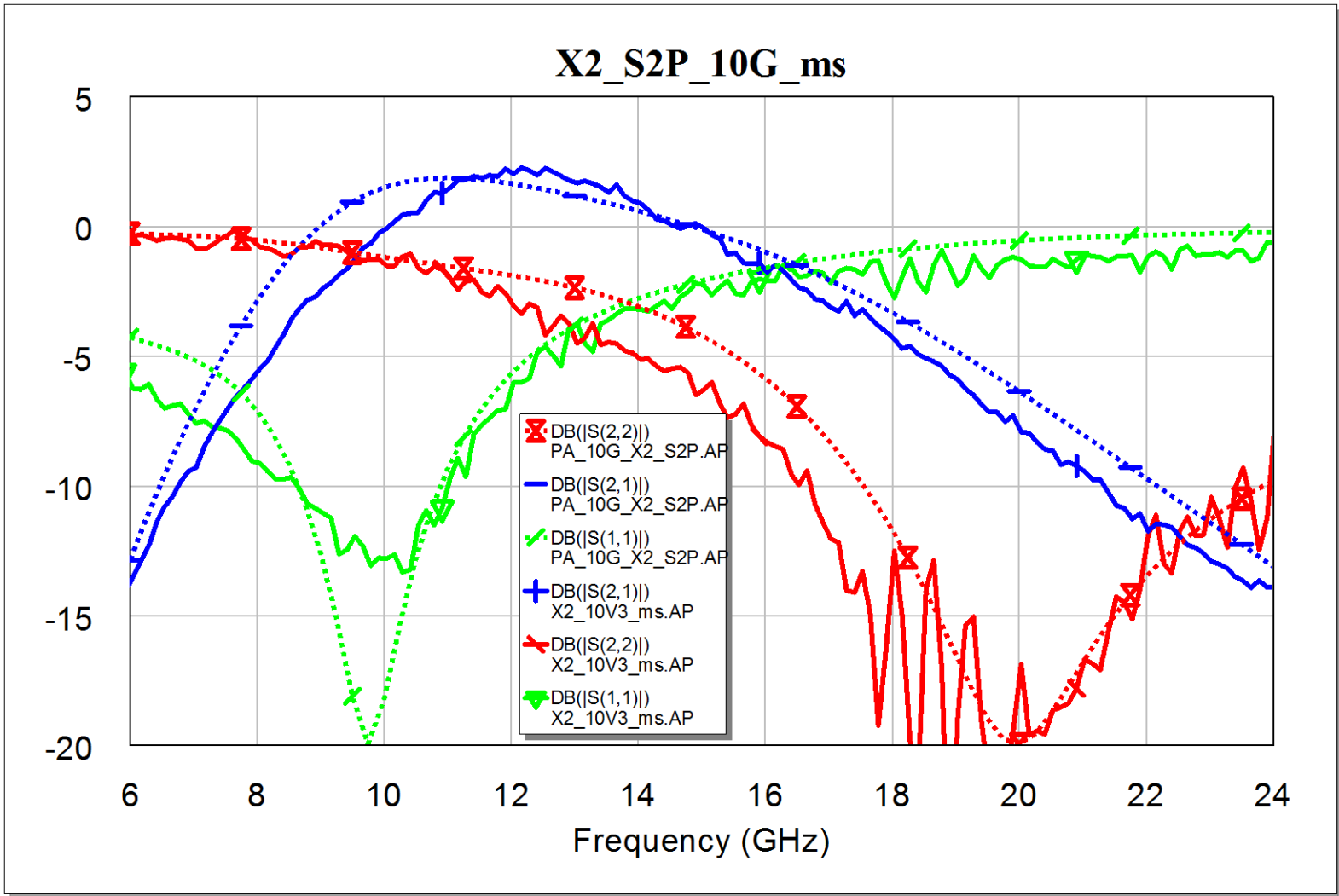
Measured 9, 10, & 11 GHz Input

X2 10 GHz P2X vs. P1In Meas/Sim 7/11/12



Frequency Doubler 10 to 20 GHz

Measured S-Parameters (solid) vs. Sim (dotted)



Frequency Doublers 16 to 32 GHz

Measured 15, 16, & 17 GHz Input

8/10/2012		16.0 GHz							
Doublers 16G			4V at ~39mA, vg=-3v			Die #1			
SG	Pin(corr)	Pin(1)	PoutX1(m	PoutX2(ms)	Pout(corr)	Pout2X(cc	Cnvloss	dBc	
9.3	5.5	5.5	-1.12	-23.5	4.0	-14.0	19.5	18.0	
10.3	6.5	6.5	-0.18	-21.2	4.9	-11.7	18.2	16.6	
11.3	7.5	7.5	0.75	-18.58	5.9	-9.1	16.6	14.9	
12.3	8.5	8.5	1.64	-15.65	6.7	-6.2	14.6	12.9	
13.3	9.5	9.4	2.55	-13.73	7.7	-4.2	13.7	11.9	
14.3	10.5	10.4	3.43	-11.62	8.5	-2.1	12.5	10.7	
15.3	11.5	11.4	4.29	-9.53	9.4	0.0	11.4	9.4	
16.3	12.5	12.3	5.13	-7.85	10.2	1.7	10.7	8.6	
17.3	13.5	13.2	5.85	-6.42	11.0	3.1	10.2	7.9	
18.2	14.4	14.2	6.59	-5.23	11.7	4.3	9.9	7.4	

8/10/2012		17 GHz							
Doublers 16G			4V at ~39mA, vg=-3v			Die #1			
SG	Pin(corr)	Pin(1)	PoutX1(m	PoutX2(m	Pout(corr)	Pout2X(cc	Cnvloss	dBc	
9.1	5.3	4.9	-2.23	-25.4	2.9	-15.9	20.8	18.8	
10.1	6.3	5.9	-1.27	-23.1	3.8	-13.6	19.5	17.4	
11.0	7.2	6.9	-0.33	-20.79	4.8	-11.3	18.2	16.1	
12.0	8.2	7.9	0.59	-18.22	5.7	-8.7	16.6	14.4	
13.0	9.2	8.9	1.49	-15.65	6.6	-6.2	15.0	12.7	
14.0	10.2	9.8	2.37	-13.39	7.5	-3.9	13.7	11.4	
15.0	11.2	10.8	3.24	-11.32	8.3	-1.8	12.6	10.2	
16.0	12.2	11.7	4.09	-9.57	9.2	-0.1	11.8	9.3	
16.9	13.1	12.6	4.9	-8.02	10.0	1.5	11.2	8.5	
17.9	14.1	13.5	5.68	-6.7	10.8	2.8	10.7	8.0	

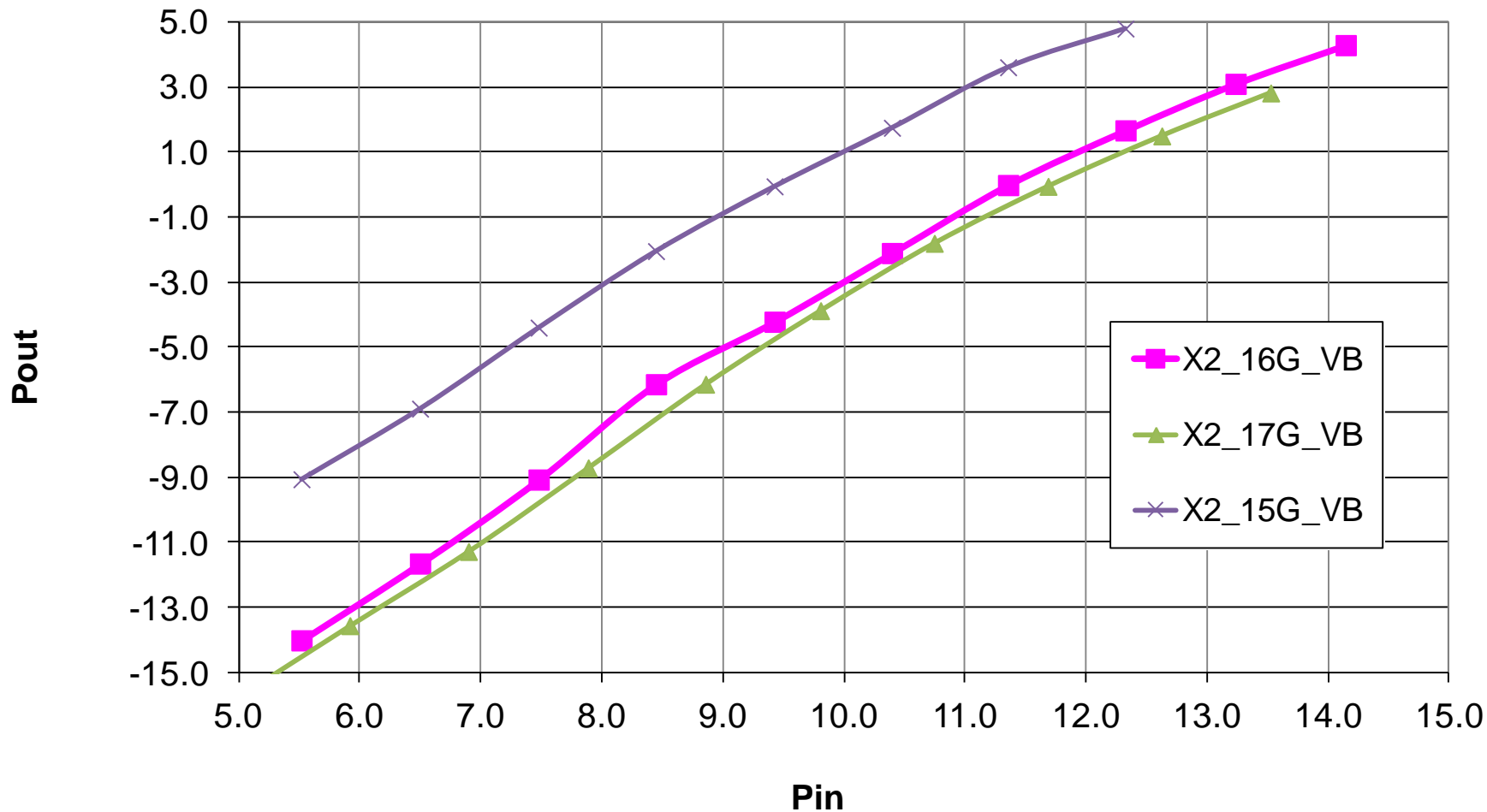
8/10/2012		15 GHz							
Doublers 16G			4V at ~39mA, vg=-3v			Die #1			
SG	Pin(corr)	Pin(1)	PoutX1(m	PoutX2(m	Pout(corr)	Pout2X(cc	Cnvloss	dBc	
11.0	7.2	5.5	1.75	-18.6	6.9	-9.1	14.6	15.9	
12.0	8.2	6.5	2.66	-16.4	7.8	-6.9	13.4	14.7	
13.0	9.2	7.5	3.56	-13.91	8.7	-4.4	11.9	13.1	
14.0	10.2	8.5	4.46	-11.56	9.6	-2.1	10.5	11.6	
15.0	11.2	9.4	5.32	-9.57	10.4	-0.1	9.5	10.5	
16.1	12.3	10.4	6.18	-7.77	11.3	1.7	8.7	9.6	
17.0	13.2	11.4	7.00	-5.91	12.1	3.6	7.8	8.5	
18.0	14.2	12.3	7.78	-4.72	12.9	4.8	7.6	8.1	

Notes:

- ms--measured
- corr--corrected
- Pout--Fundamental
- Pout2X--2nd Harmonic
- Cnvloss--2nd Harm Conversion Loss

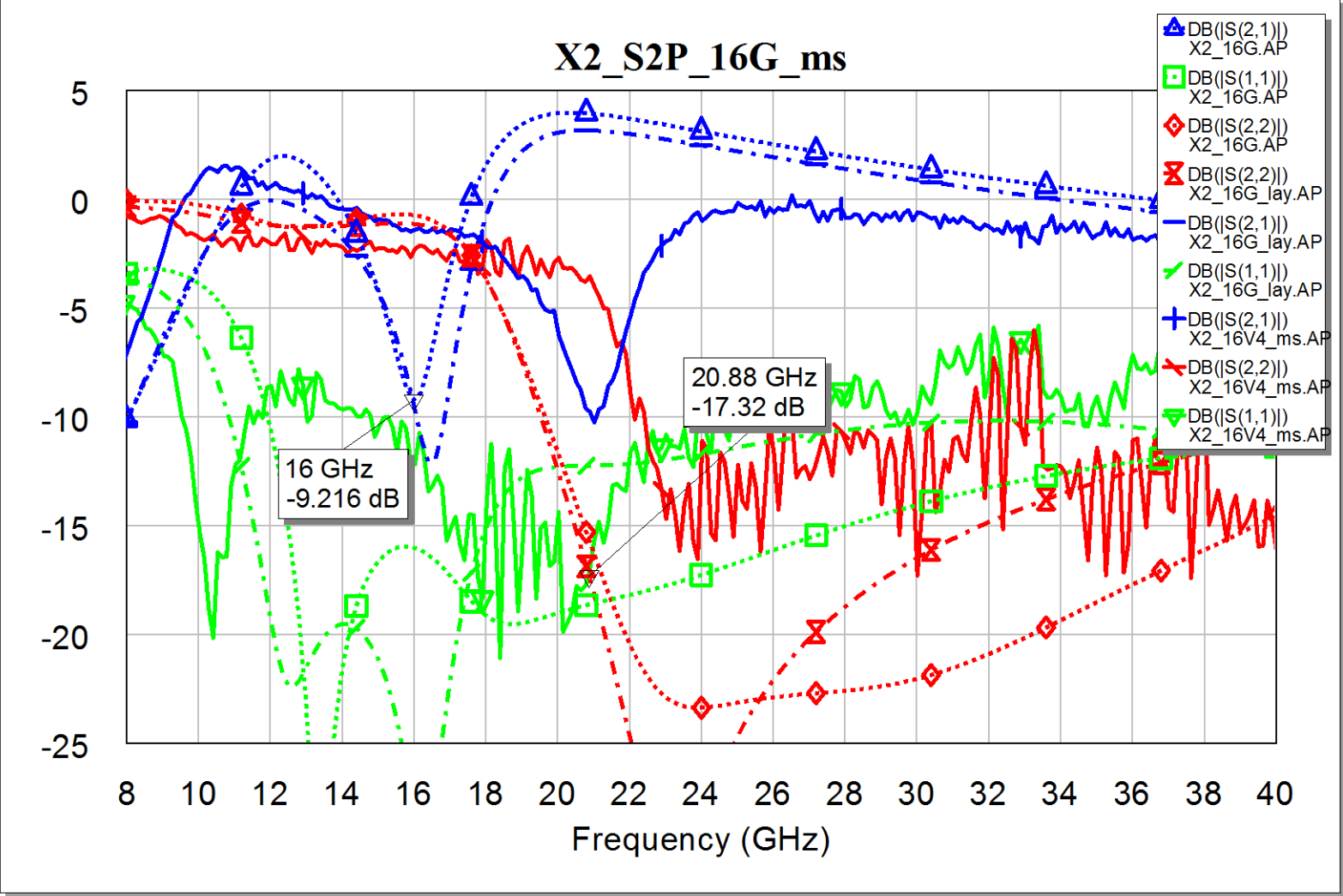
Frequency Doubler 16 to 32 GHz

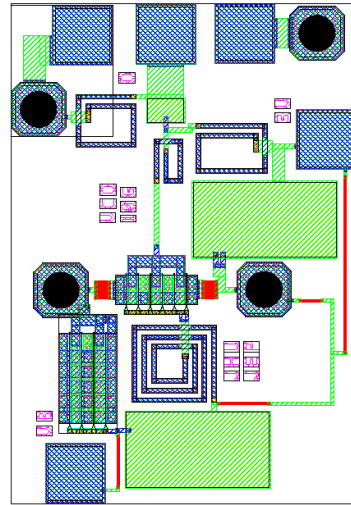
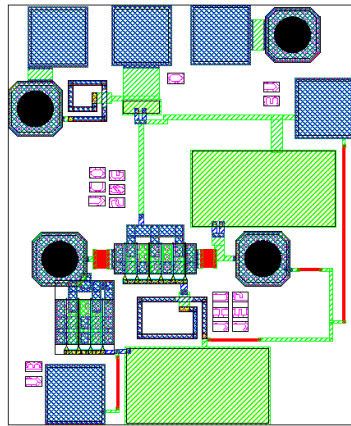
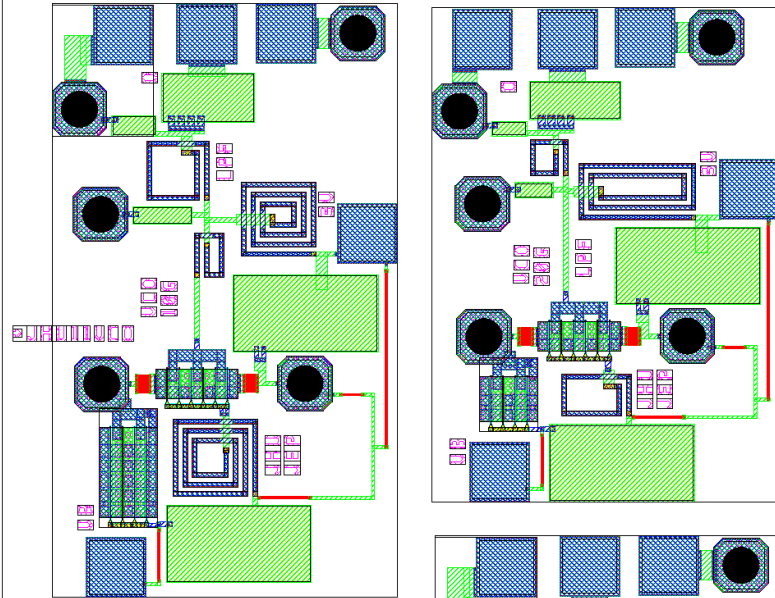
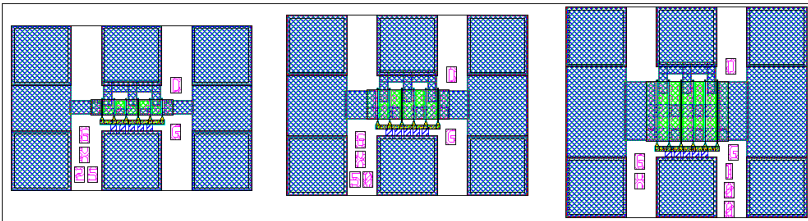
Measured 15, 16, & 17 Ghz Input
X2 16 GHz P2X vs. P1In 8/10/12



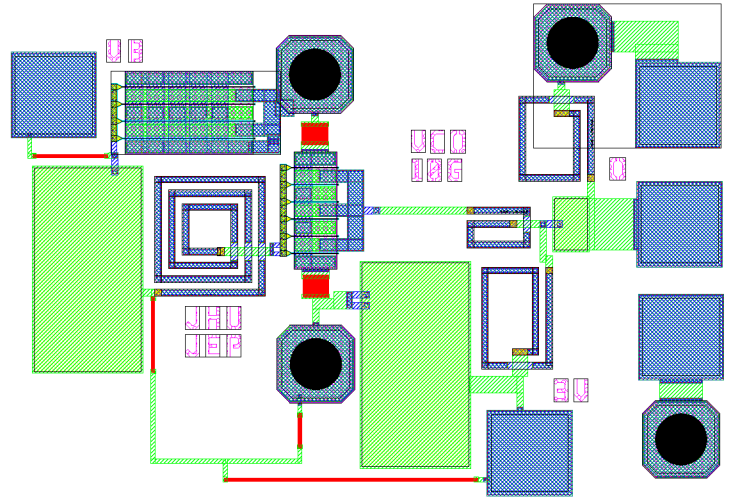
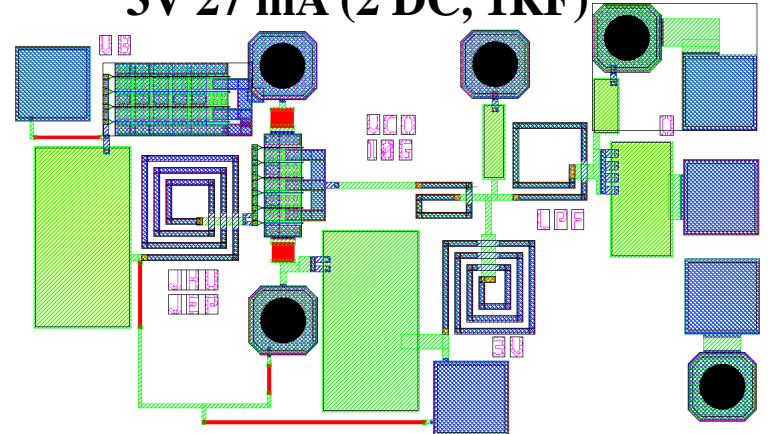
Frequency Doubler 16 to 32 GHz

Measured S-Parameters (solid) vs. Sim (dotted)



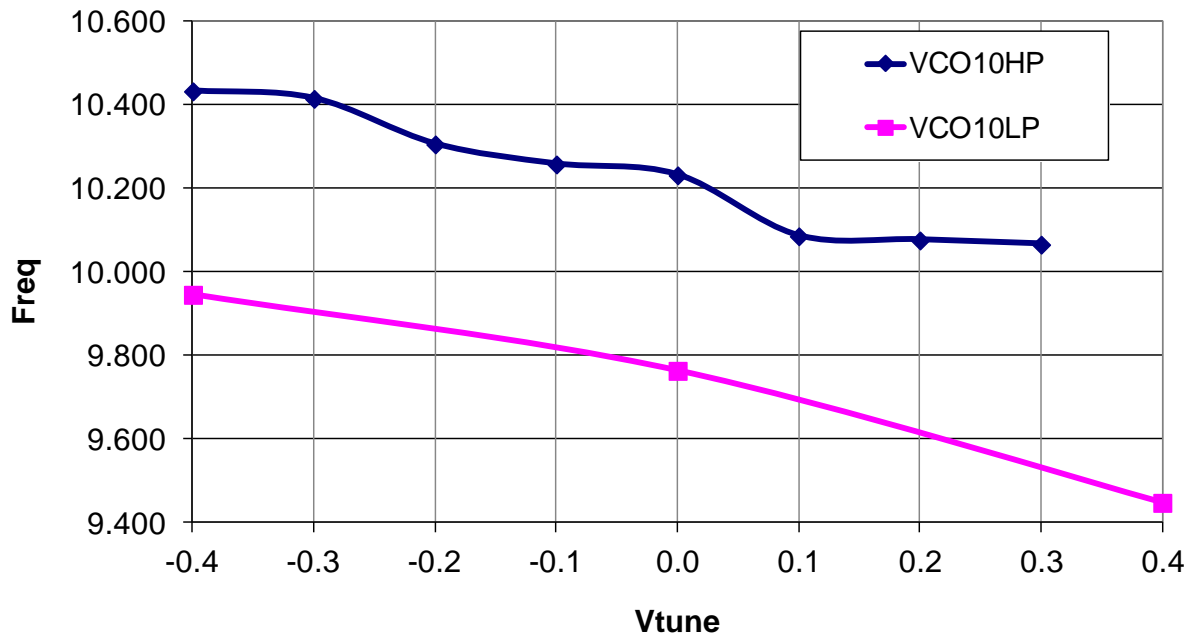


12) JHU11VCO -- JEP
10, 20 GHz VCOs
3V 27 mA (2 DC, 1RF)
3V 27 mA (2 DC, 1RF)
3V 27 mA (2 DC, 1RF)
3V 27 mA (2 DC, 1RF)



Voltage Controlled Oscillator (VCO)—Meas 10 G

BW VCO Freq vs. Tune Voltage



*LP VCO Had Lower RF Output Power but much better 2nd harmonic attenuation.

LPF_Sim	VBias (V)	Freq (GHz)	Pout	Pout2X
	-0.4	9.942	12.7	-31.9
	0.0	9.737	12.6	-29.6
	0.4	9.662	12.5	-28.9

HPF_Sim	VBias (V)	Freq (GHz)	Pout	Pout2X
	-0.4	10.136	12.2	1.4
	0.0	9.921	12.2	1.2
	0.4	9.812	12.2	0.7

Simulation is Similar

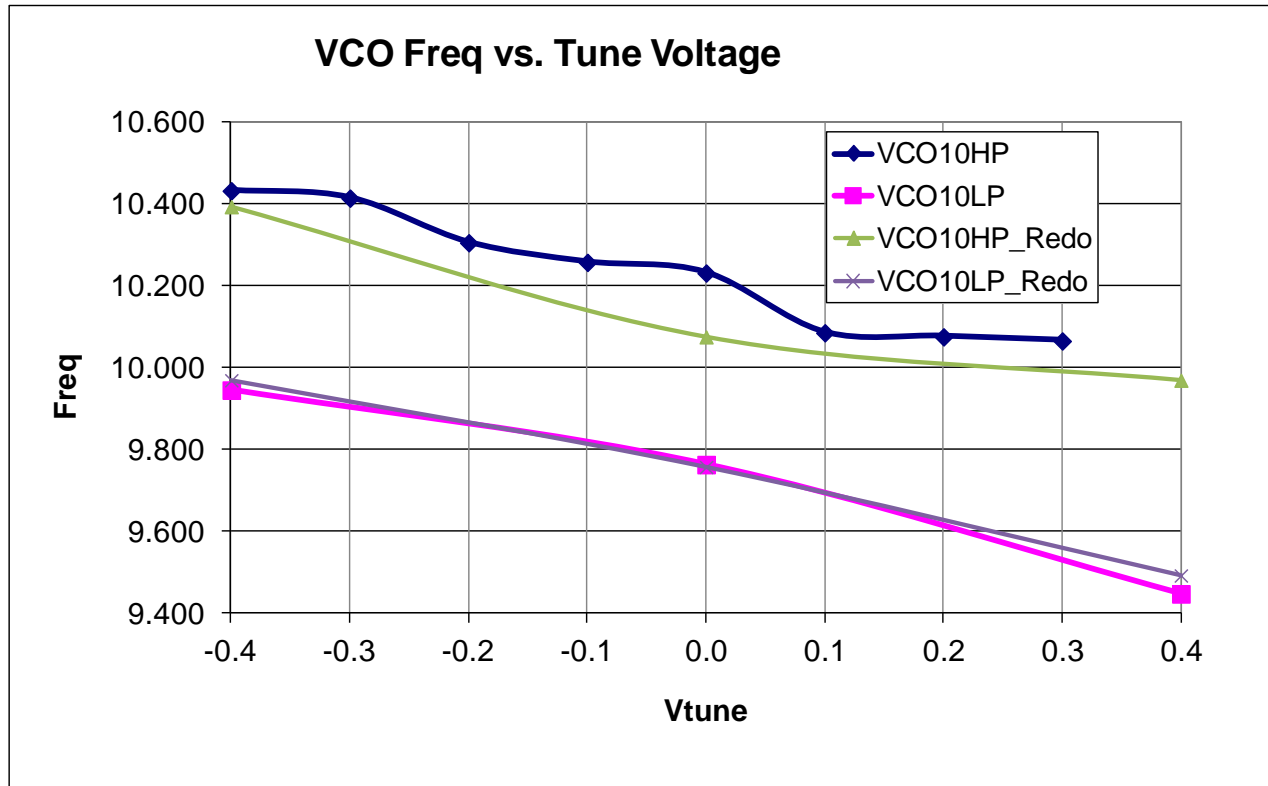
HPF VCO	3V at 35mA			Die #1		
VBias (V)	Freq (GHz)	Pout(ms)	Pout2X(ms)	Pout(corr)	Pout2X(corr)	dBc
-0.4	10.433	5.8	-3.5	8.2	0.5	7.7
-0.3	10.415	5.9	-3.7	8.2	0.4	7.9
-0.2	10.306	7.2	-2.9	9.6	1.1	8.4
-0.1	10.258	6.9	-2.7	9.2	1.3	7.9
0.0	10.232	6.9	-2.2	9.3	1.8	7.4
0.1	10.086	7.7	-4.4	10.1	-0.4	10.4
0.2	10.076	7.3	-3.6	9.6	0.5	9.1
0.3	10.066	6.9	-3.4	9.3	0.7	8.6

LPF VCO	3V at 34mA			Die #1		
VBias (V)	Freq (GHz)	Pout(ms)	Pout2X(m)	Pout(corr)	Pout2X(cc)	dBc
-0.4	9.946	5.1	-39.0	7.4	-35.0	42.4
0.0	9.764	3.8	-37.7	6.2	-33.7	39.8
0.4	9.448	3.8	-37.0	6.2	-33.0	39.1

Notes:

- ms--measured
- corr--corrected
- Pout--Fundamental
- Pout2X--2nd Harmonic

Voltage Controlled Oscillator—Re-Meas 10 G



*Re-Meas LP VCO Had Similar RF Output Power LPF: Much better 2nd harmonic attenuation.

LPF_Sim			
VBias (V)	Freq (GHz)	Pout	Pout2X
-0.4	9.942	12.7	-31.9
0.0	9.737	12.6	-29.6
0.4	9.662	12.5	-28.9

HPF_Sim			
VBias (V)	Freq (GHz)	Pout	Pout2X
-0.4	10.136	12.2	1.4
0.0	9.921	12.2	1.2
0.4	9.812	12.2	0.7

Re-Measured 8/1/12

HPF VCO 3V at 34mA						
		Die #2				
VBias (V)	Freq (GHz)	Pout(ms)	Pout2X(m)	Pout(corr)	Pout2X(cc)	dBc
-0.4	10.394	5.8	-4.4	8.1	-0.4	8.5
0.0	10.076	7.4	-4.2	9.8	-0.1	9.9
0.4	9.970	7.2	-3.7	9.5	0.3	9.2

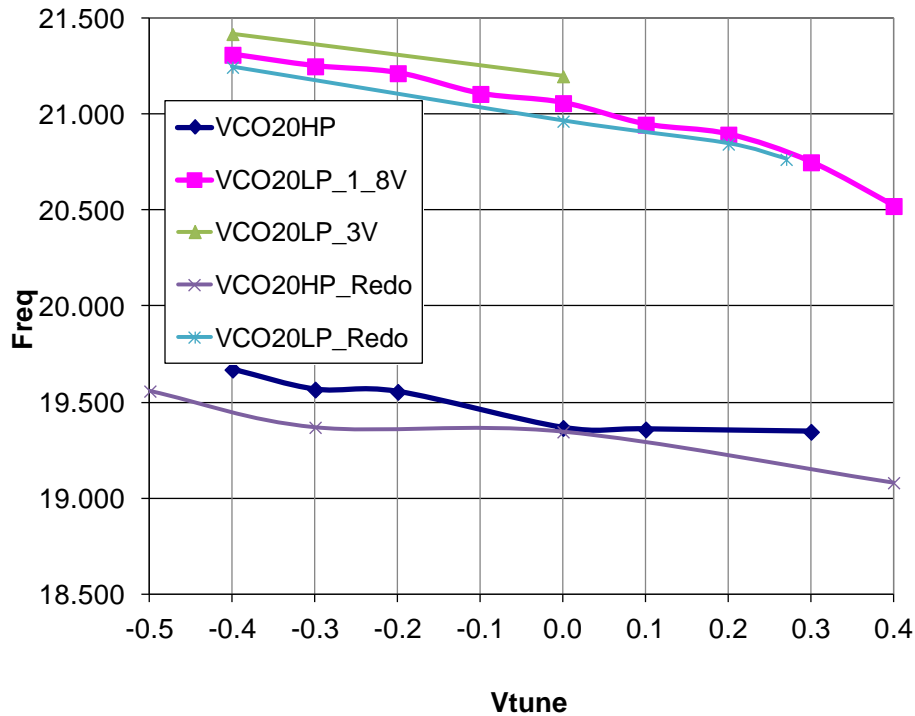
LPF VCO 3V at 32mA			Die #2			
VBias (V)	Freq (GHz)	Pout(ms)	Pout2X(m)	Pout(corr)	Pout2X(cc)	dBc
-0.4	9.970	8.4	-34.5	10.7	-30.5	41.2
0.0	9.758	8.2	-34.0	10.6	-30.0	40.5
0.4	9.493	7.9	-33.0	10.2	-29.0	39.2

Notes:

ms--measured
 corr--corrected
 Pout--Fundamental
 Pout2X--2nd Harmonic

Voltage Controlled Oscillator—Re-Meas 20 G

VCO Freq vs. Tune Voltage



*Re-Meas LP VCO Had Similar Tuning Range to previous 1.8V meas. HPF VCO consistent. Non-Linear Sim had problems with convergence.

LPF_Sim	VBias (V)	Freq (GHz)	Pout	Pout2X
	0.0	20.042	6.9	-52.8
	0.15	19.690	6.9	-51.7
	0.3	19.386	6.2	-53.6

HPF_Sim	VBias (V)	Freq (GHz)	Pout	Pout2X
	0.0	19.947	6.7	-10.9
	0.15	19.554	6.5	-10.8
	0.3	19.190	6.3	-11.2

Re-Measured 8/1/12

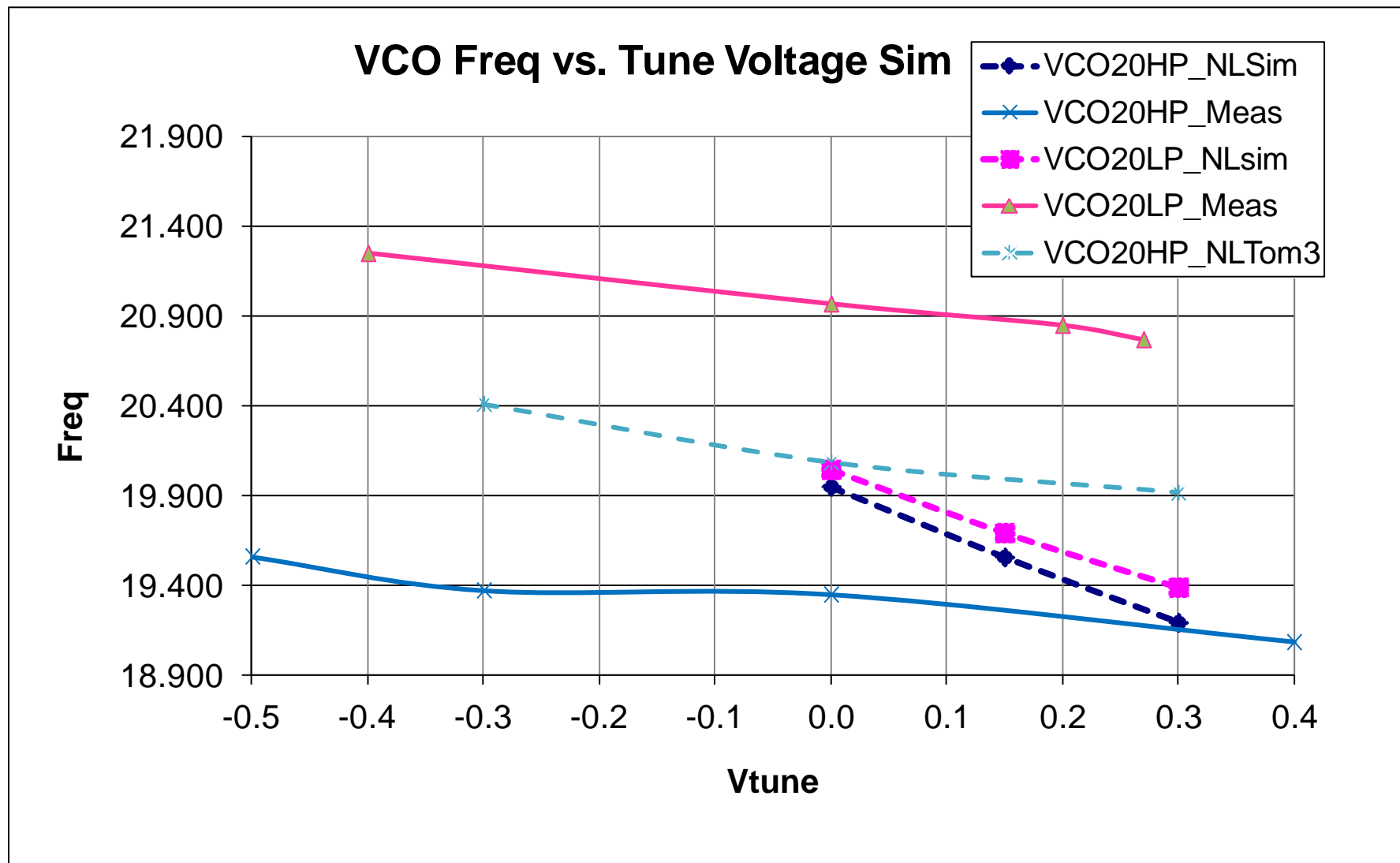
HPF VCO	3V at 24mA	Die #2
VBias (V)	Freq (GHz)	Pout(ms) Pout(corr)
-0.5	19.560	6.7 10.7
-0.3	19.371	7.2 11.2
0.0	19.348	6.2 10.2
0.4	19.083	6.5 10.5

LPF VCO	3V at 33mA	Die #2
VBias (V)	Freq (GHz)	Pout(ms) Pout(corr)
-0.4	21.247	-2.3 1.7
0.0	20.966	0.4 4.4
0.2	20.847	-0.1 3.9
0.3	20.767	-0.7 3.3

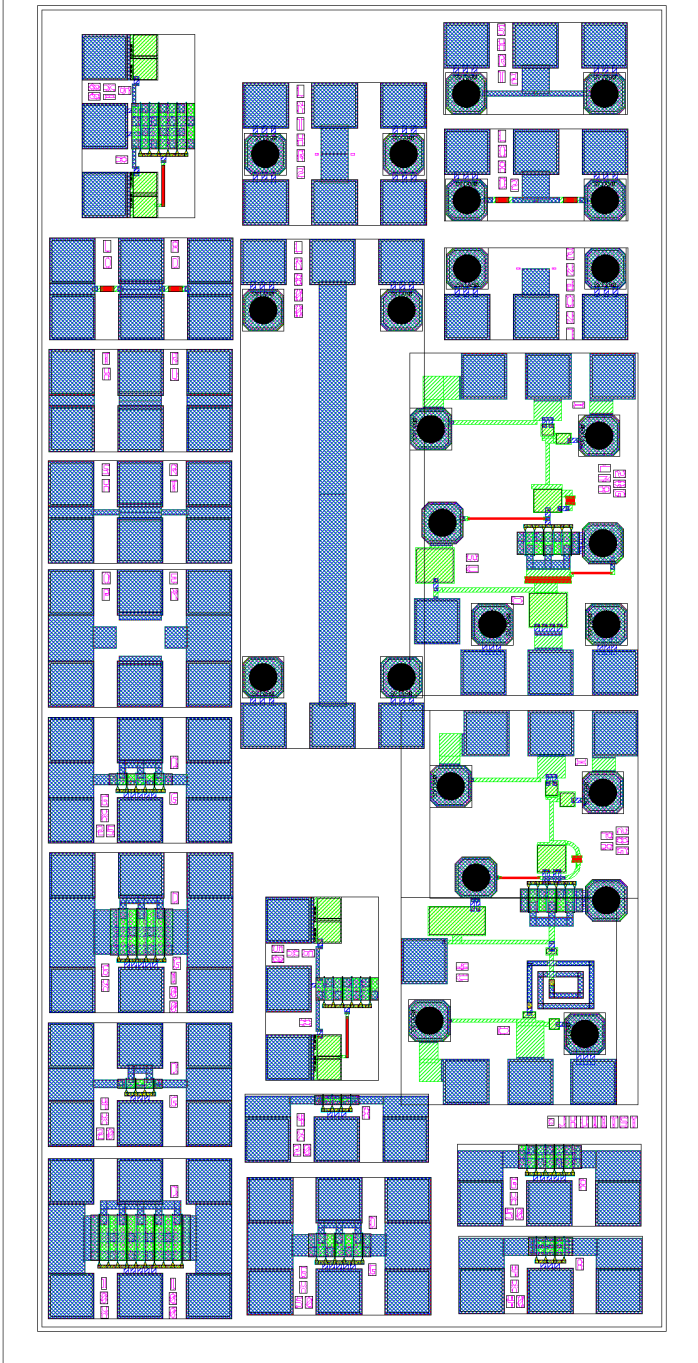
Notes:

ms--measured
 corr--corrected
 Pout--Fundamental
 Pout2X--2nd Harmonic

Voltage Controlled Oscillator (VCO)—Meas 20 G



*Non-Linear Simulation vs. Measured
Better Convergence with TOM3 Model!



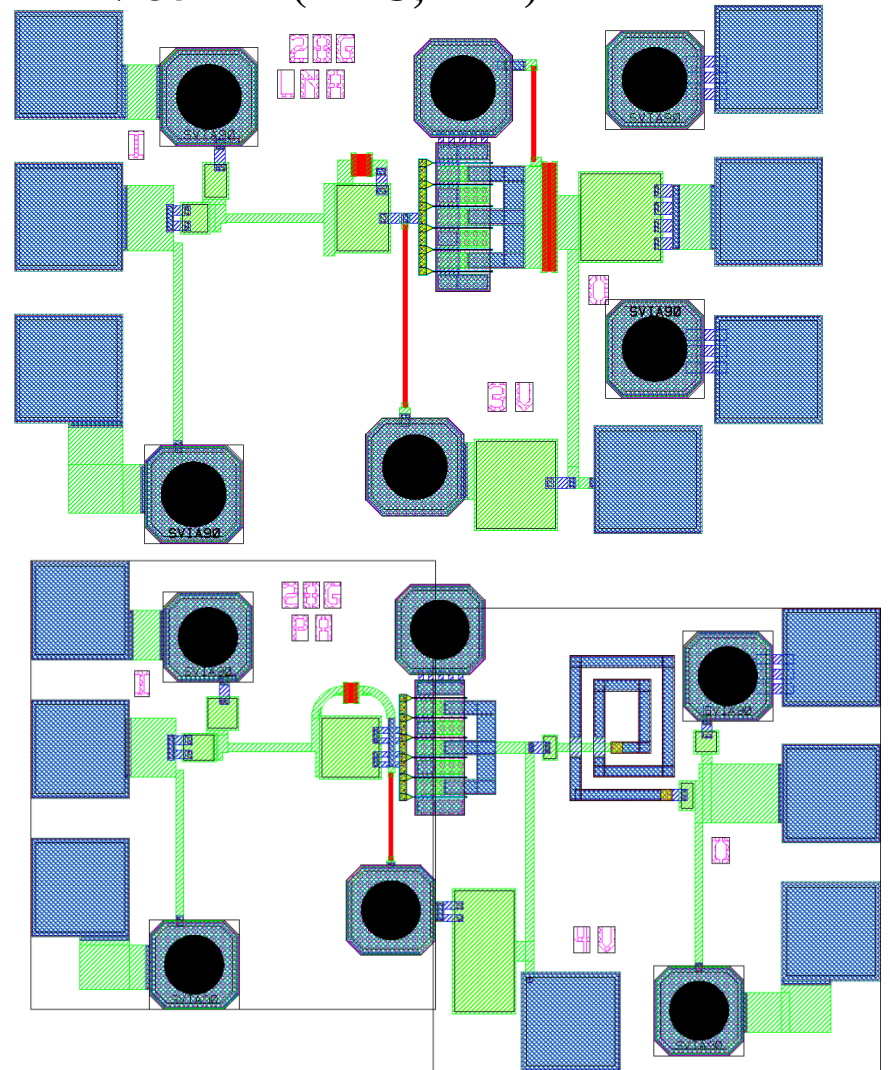
13) JHU11TST -- JEP

28 GHz LNA, PA

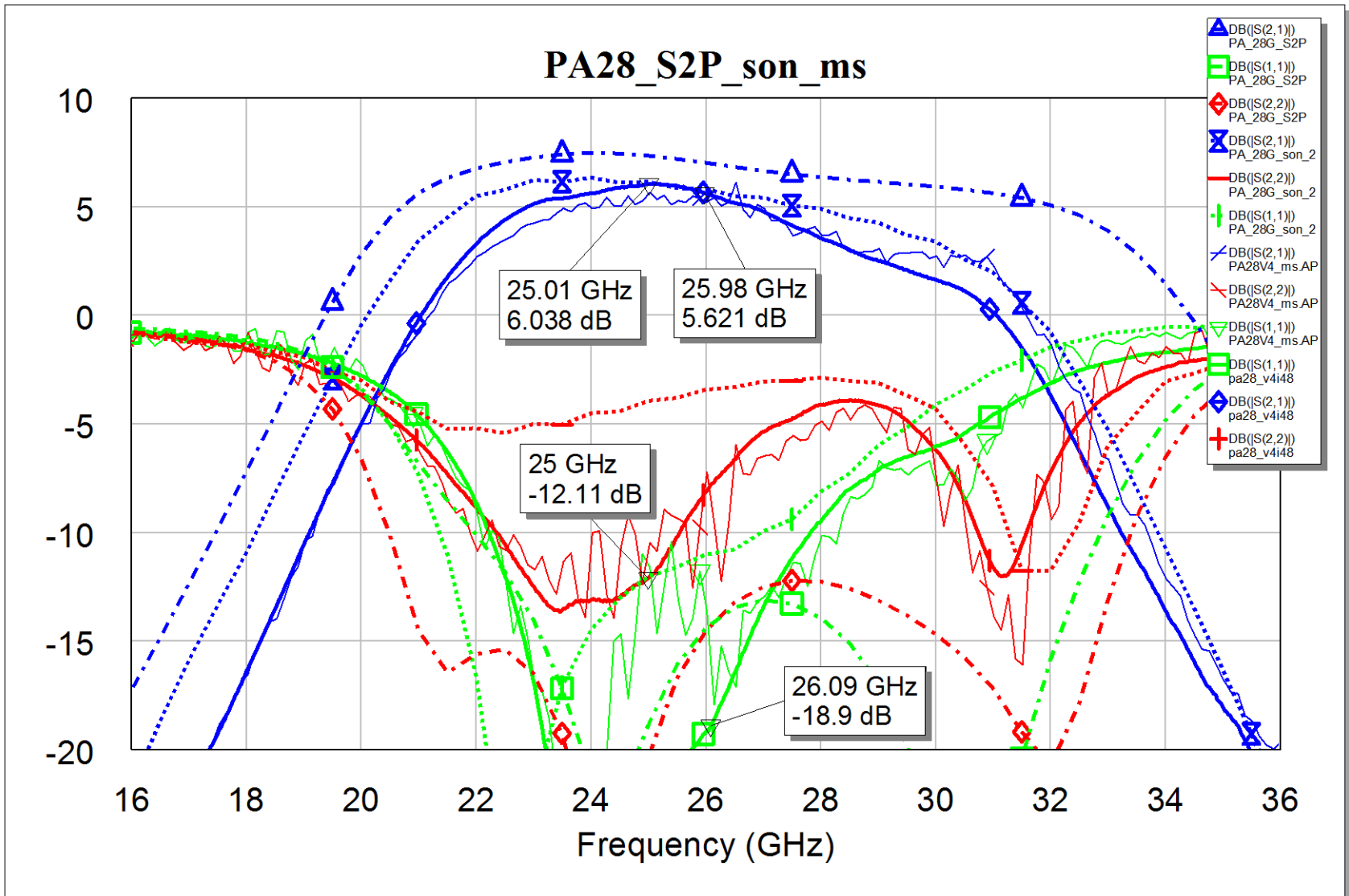
Test Devices

3V 27 mA (1 DC, 2RF)

4V 35 mA (1 DC, 2RF)



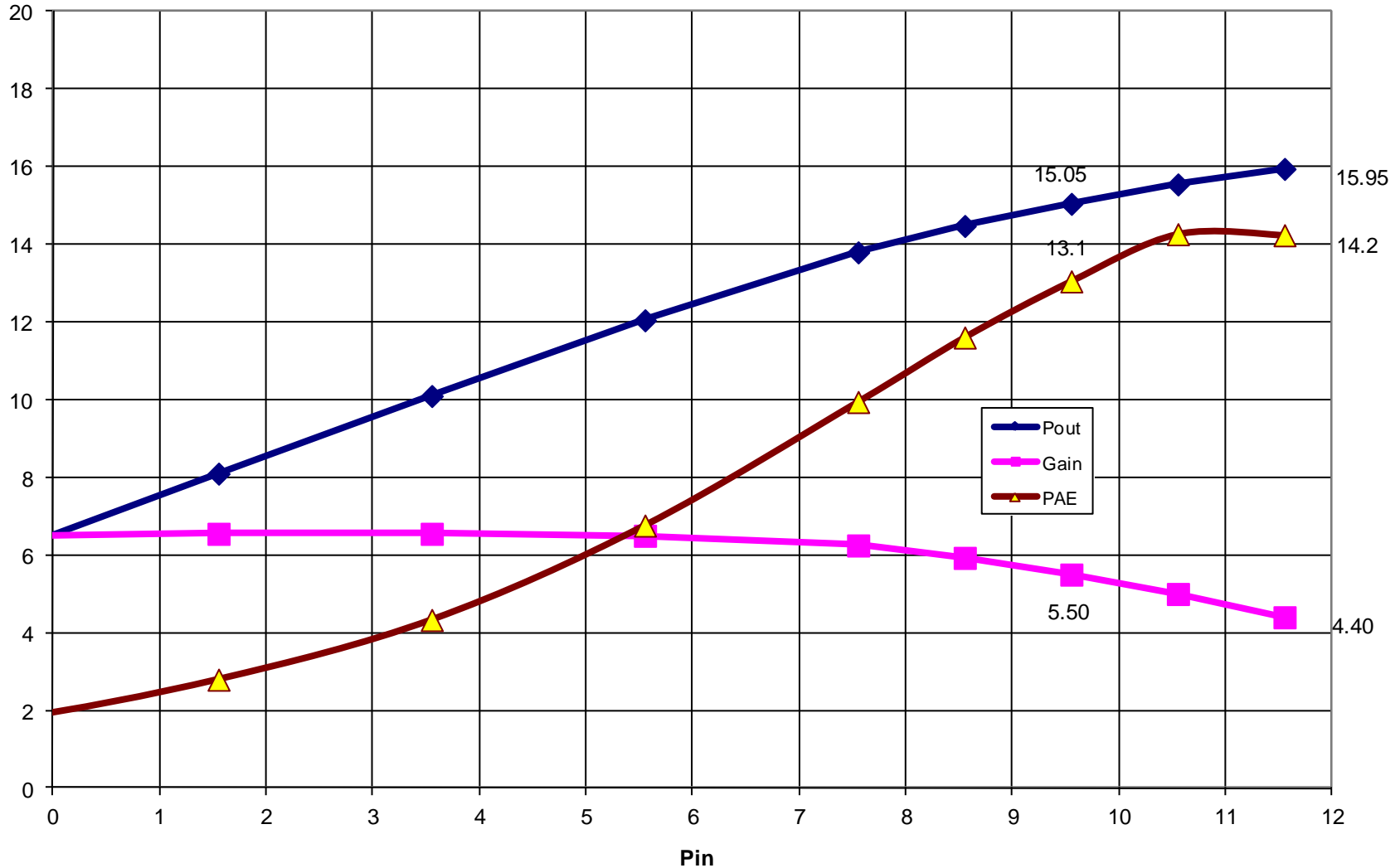
PA 28GHz—Measured vs. Sonnet, AWR



Solid-Meas, Dotted-Sonnet, Dot/Dash-AWR

PA 28GHz—Measured Performance

PA 28GHz Meas 11
25.3 GHz 4V ~44mA



Low Gain & Measured at 25.3 GHz (equipment limitation!)

PA 28GHz—Measured Performance

JEP 28 GHz 4 V										
Measured at 25.35 GHz				Loss 8.9 dB for thru						
25.35 GHz	Die#1	28 GHz Fall11 TQP13					4V ; 50 mA			
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
0.0	-2.40	-4.45	2.05	6.50	44	176.0	1.60	0.9	0.7	
2.0	-0.40	-2.45	4.05	6.50	44	176.0	2.54	1.4	1.1	
4.0	1.60	-0.45	6.05	6.50	45	180.0	4.03	2.2	1.7	
6.0	3.65	1.55	8.10	6.55	45	180.0	6.46	3.6	2.8	
8.0	5.65	3.55	10.10	6.55	46	184.0	10.23	5.6	4.3	
10.0	7.60	5.55	12.05	6.50	46	184.0	16.03	8.7	6.8	
12.0	9.35	7.55	13.80	6.25	46	184.0	23.99	13.0	9.9	
13.0	10.03	8.55	14.48	5.93	45	180.0	28.05	15.6	11.6	
14.0	10.60	9.55	15.05	5.50	44	176.0	31.99	18.2	13.1	
15.0	11.10	10.55	15.55	5.00	43	172.0	35.89	20.9	14.3	
16.0	11.50	11.55	15.95	4.40	44	176.0	39.36	22.4	14.2	

Notes:

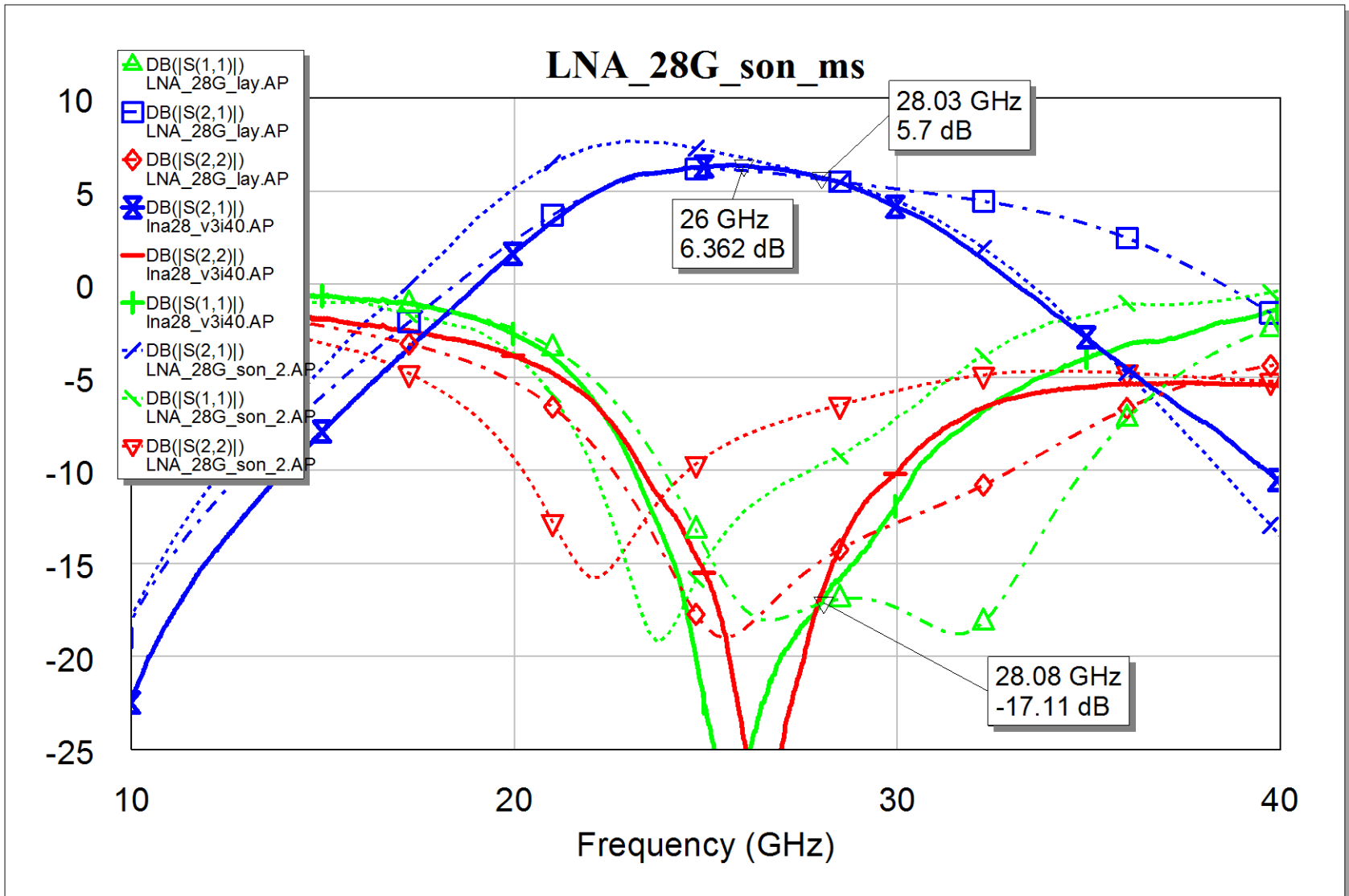
corr—corrected

SG—Signal Generator

SA—Spectrum Analyzer

Low Gain & Measured at 25.3 GHz (equipment limitation!)

LNA 28GHz—Measured vs. Sonnet, AWR

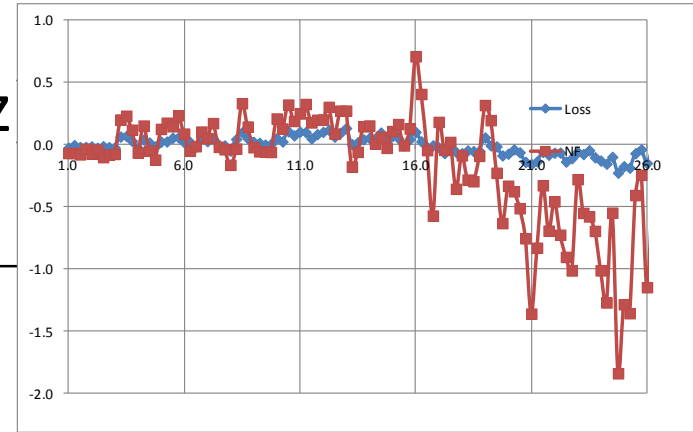
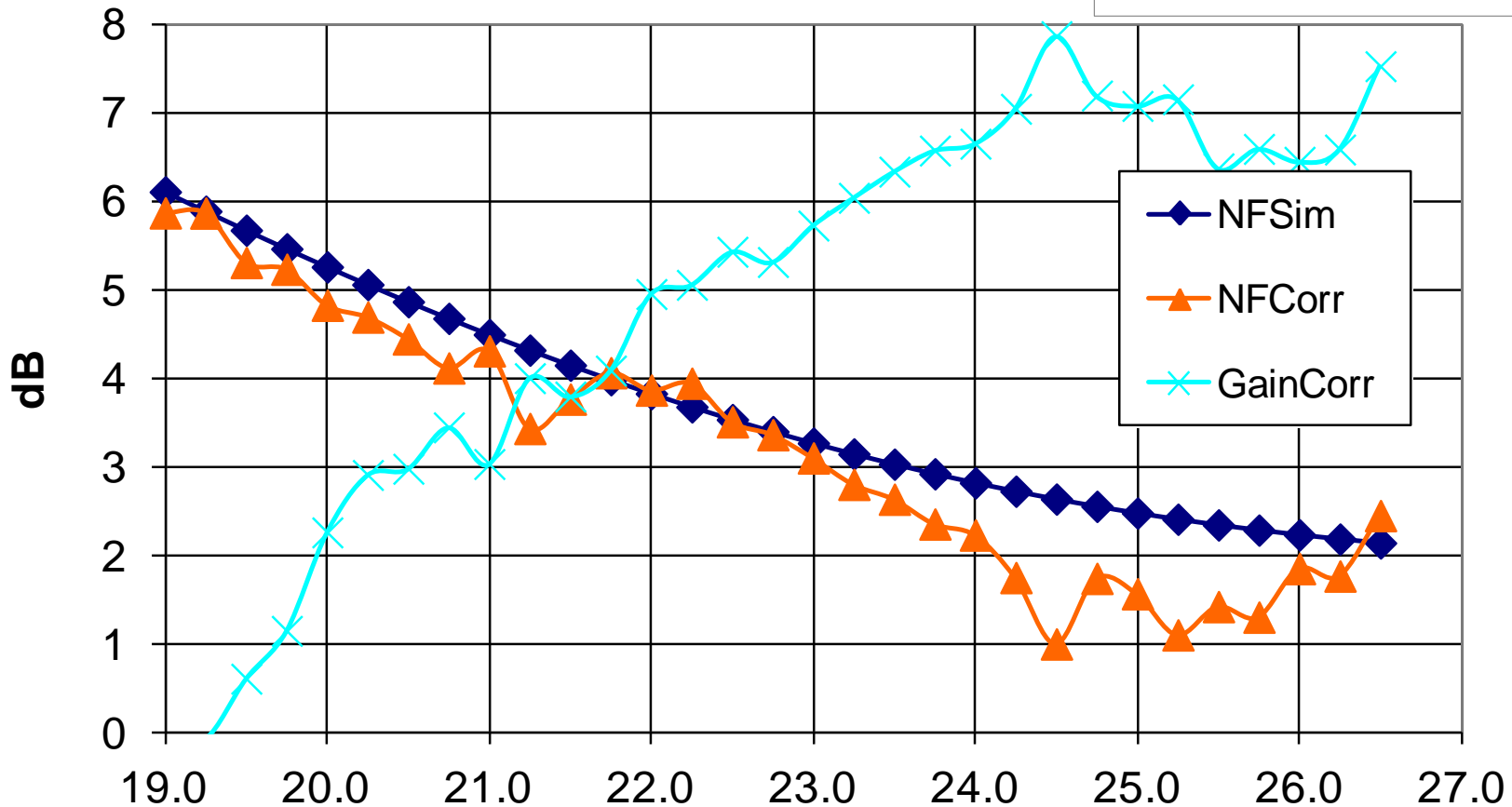


Solid-Meas, Dotted-Sonnet, Dot/Dash-AWR

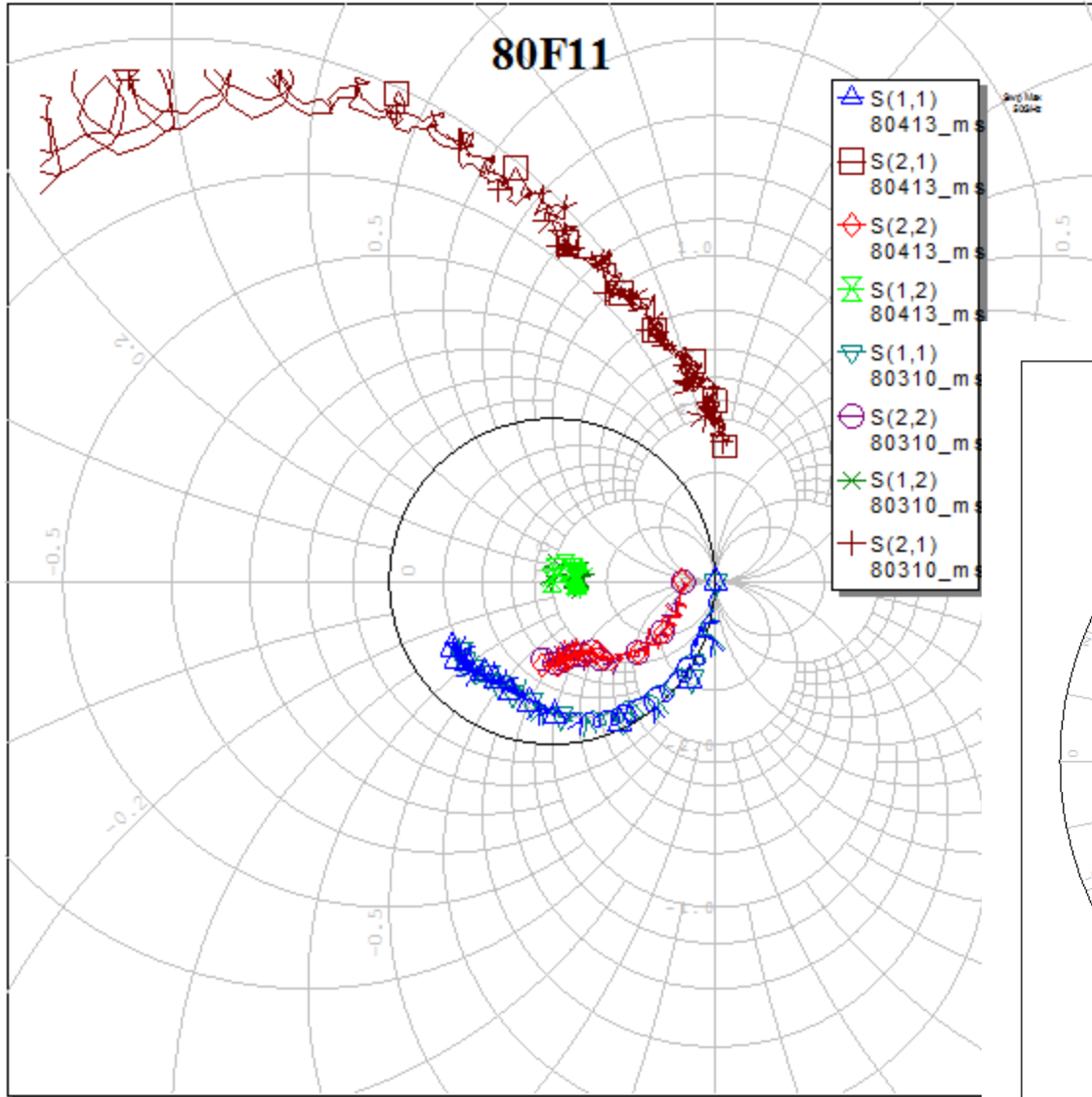
LNA 28GHz—Measured NF (to 26 GHz)

NF Low ~1dB at higher end, matches well below 23 GHz

LNA28G 3V



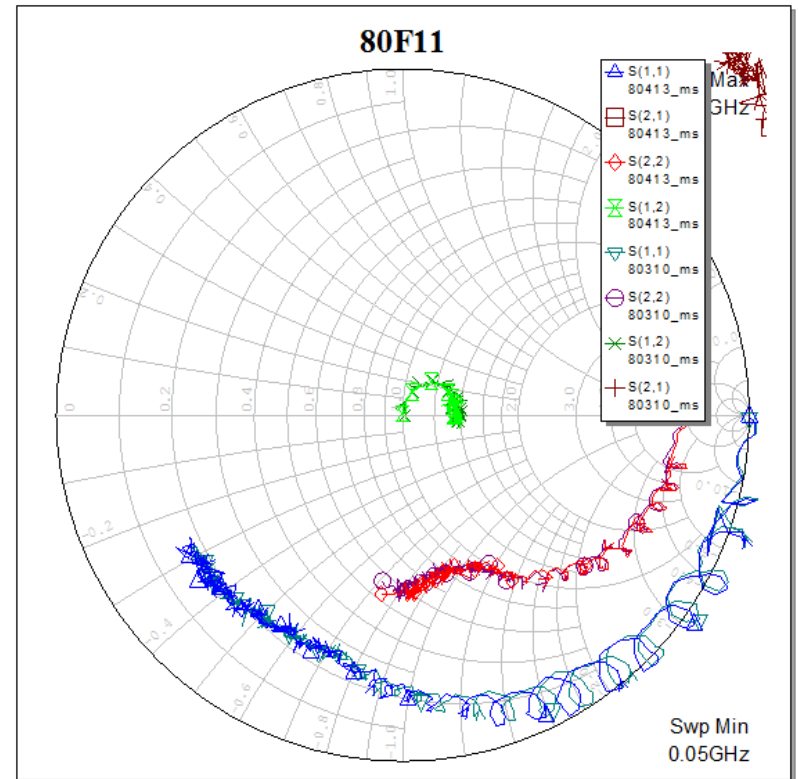
Devices 4x20 PHEMT



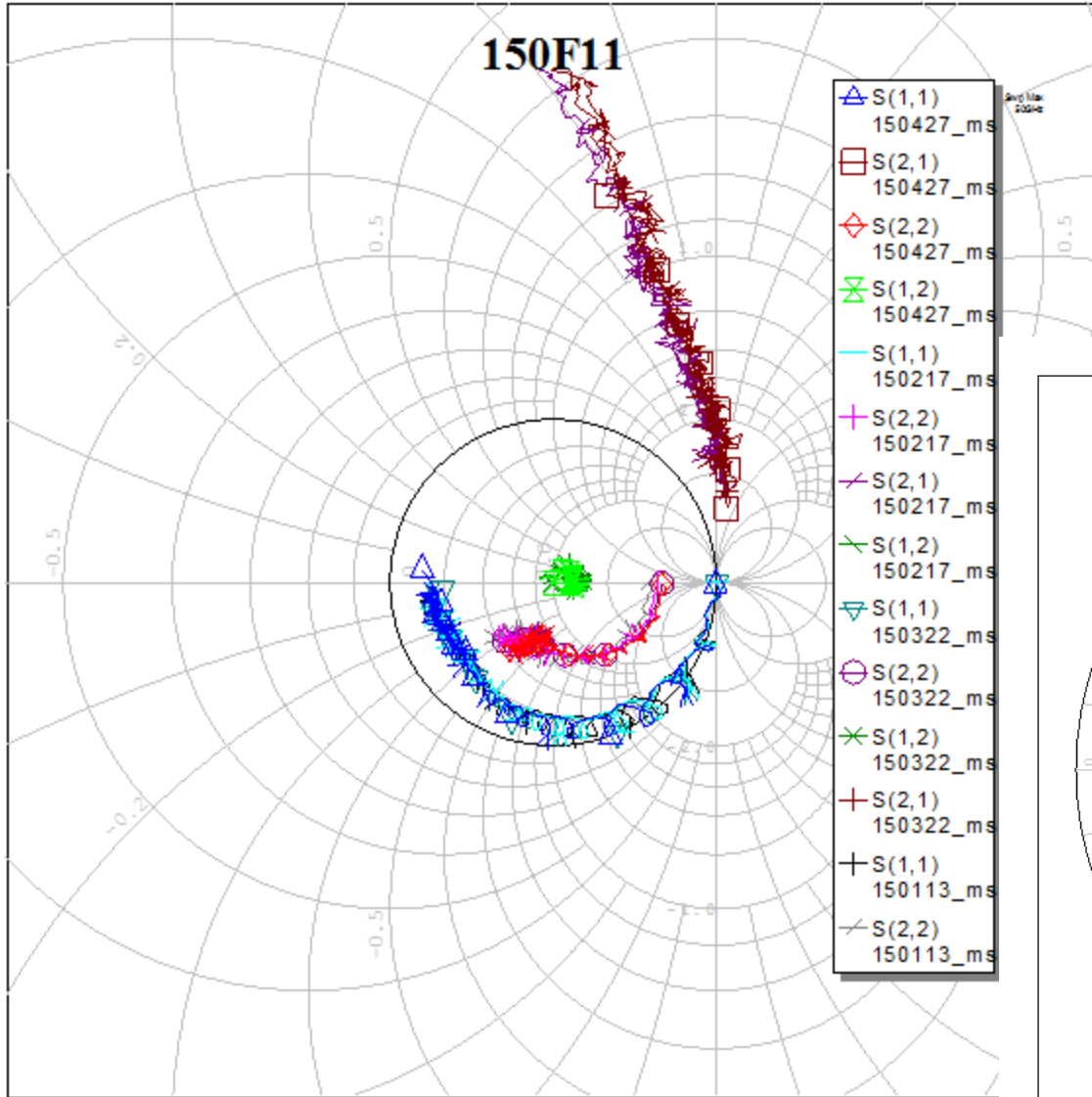
4x20 = 80

80310 3V 10 mA

80413 4V 13 mA



Devices 6x25 PHEMT



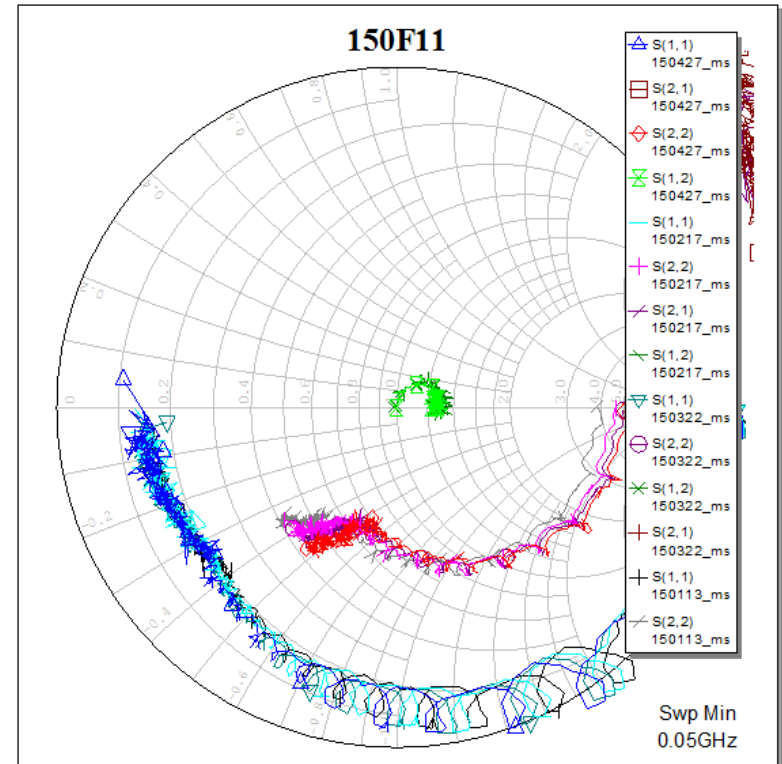
6x25 = 150

150113 1V 13 mA

150217 2V 17 mA

150322 3V 22 mA

150427 4V 27 mA



Devices 6x50 PHEMT (Meas. vs. PHEMT model)

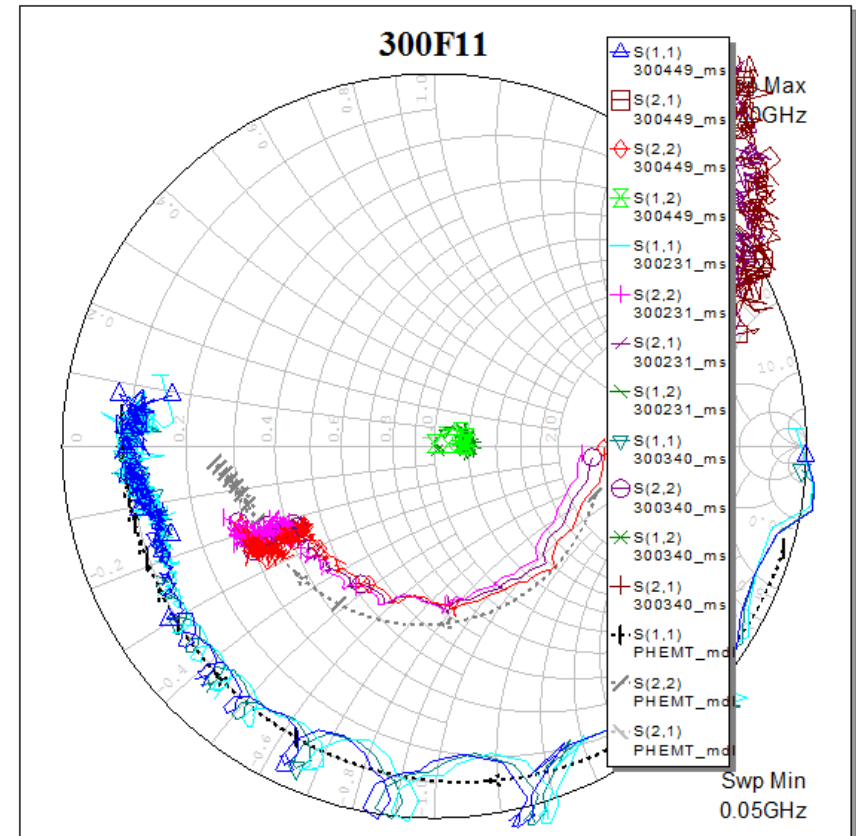
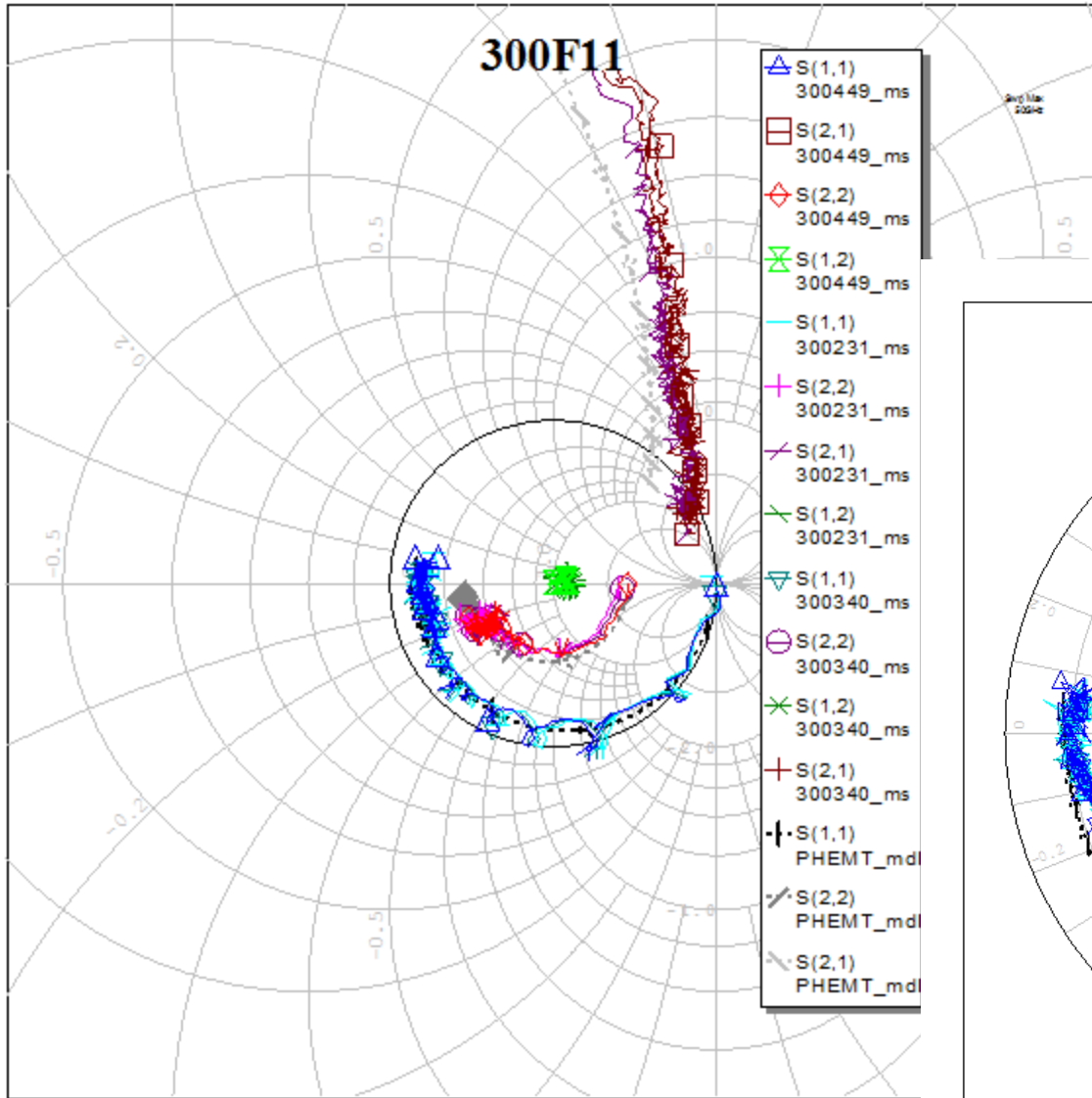
6x50 = 300

300137 1V 37 mA

300231 2V 31 mA

300340 3V 40 mA

300449 4V 49 mA



Devices 6x100 PHEMT

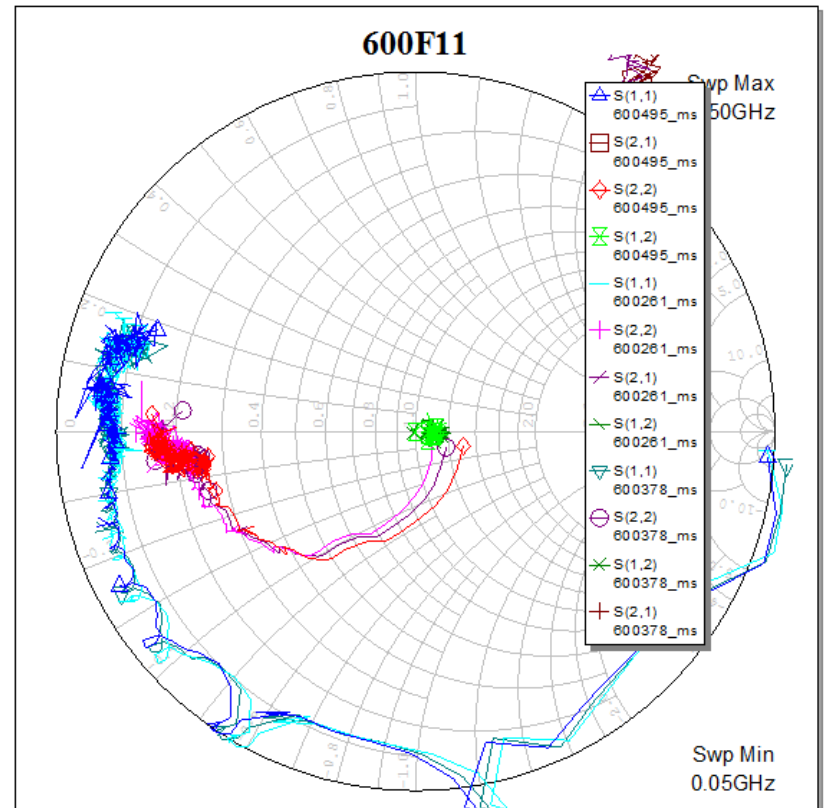
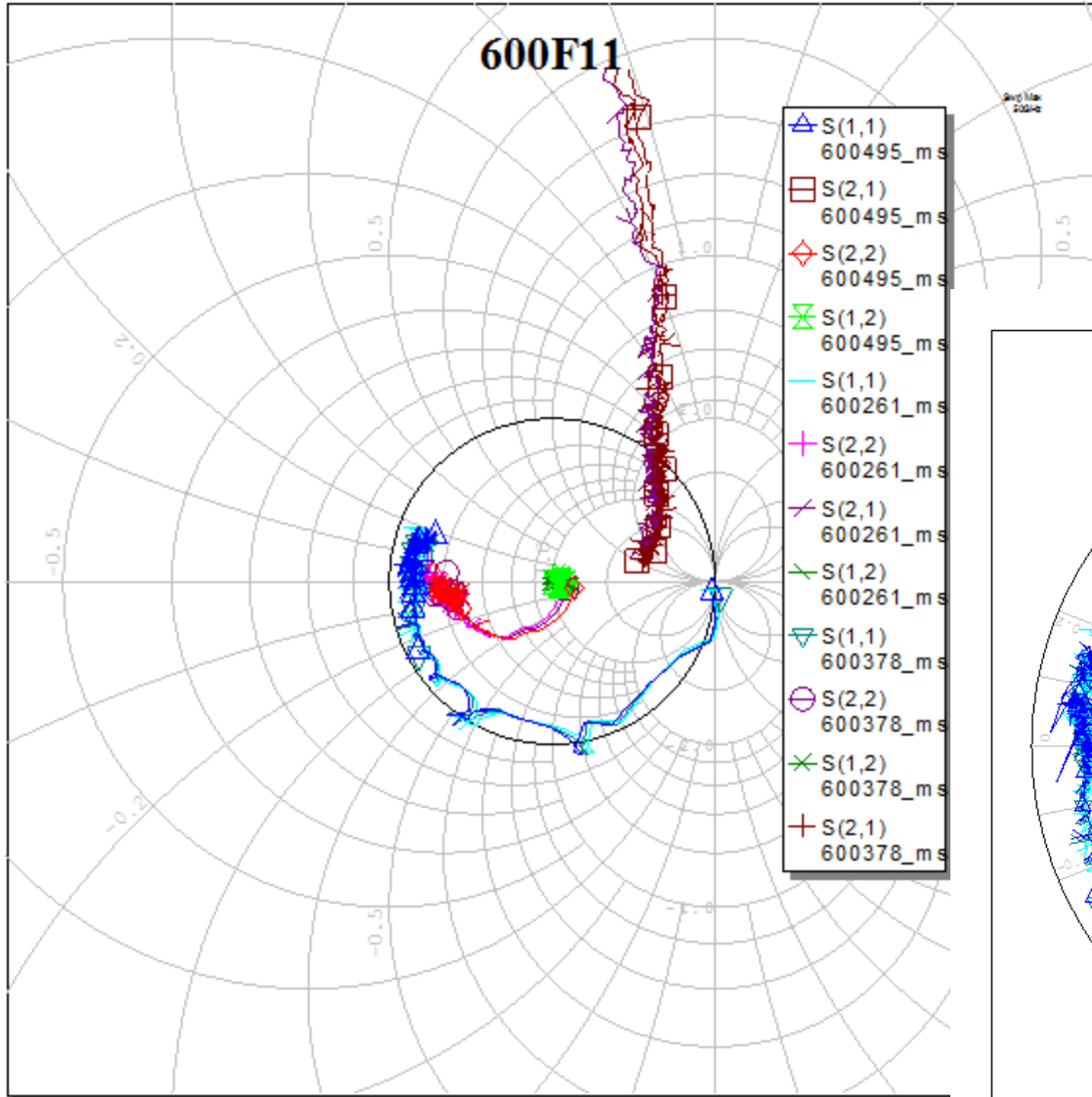
6x100 = 600

600154 1V 54 mA

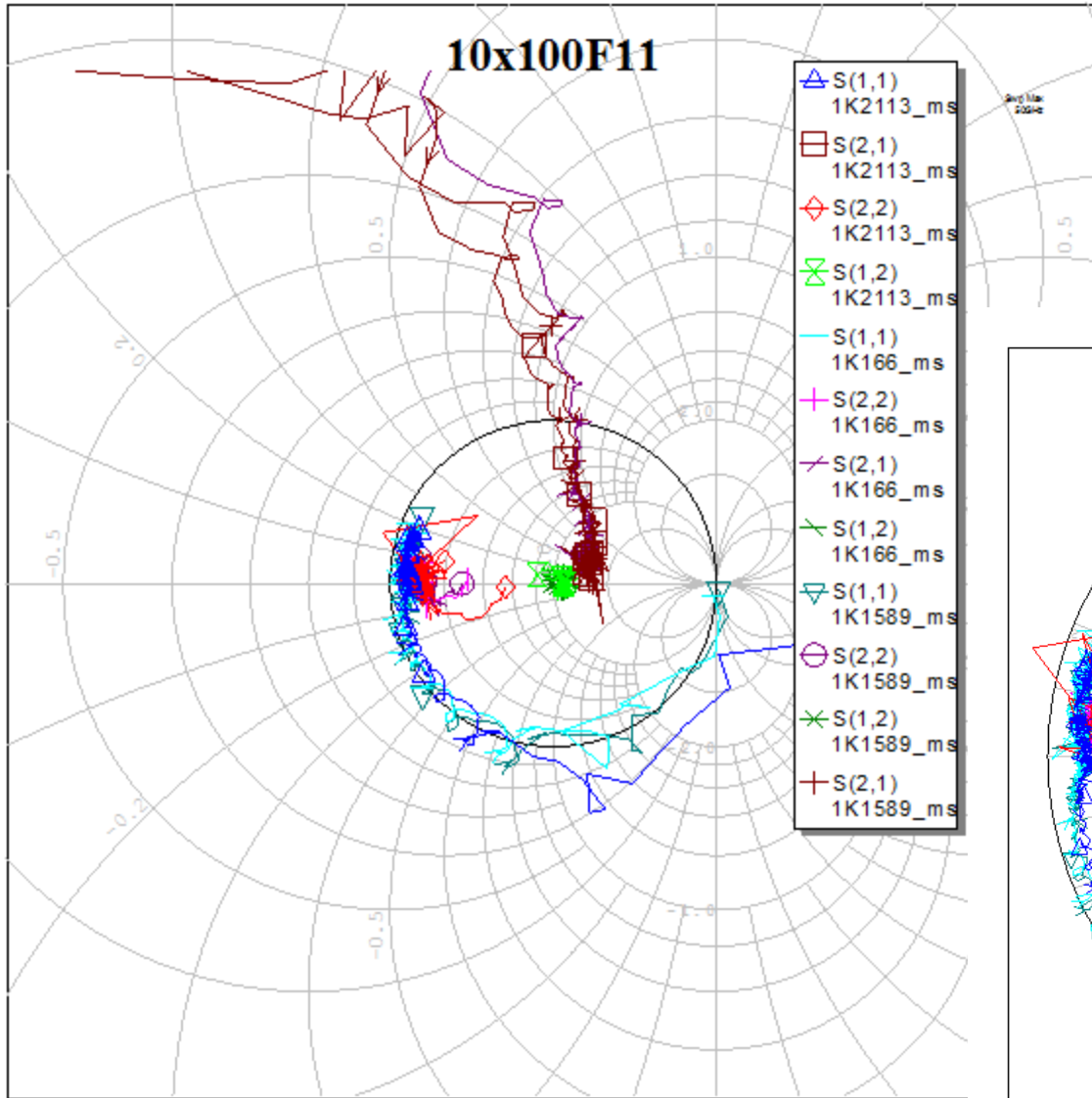
600261 2V 61 mA

600378 3V 78 mA

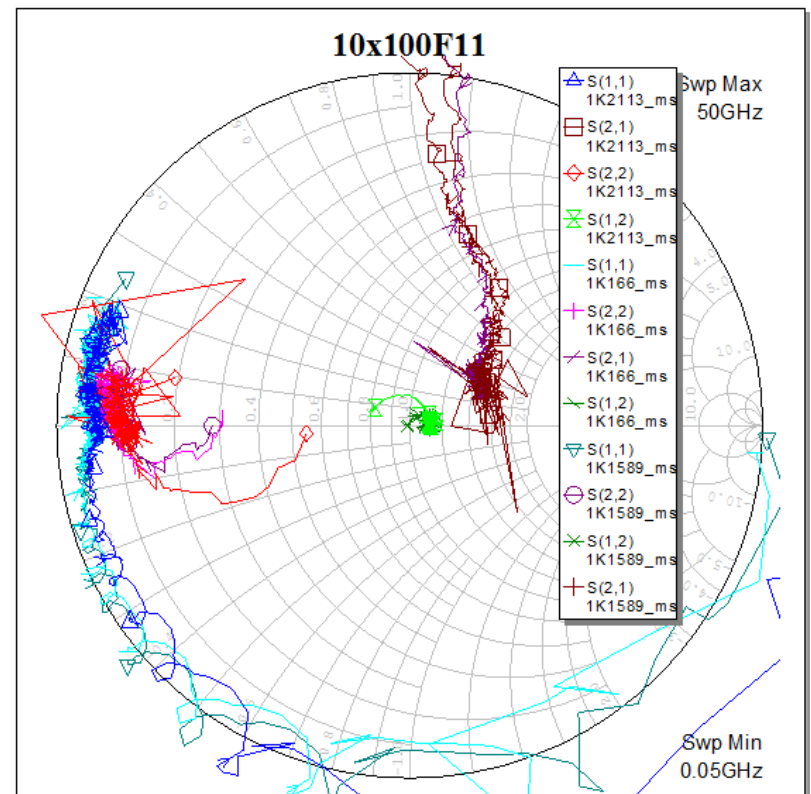
600495 4V 95 mA



Devices 10x100 PHEMT

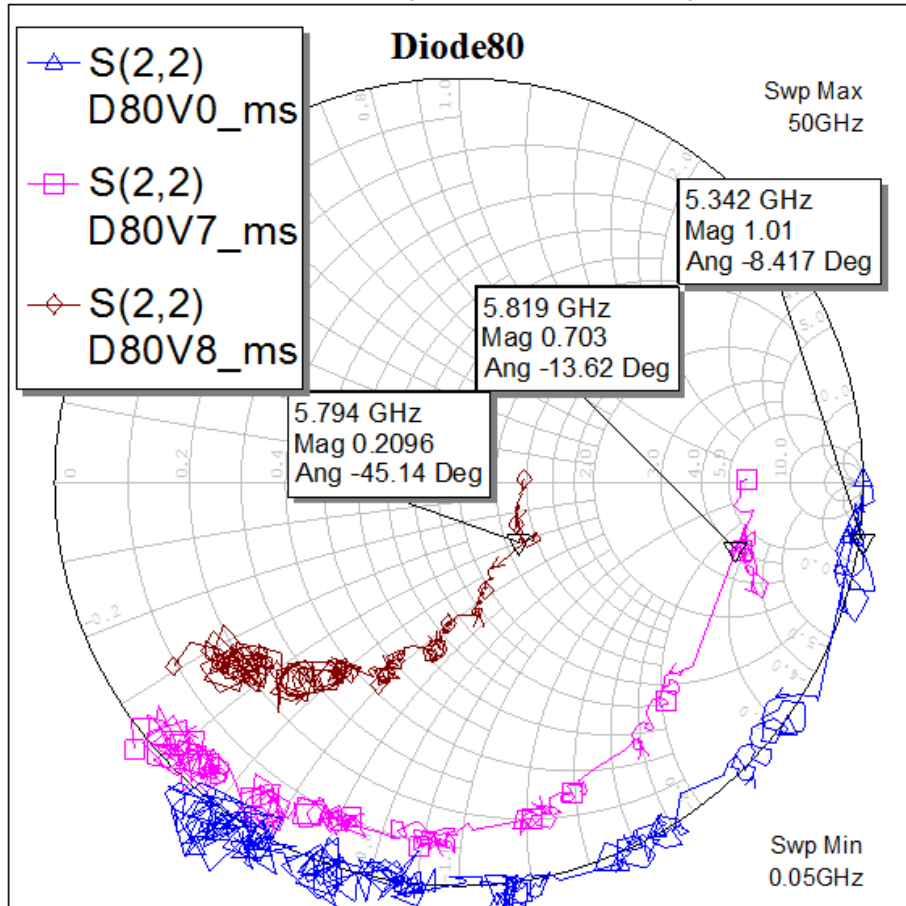


10x100 = 1K (JHU11PL8)
 1K166 1V 66 mA
 1K1589 1.5V 89 mA
 1K2113 2V 113 mA



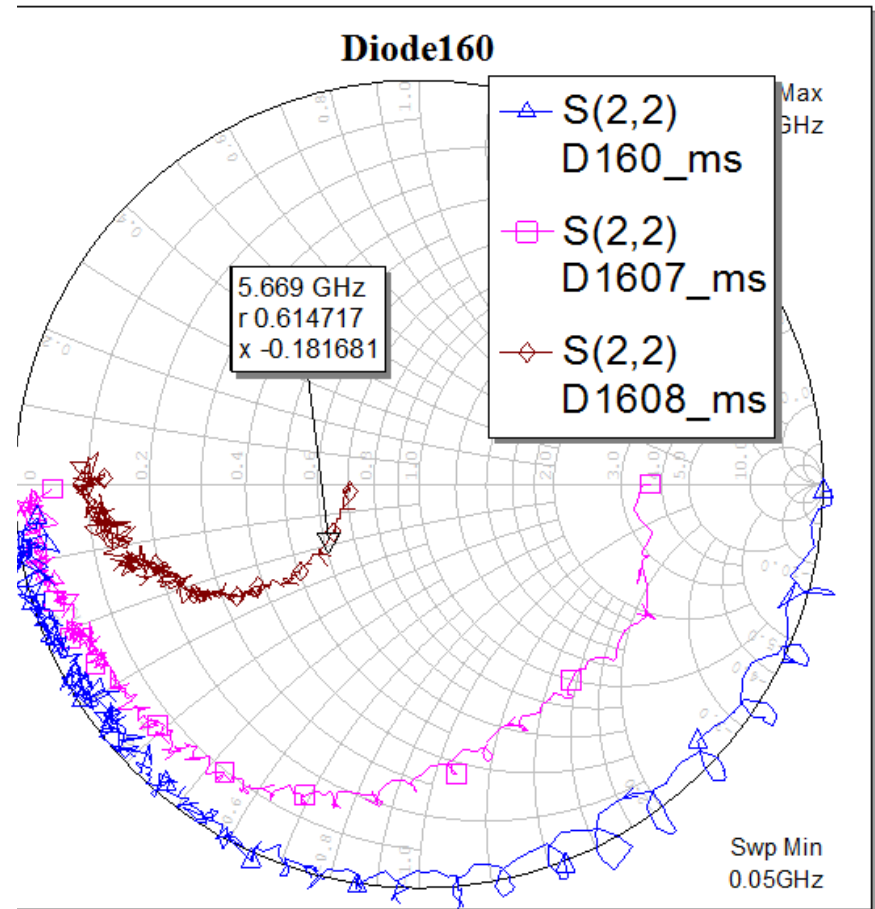
Diode 4x20 (0, 0.7, 0.8V)

- 4x20 = 80 Diode (S22 only)
- d80v0 0V (poor match, looks like cap!)
- d80v7 0.7V (good match)
- d80v8 0.8V (better match!)



Diode 4x40 (0, 0.7, 0.8V)

- Diodes 0, 0.7V, 0.8V
- D160 0V
- D1607 0.7V 1mA
- D1608 0.8V 2mA

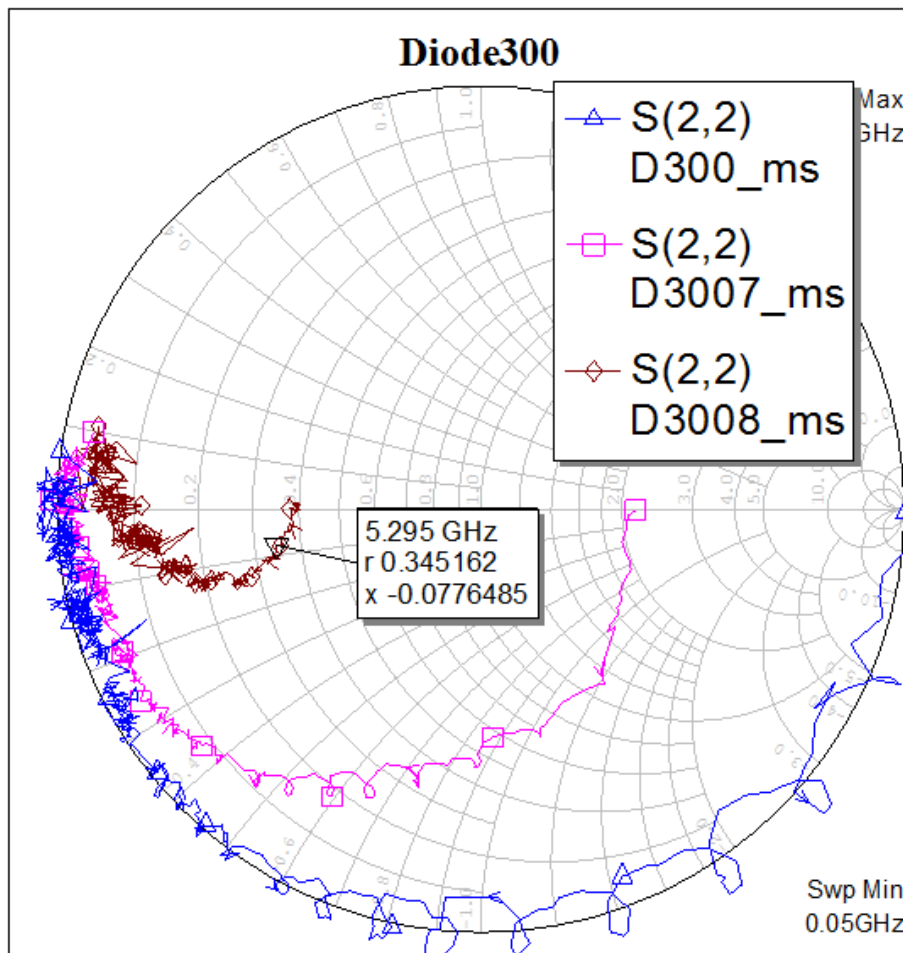


Diode 6x50 (0, 0.7, 0.8V)

D300 0V

D3007 0.7V 1mA

D3008 0.8V 3mA

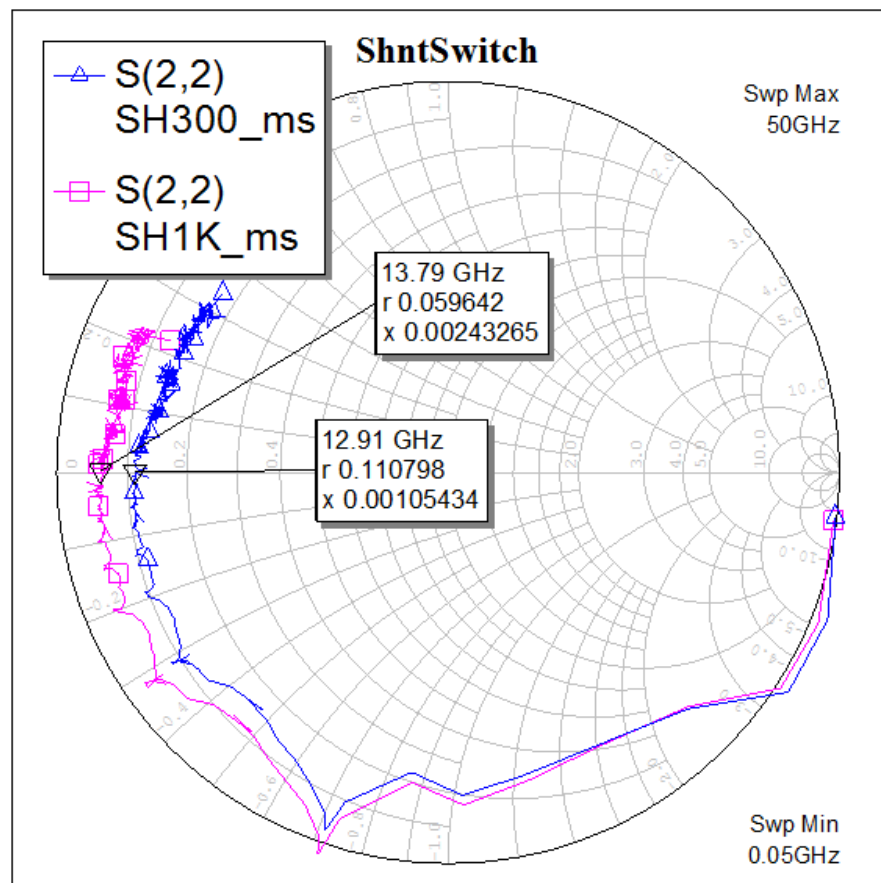


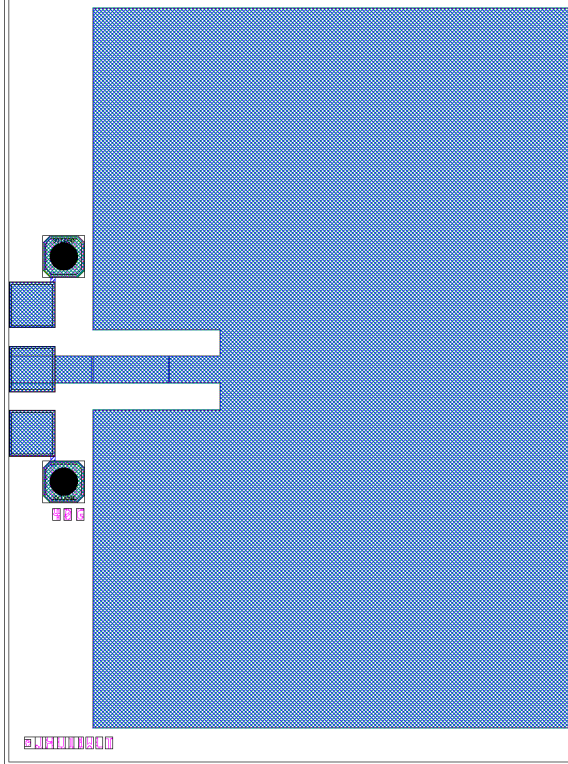
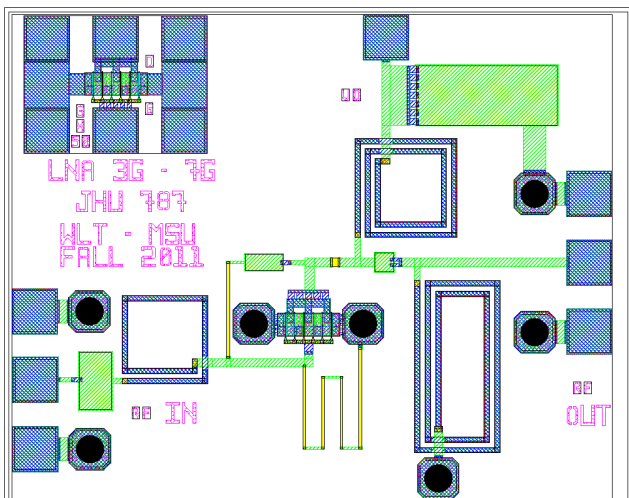
Shunt Switch 6x50, 10x100 (0V)

Shunt Switch (S22, 0V)

sh300 (6x50)

sh1K (10x100)





14) JHU11WLT

WLT LNA

Patch Antenna 40 GHz

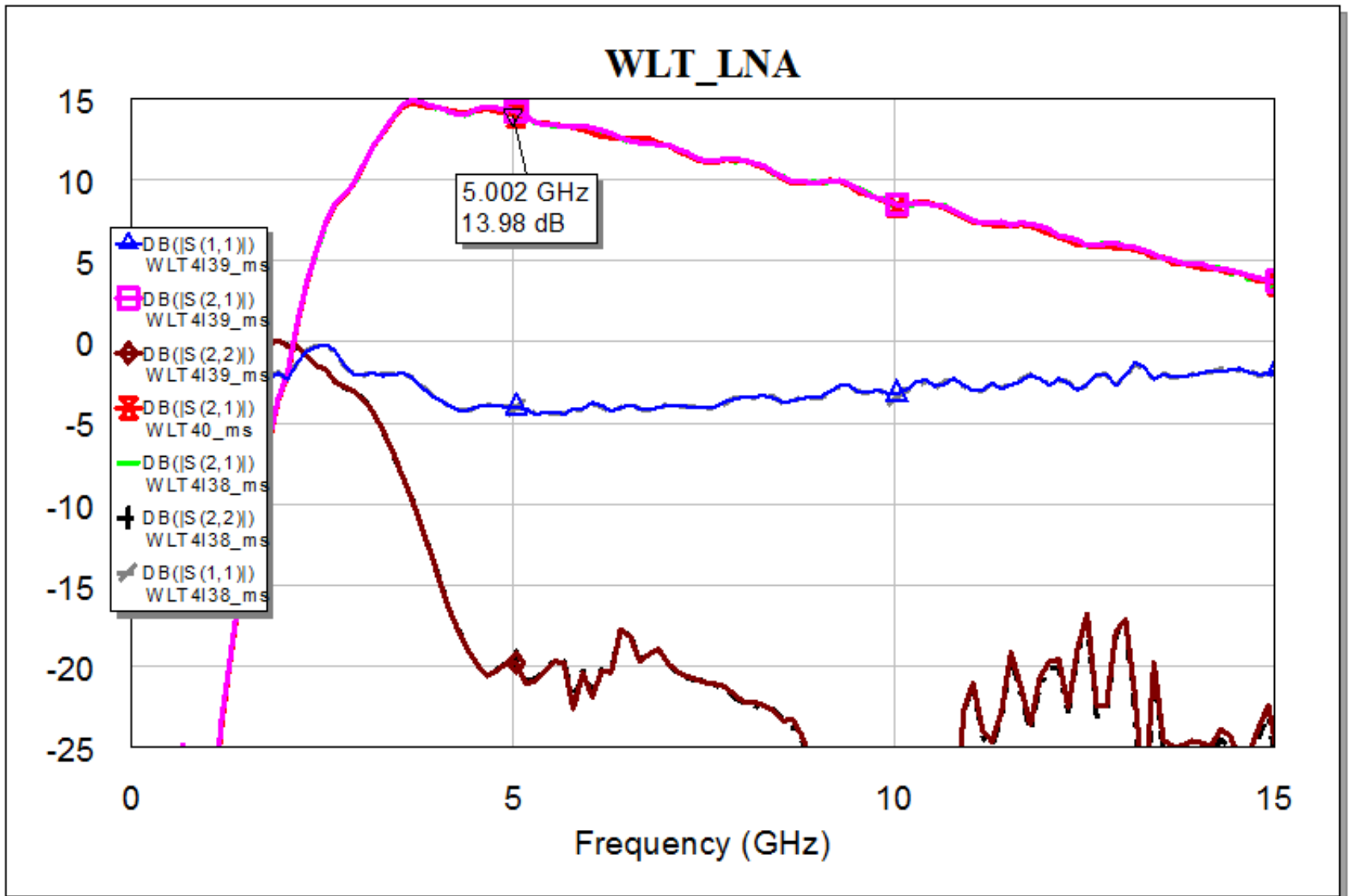
4V 35 mA (1 DC, 2RF)

(1 RF)

Broadband LNA design for constant
flat noise figure. Worked well.

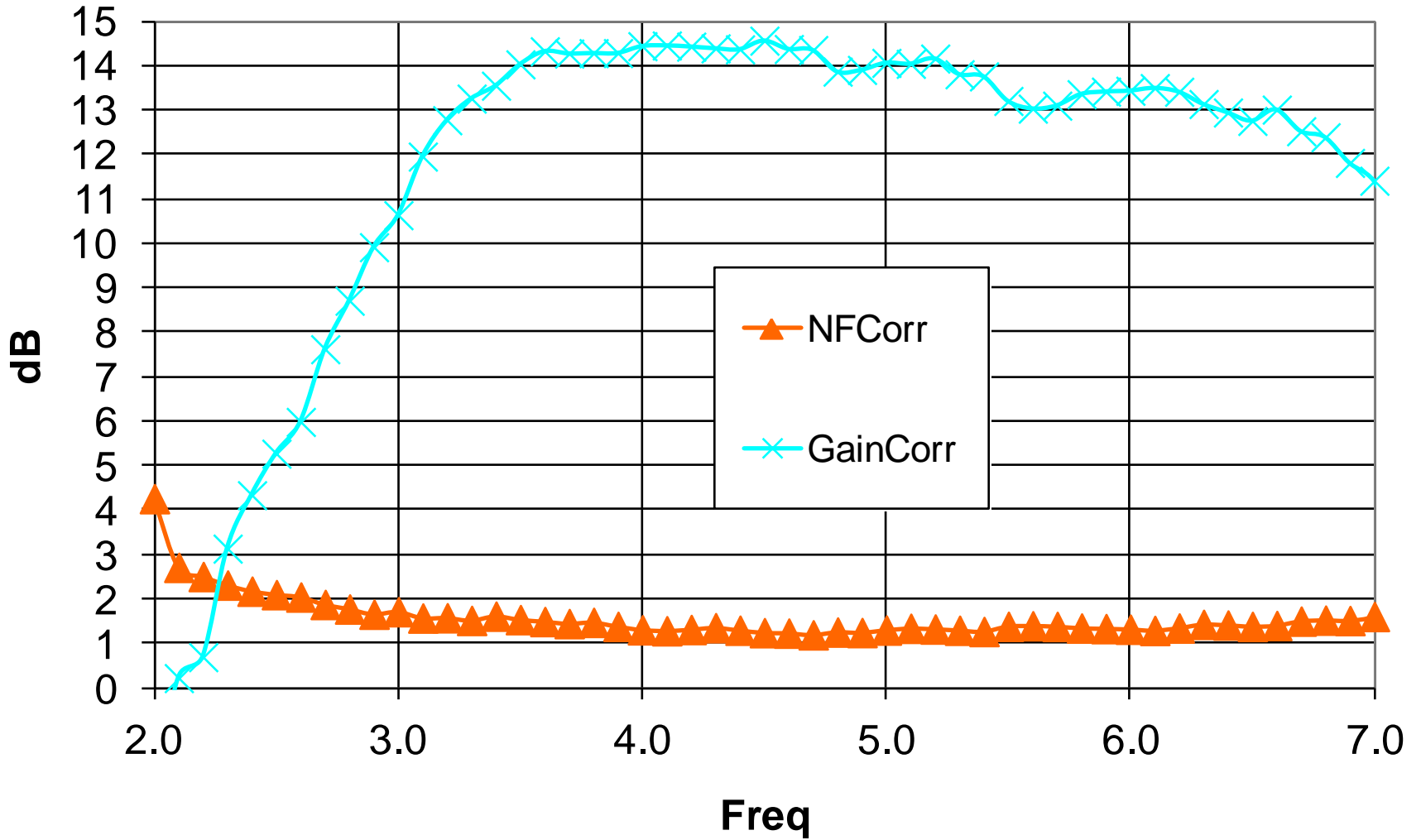
Patch Antenna at ~40 GHz—
measured as one port only.

14) JHU11WLT
WLT LNA
Patch Antenna 40 GHz

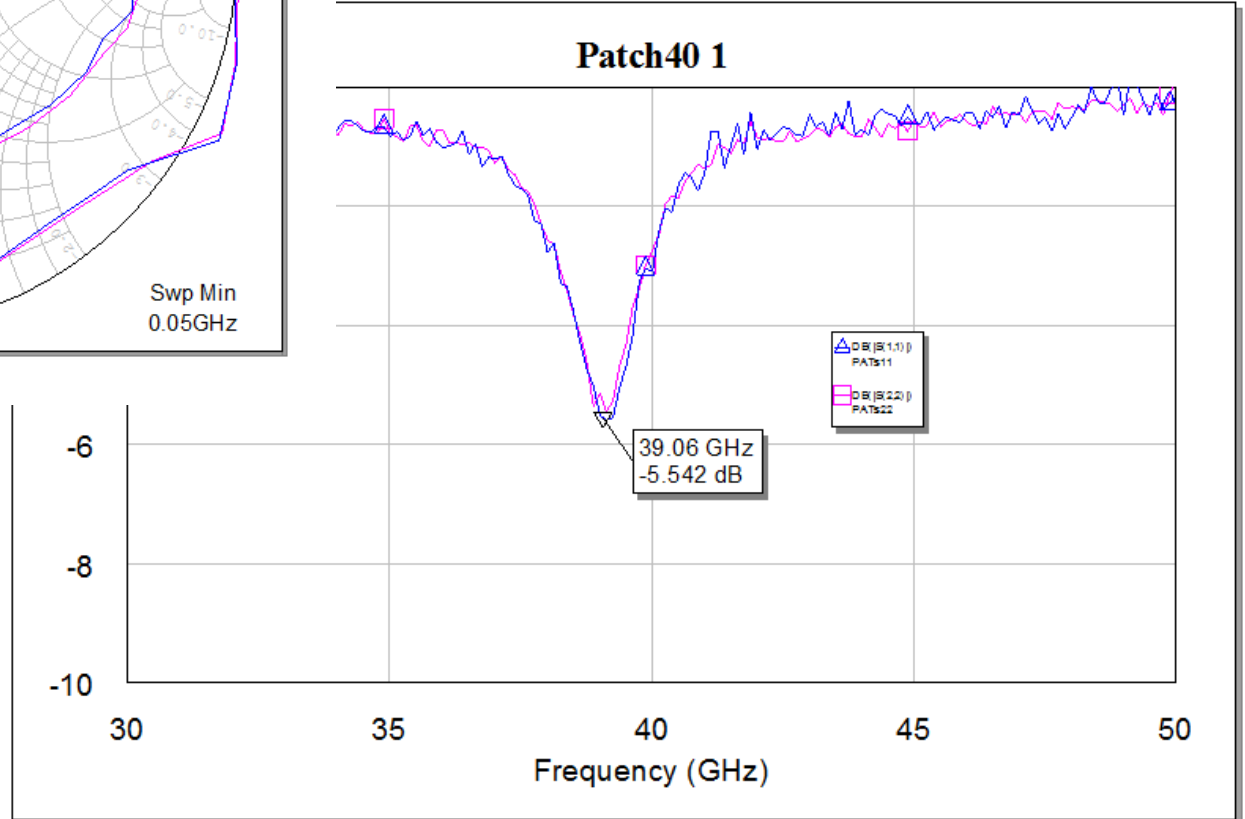
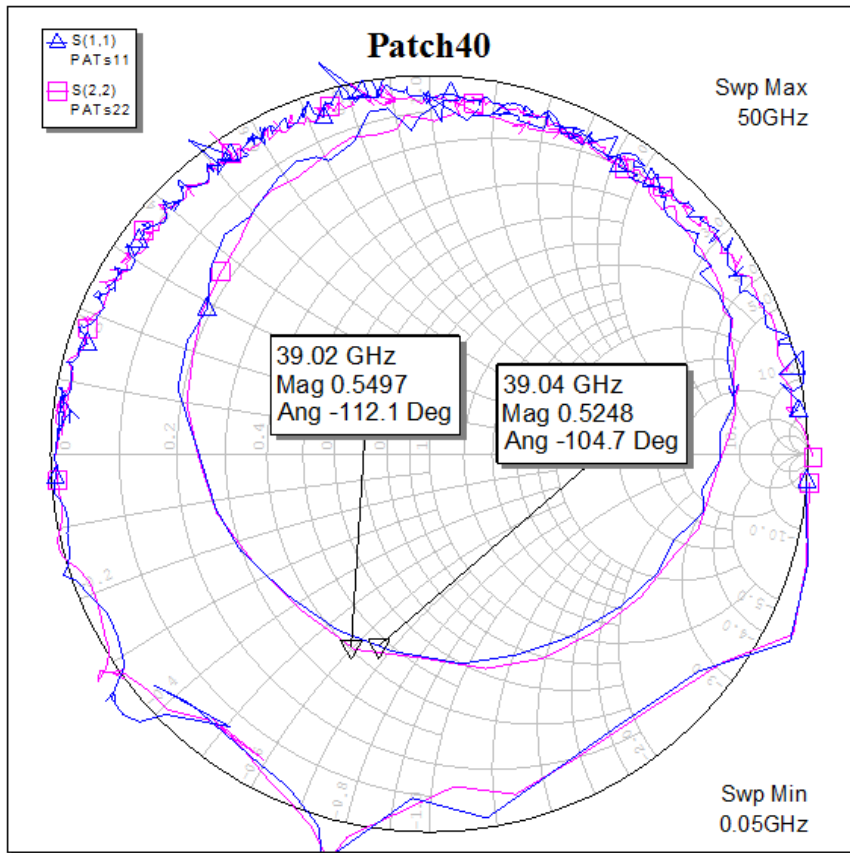


14) JHU11WLT
WLT LNA

LNA_WLT 4V



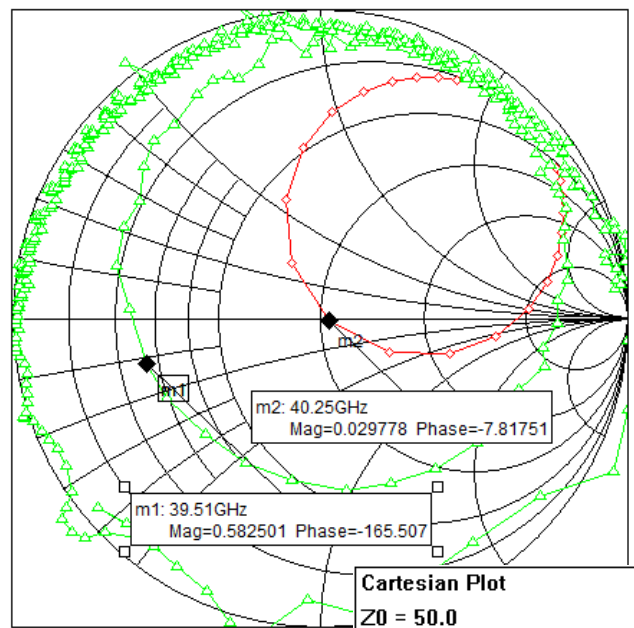
14) JHU11WLT
WLT LNA
Patch Antenna 40 GHz



Smith Plot
 Impedance
 Z0 = 50.0

Pat40c ◇
 [S11] ◇
 m2: 40.25GHz
 Mag=0.029778 Ph

PATs11 △
 [S11] △
 m1: 39.51GHz
 Mag=0.582501 Ph



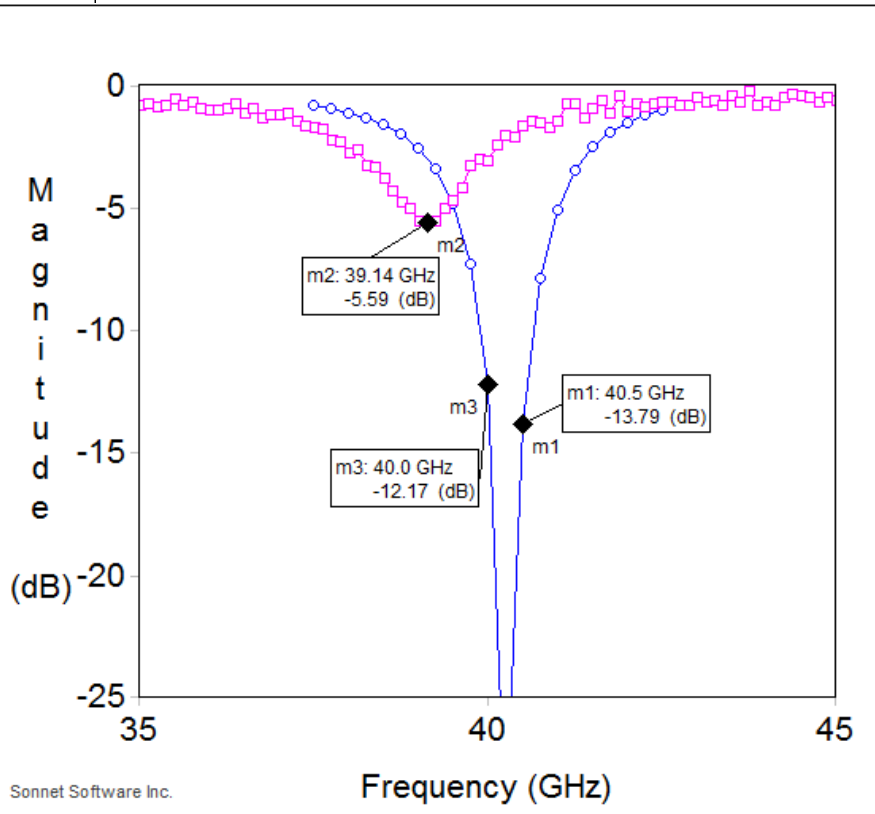
Sonnet Software Inc.

Cartesian Plot
 Z0 = 50.0

Left Axis
 Pat40c ○
 DB[S11] ○
 m1: 40.5 GHz
 -13.79 (dB)
 m3: 40.0 GHz
 -12.17 (dB)

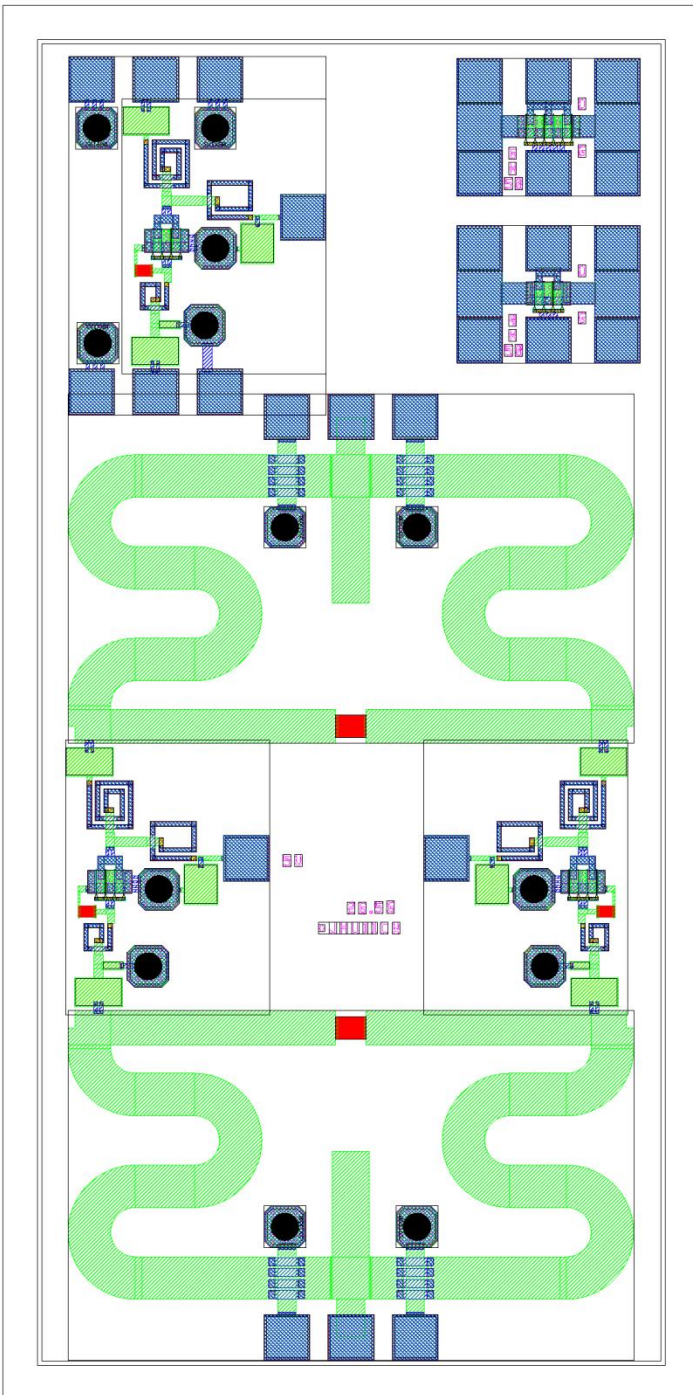
PATs11 □
 DB[S11] □
 m2: 39.14 GHz
 -5.59 (dB)

Right Axis
 [empty]



Sonnet Software Inc.

14) JHU11WLT WLT LNA Patch Antenna 40 GHz vs. Sonnet



15) JHU11CW – Caroline Waiyaki

26 GHz Amp, combined

D6x50, D4x50

5V 45 mA (2 DC, 2RF)

5V 45 mA (1 DC, 2RF)

Single Stage Amplifier and parallel
combined stages compared
favorably to simulations for small
signal parameters and DC bias.

15) JHU11CW – Caroline Waiyaki
26 GHz Amp, combined

